

STM32L053C6 STM32L053C8 STM32L053R6 STM32L053R8

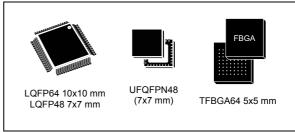
Ultra-low-power 32-bit MCU Arm[®]-based Cortex[®]-M0+, up to 64KB Flash, 8KB SRAM, 2KB EEPROM, LCD, USB, ADC, DAC

Datasheet - production data

Features

Includes ST state-of-the-art patented technology

- Ultra-low-power platform
 - 1.65 V to 3.6 V power supply
 - -40 to 125 °C temperature range
 - 0.27 μA Standby mode (2 wake-up pins)
 - 0.4 μA Stop mode (16 wake-up lines)
 - 0.8 µA Stop mode + RTC + 8-Kbyte RAM retention
 - 88 µA/MHz in Run mode
 - 3.5 μs wake-up time (from RAM)
 - 5 μs wake-up time (from flash memory)
- Core: Arm[®] 32-bit Cortex[®]-M0+ with MPU
 - From 32 kHz up to 32 MHz max.
 - 0.95 DMIPS/MHz
- Memories
 - Up to 64-Kbyte flash memory with ECC
 - 8-Kbyte RAM
 - 2 Kbytes of data EEPROM with ECC
 - 20-byte backup register
 - Sector protection against R/W operation
- Up to 51 fast I/Os (45 I/Os 5V tolerant)
- Reset and supply management
 - Ultra-safe, low-power BOR (brownout reset) with 5 selectable thresholds
 - Ultra-low-power POR/PDR
 - Programmable voltage detector (PVD)
- · Clock sources
 - 1 to 25 MHz crystal oscillator
 - 32 kHz oscillator for RTC with calibration
 - High speed internal 16 MHz factorytrimmed RC (+/- 1%)
 - Internal low-power 37 kHz RC
 - Internal multispeed low-power 65 kHz to 4.2 MHz RC
 - PLL for CPU clock
- Preprogrammed bootloader
 - USART, SPI supported
- Development support
 - Serial wire debug supported



- LCD driver for up to 8×28 segments
 - Support contrast adjustment
 - Support blinking mode
 - Step-up converted on board
- Rich Analog peripherals
 - 12-bit ADC 1.14 Msps up to 16 channels (down to 1.65 V)
 - 12-bit 1 channel DAC with output buffers (down to 1.8 V)
 - 2x ultra-low-power comparators (window mode and wake up capability, down to 1.65 V)
- Up to 24 capacitive sensing channels supporting touchkey, linear and rotary touch sensors
- 7-channel DMA controller, supporting ADC, SPI, I2C, USART, DAC, Timers
- 8x peripheral communication interfaces
 - 1x USB 2.0 crystal-less, battery charging detection and LPM
 - 3x USART/LPUART (SPI, ISO 7816, IrDA)
 - Up to 4x SPI 16 Mbits/s (+ 2 with USART)
 - 2x I2C (SMBus/PMBus)
- 9x timers: 1x 16-bit with up to 4 channels, 2x 16-bit with up to 2 channels, 1x 16-bit ultra-low-power timer, 1x SysTick, 1x RTC, 1x 16-bit basic for DAC, 2x watchdogs (independent/window)



- CRC calculation unit, 96-bit unique ID
- True RNG and firewall protection
- All packages are ECOPACK2

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1 Introduction

The ultra-low-power STM32L053x6/8 are offered in 4 different package types: from 48 pins to 64 pins. Depending on the device chosen, different sets of peripherals are included, the description below gives an overview of the complete range of peripherals proposed in this family.

These features make the ultra-low-power STM32L053x6/8 microcontrollers suitable for a wide range of applications:

- Gas/water meters and industrial sensors
- Healthcare and fitness equipment
- · Remote control and user interface
- · PC peripherals, gaming, GPS equipment
- Alarm system, wired and wireless sensors, video intercom

This STM32L053x6/8 datasheet should be read in conjunction with the STM32L0x3xx reference manual (RM0367).

For information on the device errata with respect to the datasheet and reference manual, refer to the STM32L053x6/8 errata sheet (ES0251), available on the STMicroelectronics website www.st.com.

For information on the Arm^{®(a)} Cortex[®]-M0+ core please refer to the Cortex[®]-M0+ Technical Reference Manual, available from the www.arm.com website.

Figure 1 shows the general block diagram of the device family.

arm



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2 Description

The ultra-low-power STM32L053x6/8 microcontrollers incorporate the connectivity power of the universal serial bus (USB 2.0 crystal-less) with the high-performance Arm Cortex-M0+32-bit RISC core operating at a 32 MHz frequency, a memory protection unit (MPU), high-speed embedded memories (up to 64 Kbytes of flash program memory, 2 Kbytes of data EEPROM and 8 Kbytes of RAM) plus an extensive range of enhanced I/Os and peripherals.

The STM32L053x6/8 devices provide high power efficiency for a wide range of performance. It is achieved with a large choice of internal and external clock sources, an internal voltage adaptation and several low-power modes.

The STM32L053x6/8 devices offer several analog features, one 12-bit ADC with hardware oversampling, one DAC, two ultra-low-power comparators, several timers, one low-power timer (LPTIM), three general-purpose 16-bit timers and one basic timer, one RTC and one SysTick which can be used as timebases. They also feature two watchdogs, one watchdog with independent clock and window capability and one window watchdog based on bus clock.

Moreover, the STM32L053x6/8 devices embed standard and advanced communication interfaces: up to two I2C, two SPIs, one I2S, two USARTs, a low-power UART (LPUART), and a crystal-less USB. The devices offer up to 24 capacitive sensing channels to simply add touch sensing functionality to any application.

The STM32L053x6/8 also include a real-time clock and a set of backup registers that remain powered in Standby mode.

Finally, their integrated LCD controller has a built-in LCD voltage generator that allows to drive up to 8 multiplexed LCDs with contrast independent of the supply voltage.

The ultra-low-power STM32L053x6/8 devices operate from a 1.8 to 3.6 V power supply (down to 1.65 V at power down) with BOR and from a 1.65 to 3.6 V power supply without BOR option. They are available in the -40 to +125 °C temperature range. A comprehensive set of power-saving modes allows the design of low-power applications.



2.1 Device overview

Table 1. Ultra-low-power STM32L053x6/x8 device features and peripheral counts

Perip	pheral	STM32L053C6	STM32L053R6	STM32L053C8	STM32L053R8	
Flash (Kbytes)		32		64		
Data EEPROM (Kbyt	es)	2	2	2	2	
RAM (Kbytes)		8	3		8	
	General-purpose	;	3	;	3	
Timers	Basic	,	1		1	
	LPTIMER		1		1	
RTC/SYSTICK	(/IWDG/WWDG	1/1.	/1/1	1/1.	/1/1	
	SPI/I2S	4(2)	⁽¹⁾ /1	4(2)	⁽¹⁾ /1	
	I ² C	2	2	-	2	
Communication interfaces	USART	2	2	:	2	
	LPUART	1			1	
	USB/(VDD_USB)	1/(1)		1/(1)		
GPIOs		37	51 ⁽²⁾	37	51 ⁽²⁾	
Clocks: HSE/LSE/HS	GI/MSI/LSI	1/1/1/1		1/1/1/1		
12-bit synchronized Number of channels		1 10	1 16 ⁽²⁾	1 10	1 16 ⁽²⁾	
12-bit DAC Number of channels		1 1		1 1		
LCD COM x SEG		1 4x18	1 4x32 or 8x28 ⁽²⁾	1 4x18	1 4x32 or 8x28 ⁽²⁾	
Comparators		2		2		
Capacitive sensing of	channels	17	24 ⁽²⁾	17	24 ⁽²⁾	
Max. CPU frequency	,	32 MHz				
Operating voltage		1.8 V to 3.6 V (down to 1.65 V at power-down) with BOR option 1.65 V to 3.6 V without BOR option				
Operating temperatu	ıres	Ambient temperature: -40 to +125 °C Junction temperature: -40 to +130 °C				
Packages		LQFP48, UFQFPN48	LQFP64, TFBGA64	LQFP48, UFQFPN48	LQFP64, TFBGA64	

^{1. 2} SPI interfaces are USARTs operating in SPI master mode.

^{2.} TFBGA64 has one GPIO, one LCD COM x SEG, one ADC input and one capacitive sensing channel less than LQFP64.

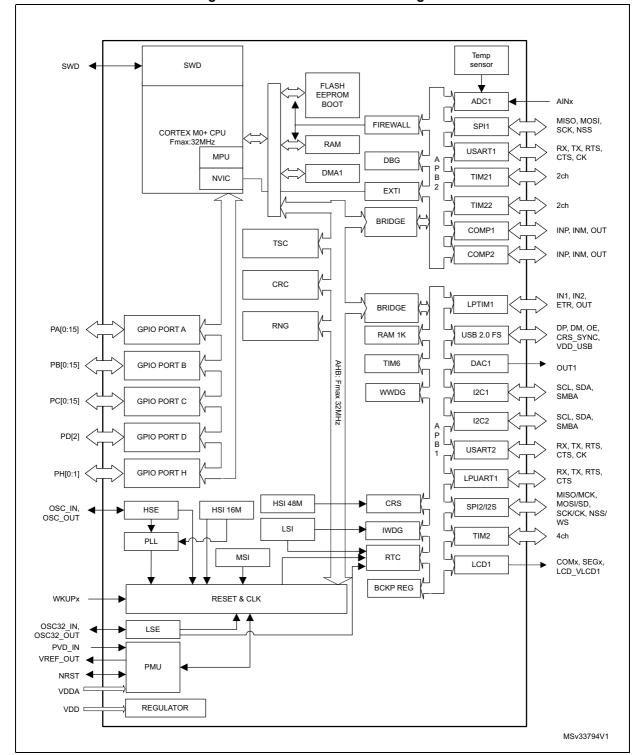


Figure 1. STM32L053x6/8 block diagram

2.2 Ultra-low-power device continuum

The ultra-low-power family offers a large choice of core and features, from 8-bit proprietary core up to Arm[®] Cortex[®]-M4, including Arm[®] Cortex[®]-M3 and Arm[®] Cortex[®]-M0+. The STM32Lx series are the best choice to answer your needs in terms of ultra-low-power features. The STM32 ultra-low-power series are the best solution for applications such as gaz/water meter, keyboard/mouse or fitness and healthcare application. Several built-in features like LCD drivers, dual-bank memory, low-power run mode, operational amplifiers, 128-bit AES, DAC, crystal-less USB and many other definitely help you building a highly cost optimized application by reducing BOM cost. STMicroelectronics, as a reliable and long-term manufacturer, ensures as much as possible pin-to-pin compatibility between all STM8Lx and STM32Lx on one hand, and between all STM32Lx and STM32Fx on the other hand. Thanks to this unprecedented scalability, your legacy application can be upgraded to respond to the latest market feature and efficiency requirements.

3 Functional overview

3.1 Low-power modes

The ultra-low-power STM32L053x6/8 support dynamic voltage scaling to optimize its power consumption in Run mode. The voltage from the internal low-drop regulator that supplies the logic can be adjusted according to the system's maximum operating frequency and the external voltage supply.

There are three power consumption ranges:

- Range 1 (V_{DD} range limited to 1.71-3.6 V), with the CPU running at up to 32 MHz
- Range 2 (full V_{DD} range), with a maximum CPU frequency of 16 MHz
- Range 3 (full V_{DD} range), with a maximum CPU frequency limited to 4.2 MHz

Seven low-power modes are provided to achieve the best compromise between low-power consumption, short startup time and available wake-up sources:

Sleep mode

In Sleep mode, only the CPU is stopped. All peripherals continue to operate and can wake up the CPU when an interrupt/event occurs. Sleep mode power consumption at 16 MHz is about 1 mA with all peripherals off.

Low-power run mode

This mode is achieved with the multispeed internal (MSI) RC oscillator set to the low-speed clock (max 131 kHz), execution from SRAM or flash memory, and internal regulator in low-power mode to minimize the regulator's operating current. In Low-power run mode, the clock frequency and the number of enabled peripherals are both limited.

• Low-power sleep mode

This mode is achieved by entering Sleep mode with the internal voltage regulator in low-power mode to minimize the regulator's operating current. In Low-power sleep mode, both the clock frequency and the number of enabled peripherals are limited; a typical example would be to have a timer running at 32 kHz.

When wake-up is triggered by an event or an interrupt, the system reverts to the Run mode with the regulator on.

Stop mode with RTC

The Stop mode achieves the lowest power consumption while retaining the RAM and register contents and real time clock. All clocks in the V_{CORE} domain are stopped, the PLL, MSI RC, HSE crystal and HSI RC oscillators are disabled. The LSE or LSI is still running. The voltage regulator is in the low-power mode.

Some peripherals featuring wake-up capability can enable the HSI RC during Stop mode to detect their wake-up condition.

The device can be woken up from Stop mode by any of the EXTI line, in 3.5 µs, the processor can serve the interrupt or resume the code. The EXTI line source can be any GPIO. It can be the PVD output, the comparator 1 event or comparator 2 event (if internal reference voltage is on), it can be the RTC alarm/tamper/timestamp/wake-up events, the USB/USART/I2C/LPUART/LPTIMER wake-up events.

Stop mode without RTC

The Stop mode achieves the lowest power consumption while retaining the RAM and register contents. All clocks are stopped, the PLL, MSI RC, HSI and LSI RC, HSE and LSE crystal oscillators are disabled.

Some peripherals featuring wake-up capability can enable the HSI RC during Stop mode to detect their wake-up condition.

The voltage regulator is in the low-power mode. The device can be woken up from Stop mode by any of the EXTI line, in 3.5 μ s, the processor can serve the interrupt or resume the code. The EXTI line source can be any GPIO. It can be the PVD output, the comparator 1 event or comparator 2 event (if internal reference voltage is on). It can also be wakened by the USB/USART/I2C/LPUART/LPTIMER wake-up events.

Standby mode with RTC

The Standby mode is used to achieve the lowest power consumption and real time clock. The internal voltage regulator is switched off so that the entire V_{CORE} domain is powered off. The PLL, MSI RC, HSE crystal and HSI RC oscillators are also switched off. The LSE or LSI is still running. After entering Standby mode, the RAM and register contents are lost except for registers in the Standby circuitry (wake-up logic, IWDG, RTC, LSI, LSE Crystal 32 KHz oscillator, RCC_CSR register).

The device exits Standby mode in 60 µs when an external reset (NRST pin), an IWDG reset, a rising edge on one of the three WKUP pins, RTC alarm (Alarm A or Alarm B), RTC tamper event, RTC timestamp event or RTC Wake-up event occurs.

Standby mode without RTC

The Standby mode is used to achieve the lowest power consumption. The internal voltage regulator is switched off so that the entire V_{CORE} domain is powered off. The PLL, MSI RC, HSI and LSI RC, HSE and LSE crystal oscillators are also switched off. After entering Standby mode, the RAM and register contents are lost except for registers in the Standby circuitry (wake-up logic, IWDG, RTC, LSI, LSE Crystal 32 KHz oscillator, RCC_CSR register).

The device exits Standby mode in 60 µs when an external reset (NRST pin) or a rising edge on one of the three WKUP pin occurs.

Note:

The RTC, the IWDG, and the corresponding clock sources are not stopped automatically by entering Stop or Standby mode. The LCD is not stopped automatically by entering Stop mode.



Table 2. Functionalities depending on the operating power supply range

Operating power cumply	Functionalities depending on the operating power supply range					
Operating power supply range ⁽¹⁾	DAC and ADC operation	Dynamic voltage scaling range	USB			
V _{DD} = 1.65 to 1.71 V	ADC only, conversion time up to 570 ksps	Range 2 or range 3	Not functional			
V _{DD} = 1.71 to 1.8 V ⁽²⁾	ADC only, conversion time up to 1.14 Msps	Range 1, range 2 or range 3	Functional ⁽³⁾			
V _{DD} = 1.8 to 2.0 V ⁽²⁾	Conversion time up to 1.14 Msps	Range1, range 2 or range 3	Functional ⁽³⁾			
V _{DD} = 2.0 to 2.4 V	Conversion time up to 1.14 Msps	Range 1, range 2 or range 3	Functional ⁽³⁾			
V _{DD} = 2.4 to 3.6 V	Conversion time up to 1.14 Msps	Range 1, range 2 or range 3	Functional ⁽³⁾			

GPIO speed depends on V_{DD} voltage range. Refer to Table 60: I/O AC characteristics for more information about I/O speed.

Table 3. CPU frequency range depending on dynamic voltage scaling

CPU frequency range	Dynamic voltage scaling range
16 MHz to 32 MHz (1ws) 32 kHz to 16 MHz (0ws)	Range 1
8 MHz to 16 MHz (1ws) 32 kHz to 8 MHz (0ws)	Range 2
32 kHz to 4.2 MHz (0ws)	Range 3

CPU frequency changes from initial to final must respect "fcpu initial <4*fcpu final". It must also respect 5
μs delay between two changes. For example to switch from 4.2 MHz to 32 MHz, you can switch from 4.2
MHz to 16 MHz, wait 5 μs, then switch from 16 MHz to 32 MHz.

^{3.} To be USB compliant from the I/O voltage standpoint, the minimum $\rm V_{\rm DD_USB}$ is 3.0 V.

Table 4. Functionalities depending on the working mode (from Run/active down to standby) ⁽¹⁾

			Low-			Stop		Standby	
IPs	Run/Active	Sleep	power run	power sleep		Wake-up capability		Wake-up capability	
CPU	Υ		Y						
Flash memory	0	0	0	0					
RAM	Υ	Υ	Y	Y	Υ				
Backup registers	Y	Y	Y	Y	Υ		Υ		
EEPROM	0	0	0	0					
Brown-out reset (BOR)	0	0	0	0	0	0	0	0	
DMA	0	0	0	0					
Programmable Voltage Detector (PVD)	0	0	0	0	0	0	-		
Power-on/down reset (POR/PDR)	Y	Y	Y	Y	Υ	Y	Υ	Y	
High Speed Internal (HSI)	0	0			(2)				
High Speed External (HSE)	0	0	0	0					
Low Speed Internal (LSI)	0	0	0	0	0		0		
Low Speed External (LSE)	0	0	0	0	0		0		
Multi-Speed Internal (MSI)	0	0	Y	Y					
Inter-Connect Controller	Y	Y	Υ	Y	Υ				
RTC	0	0	0	0	0	0	0		
RTC Tamper	0	0	0	0	0	0	0	0	
Auto wake-up (AWU)	0	0	0	0	0	0	0	0	
LCD	0	0	0	0	0				
USB	0	0				0			
USART	0	0	0	0	O ⁽³⁾	0	-		
LPUART	0	0	0	0	O ⁽³⁾	0			
SPI	0	0	0	0					
I2C	0	0			O ⁽⁴⁾	0	-		
ADC	0	0							

Table 4. Functionalities depending on the working mode (from Run/active down to standby) (continued)(1)

			Low-	Low-	Stop		Standby	
IPs	Run/Active	Sleep	power run	power sleep		Wake-up capability		Wake-up capability
DAC	0	0	0	0	0			
Temperature sensor	0	0	0	0	0			
Comparators	0	0	0	0	0	0		
16-bit timers	0	0	0	0				
LPTIMER	0	0	0	0	0	0		
IWDG	0	0	0	0	0	0	0	0
WWDG	0	0	0	0				
Touch sensing controller (TSC)	0	0						
SysTick Timer	0	0	0	0				
GPIOs	0	0	0	0	0	0		2 pins
Wake-up time to Run mode	0 μs	0.36 µs	3 µs	32 µs		3.5 µs		50 µs
						4 μA (No) V _{DD} =1.8 V		28 μΑ (No) V _{DD} =1.8 V
Consumption V _{DD} =1.8 to 3.6 V	140 μA/MHz 37 μA (from flash (from	Down to 37 µA/MHz	Down to	Down to	0.8 μA (with RTC) V _{DD} =1.8 V		0.65 μA (with RTC) V _{DD} =1.8 V	
(Typ)		(from flash memory)	8 μΑ	4.5 μA	0.4 μA (No RTC) V _{DD} =3.0 V			29 μA (No) V _{DD} =3.0 V
						(with RTC) DD=3.0 V		5 μA (with) V _{DD} =3.0 V

^{1.} Legend:

- 2. Some peripherals with wake-up from Stop capability can request HSI to be enabled. In this case, HSI is woken up by the peripheral, and only feeds the peripheral which requested it. HSI is automatically put off when the peripheral does not need it anymore.
- 3. UART and LPUART reception is functional in Stop mode. It generates a wake-up interrupt on Start. To generate a wake-up on address match or received frame event, the LPUART can run on LSE clock while the UART has to wake up or keep
- I2C address detection is functional in Stop mode. It generates a wake-up interrupt in case of address match. It will wake up the HSI during reception.



[&]quot;Y" = Yes (enable).
"O" = Optional can be enabled/disabled by software)
"-" = Not available

3.2 Interconnect matrix

Several peripherals are directly interconnected. This allows autonomous communication between peripherals, thus saving CPU resources and power consumption. In addition, these hardware connections allow fast and predictable latency.

Depending on peripherals, these interconnections can operate in Run, Sleep, Low-power run, Low-power sleep and Stop modes.

Table 5. STM32L053x6/8 peripherals interconnect matrix

Interconnect source	Interconnect destination	Interconnect action	Run	Sleep	Low- power run	Low- power sleep	Stop
COMPx	TIM2,TIM21, TIM22	Timer input channel, trigger from analog signals comparison	Y	Y	Y	Y	-
COMFX	LPTIM	Timer input channel, trigger from analog signals comparison	Υ	Υ	Y	Y	Y
TIMx	TIMx	Timer triggered by other timer	Υ	Y	Y	Y	-
DIC	TIM21	Timer triggered by Auto wake-up	Υ	Υ	Y	Y	-
RTC	LPTIM	Timer triggered by RTC event	Y	Y	Y	Y	Y
All clock source	TIMx	Clock source used as input channel for RC measurement and trimming	Υ	Y	Y	Y	-
USB	CRS/HSI48	the clock recovery system trims the HSI48 based on USB SOF	Y	Υ	-	-	-
GPIO	TIMx	Timer input channel and trigger	Y	Y	Y	Y	-
	LPTIM	Timer input channel and trigger	Y	Y	Y	Y	Y
	ADC,DAC	Conversion trigger	Υ	Y	Y	Y	-

3.3 Arm® Cortex®-M0+ core with MPU

The Cortex-M0+ processor is an entry-level 32-bit Arm Cortex processor designed for a broad range of embedded applications. It offers significant benefits to developers, including:

- a simple architecture that is easy to learn and program
- ultra-low power, energy-efficient operation
- excellent code density
- deterministic, high-performance interrupt handling
- upward compatibility with Cortex-M processor family
- platform security robustness, with integrated Memory Protection Unit (MPU).

The Cortex-M0+ processor is built on a highly area and power optimized 32-bit processor core, with a 2-stage pipeline Von Neumann architecture. The processor delivers exceptional energy efficiency through a small but powerful instruction set and extensively optimized design, providing high-end processing hardware including a single-cycle multiplier.

The Cortex-M0+ processor provides the exceptional performance expected of a modern 32-bit architecture, with a higher code density than other 8-bit and 16-bit microcontrollers.

Owing to its embedded Arm core, the STM32L053x6/8 are compatible with all Arm tools and software.

Nested vectored interrupt controller (NVIC)

The ultra-low-power STM32L053x6/8 embed a nested vectored interrupt controller able to handle up to 32 maskable interrupt channels and 4 priority levels.

The Cortex-M0+ processor closely integrates a configurable Nested Vectored Interrupt Controller (NVIC), to deliver industry-leading interrupt performance. The NVIC:

- includes a Non-Maskable Interrupt (NMI)
- provides zero jitter interrupt option
- provides four interrupt priority levels

The tight integration of the processor core and NVIC provides fast execution of Interrupt Service Routines (ISRs), dramatically reducing the interrupt latency. This is achieved through the hardware stacking of registers, and the ability to abandon and restart load-multiple and store-multiple operations. Interrupt handlers do not require any assembler wrapper code, removing any code overhead from the ISRs. Tail-chaining optimization also significantly reduces the overhead when switching from one ISR to another.

To optimize low-power designs, the NVIC integrates with the sleep modes, that include a deep sleep function that enables the entire device to enter rapidly stop or standby mode.

This hardware block provides flexible interrupt management features with minimal interrupt latency.

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3.4 Reset and supply management

3.4.1 Power supply schemes

- V_{DD} = 1.65 to 3.6 V: external power supply for I/Os and the internal regulator. Provided externally through V_{DD} pins.
- V_{SSA}, V_{DDA} = 1.65 to 3.6 V: external analog power supplies for ADC, DAC, reset blocks, RCs and PLL (minimum voltage to be applied to V_{DDA} is 1.8 V when the DAC is used). V_{DDA} and V_{SSA} must be connected to V_{DD} and V_{SS}, respectively.
- V_{DD_USB} = 1.65 to 3.6V: external power supply for USB transceiver, USB_DM (PA11) and USB_DP (PA12). To guarantee a correct voltage level for USB communication V_{DD_USB} must be above 3.0V. If USB is not used this pin must be tied to V_{DD} or V_{SS}. On packages without VDD_USB pin, V_{DD_USB} voltage is internally connected to V_{DD} voltage.

3.4.2 Power supply supervisor

The devices have an integrated ZEROPOWER power-on reset (POR)/power-down reset (PDR) that can be coupled with a brownout reset (BOR) circuitry.

Two versions are available:

- The version with BOR activated at power-on operates between 1.8 V and 3.6 V.
- The other version without BOR operates between 1.65 V and 3.6 V.

After the V_{DD} threshold is reached (1.65 V or 1.8 V depending on the BOR which is active or not at power-on), the option byte loading process starts, either to confirm or modify default thresholds, or to disable the BOR permanently: in this case, the VDD min value becomes 1.65 V (whatever the version, BOR active or not, at power-on).

When BOR is active at power-on, it ensures proper operation starting from 1.8 V whatever the power ramp-up phase before it reaches 1.8 V. When BOR is not active at power-up, the power ramp-up should guarantee that 1.65 V is reached on V_{DD} at least 1 ms after it exits the POR area.

Five BOR thresholds are available through option bytes, starting from 1.8 V to 3 V. To reduce the power consumption in Stop mode, it is possible to automatically switch off the internal reference voltage (V_{REFINT}) in Stop mode. The device remains in reset mode when V_{DD} is below a specified threshold, $V_{POR/PDR}$ or V_{BOR} , without the need for any external reset circuit.

Note:

The start-up time at power-on is typically 3.3 ms when BOR is active at power-up, the start-up time at power-on can be decreased down to 1 ms typically for devices with BOR inactive at power-up.

The devices feature an embedded programmable voltage detector (PVD) that monitors the $V_{DD/VDDA}$ power supply and compares it to the V_{PVD} threshold. This PVD offers 7 different levels between 1.85 V and 3.05 V, chosen by software, with a step around 200 mV. An interrupt can be generated when $V_{DD/VDDA}$ drops below the V_{PVD} threshold and/or when $V_{DD/VDDA}$ is higher than the V_{PVD} threshold. The interrupt service routine can then generate a warning message and/or put the MCU into a safe state. The PVD is enabled by software.

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3.4.3 Voltage regulator

The regulator has three operation modes: main (MR), low power (LPR) and power down.

- MR is used in Run mode (nominal regulation)
- LPR is used in the Low-power run, Low-power sleep and Stop modes
- Power down is used in Standby mode. The regulator output is high impedance, the kernel circuitry is powered down, inducing zero consumption but the contents of the registers and RAM are lost except for the standby circuitry (wake-up logic, IWDG, RTC, LSI, LSE crystal 32 KHz oscillator, RCC CSR).

3.5 Clock management

The clock controller distributes the clocks coming from different oscillators to the core and the peripherals. It also manages clock gating for low-power modes and ensures clock robustness. It features:

Clock prescaler

To get the best trade-off between speed and current consumption, the clock frequency to the CPU and peripherals can be adjusted by a programmable prescaler.

Safe clock switching

Clock sources can be changed safely on the fly in Run mode through a configuration register.

• Clock management

To reduce power consumption, the clock controller can stop the clock to the core, individual peripherals or memory.

System clock source

Three different clock sources can be used to drive the master clock SYSCLK:

- 1-25 MHz high-speed external crystal (HSE), that can supply a PLL
- 16 MHz high-speed internal RC oscillator (HSI), trimmable by software, that can supply a PLLMultispeed internal RC oscillator (MSI), trimmable by software, able to generate 7 frequencies (65 kHz, 131 kHz, 262 kHz, 524 kHz, 1.05 MHz, 2.1 MHz, 4.2 MHz). When a 32.768 kHz clock source is available in the system (LSE), the MSI frequency can be trimmed by software down to a ±0.5% accuracy.

Auxiliary clock source

Two ultra-low-power clock sources that can be used to drive the LCD controller and the real-time clock:

- 32.768 kHz low-speed external crystal (LSE)
- 37 kHz low-speed internal RC (LSI), also used to drive the independent watchdog.
 The LSI clock can be measured using the high-speed internal RC oscillator for greater precision.

RTC and LCD clock sources

The LSI, LSE or HSE sources can be chosen to clock the RTC and the LCD, whatever the system clock.

USB clock source

A 48 MHz clock trimmed through the USB SOF supplies the USB interface.

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Startup clock

After reset, the microcontroller restarts by default with an internal 2 MHz clock (MSI). The prescaler ratio and clock source can be changed by the application program as soon as the code execution starts.

Clock security system (CSS)

This feature can be enabled by software. If an HSE clock failure occurs, the master clock is automatically switched to HSI and a software interrupt is generated if enabled. Another clock security system can be enabled, in case of failure of the LSE it provides an interrupt or wake-up event which is generated if enabled.

Clock-out capability (MCO: microcontroller clock output)
 It outputs one of the internal clocks for external use by the application.

Several prescalers allow the configuration of the AHB frequency, each APB (APB1 and APB2) domains. The maximum frequency of the AHB and the APB domains is 32 MHz. See *Figure 2* for details on the clock tree.

@V33 Enable Watchdog Watchdog LS Legend: HSE = High-speed external clock signal LSI RC LSI tempo HSI = High-speed internal clock signal LSI = Low-speed internal clock signal RŢCSEL RTC2 enable LSE = Low-speed external clock signal MSI = Multispeed internal clock signal RTC LSE OSC LSE tempo LCD enable LSU LSD LSD LSD 1 MHz LCDCLK @V18 @V33 MCOSEL ADC enable LSI ADCCLK MSI RC LSE MSI Level shifters MCO / 1,2,4,8,16 @V18 not deepsleep / 2,4,8,16 CK_PWR @V33 not deepsleep HSI16 RC rchs / 1,4 HSI16 Level shifters **FCLK** not (sleep or System Clock HCI K not (sleep or /8 MSI SysTick @V33 Timer HSI16 AHB HSE OSC 4 MHz **PRESC** HSE PCLK1 to APB1 Level shifters / 1,2,..., 512 PĻĻSRC _{@V3}PLLCLK 32 MHz peripheralsi APB1 @V18 PRESC ck_pllin PLL / 1,2,4,8,16 LSU Peripheral @V33 3,4,6,8,12,16, clock enable 24,32,48 to TIMx 1 MHz Clock If (APB1 presc=1) x1 else x2) / 2,3,4 Detector Level shifters Peripheral @V_{DDCORE} clock enable PCLK2 to APB2 LSD Clock Source Dedicated 48MHz PLL output 32 MHz peripherals APB2 PRESC Control max. HSI48MSEL / 1,2,4,8,16 Peripheral @V33 clock enable to TIMx RC 48MHz If (APB2 presc=1) x1 HSI48 else x2) Level shifters @V18 Peripheral clock enable SYSCLK Clock Recovery LPTIMCLK System Peripheral LSE clock enable HSI16 LPUART/ **PCLK** Peripheral clock enable UARTCLK I2C1CLK usb en 48MHz USBCLK rng_en 48MHz RNG MS32912V3

Figure 2. Clock tree

3.6 Low-power real-time clock and backup registers

The real time clock (RTC) and the 5 backup registers are supplied in all modes including standby mode. The backup registers are five 32-bit registers used to store 20 bytes of user application data. They are not reset by a system reset, or when the device wakes up from Standby mode.

The RTC is an independent BCD timer/counter. Its main features are the following:

- Calendar with subsecond, seconds, minutes, hours (12 or 24 format), week day, date, month, year, in BCD (binary-coded decimal) format
- Automatically correction for 28, 29 (leap year), 30, and 31 day of the month
- Two programmable alarms with wake up from Stop and Standby mode capability
- Periodic wake-up from Stop and Standby with programmable resolution and period
- On-the-fly correction from 1 to 32767 RTC clock pulses. This can be used to synchronize it with a master clock.
- Reference clock detection: a more precise second source clock (50 or 60 Hz) can be used to enhance the calendar precision.
- Digital calibration circuit with 1 ppm resolution, to compensate for quartz crystal inaccuracy
- 2 anti-tamper detection pins with programmable filter. The MCU can be woken up from Stop and Standby modes on tamper event detection.
- Timestamp feature which can be used to save the calendar content. This function can be triggered by an event on the timestamp pin, or by a tamper event. The MCU can be woken up from Stop and Standby modes on timestamp event detection.

The RTC clock sources can be:

- A 32.768 kHz external crystal
- A resonator or oscillator
- The internal low-power RC oscillator (typical frequency of 37 kHz)
- The high-speed external clock

3.7 General-purpose inputs/outputs (GPIOs)

Each of the GPIO pins can be configured by software as output (push-pull or open-drain), as input (with or without pull-up or pull-down) or as peripheral alternate function. Most of the GPIO pins are shared with digital or analog alternate functions, and can be individually remapped using dedicated alternate function registers. All GPIOs are high current capable. Each GPIO output, speed can be slowed (40 MHz, 10 MHz, 2 MHz, 400 kHz). The alternate function configuration of I/Os can be locked if needed following a specific sequence in order to avoid spurious writing to the I/O registers. The I/O controller is connected to a dedicated IO bus with a toggling speed of up to 32 MHz.

Extended interrupt/event controller (EXTI)

The extended interrupt/event controller consists of 28 edge detector lines used to generate interrupt/event requests. Each line can be individually configured to select the trigger event (rising edge, falling edge, both) and can be masked independently. A pending register maintains the status of the interrupt requests. The EXTI can detect an external line with a pulse width shorter than the Internal APB2 clock period. Up to 51 GPIOs can be connected to the 16 configurable interrupt/event lines. The 12 other lines are connected to PVD, RTC, USB, USARTS, LPUART, LPTIMER or comparator events.



3.8 Memories

The STM32L053x6/8 devices have the following features:

- 8 Kbytes of embedded SRAM accessed (read/write) at CPU clock speed with 0 wait states. With the enhanced bus matrix, operating the RAM does not lead to any performance penalty during accesses to the system bus (AHB and APB buses).
- The non-volatile memory is divided into three arrays:
 - 32 or 64 Kbytes of embedded flash program memory
 - 2 Kbytes of data EEPROM
 - Information block containing 32 user and factory options bytes plus 4 Kbytes of system memory

The user options bytes are used to write-protect or read-out protect the memory (with 4 Kbyte granularity) and/or readout-protect the whole memory with the following options:

- Level 0: no protection
- Level 1: memory readout protected.
 - The flash memory cannot be read from or written to if either debug features are connected or boot in RAM is selected
- Level 2: chip readout protected, debug features (Cortex-M0+ serial wire) and boot in RAM selection disabled (debugline fuse)

The firewall protects parts of code/data from access by the rest of the code that is executed outside of the protected area. The granularity of the protected code segment or the non-volatile data segment is 256 bytes (flash memory or EEPROM) against 64 bytes for the volatile data segment (RAM).

The whole non-volatile memory embeds the error correction code (ECC) feature.

3.9 Boot modes

At startup, BOOT0 pin and nBOOT1 option bit are used to select one of three boot options:

- Boot from flash memory
- Boot from System memory
- · Boot from embedded RAM

The boot loader is located in System memory. It is used to reprogram the flash memory by using SPI1(PA4, PA5, PA6, PA7) or SPI2 (PB12, PB13, PB14, PB15), USART1(PA9, PA10) or USART2(PA2, PA3). See STM32 microcontroller system memory boot mode AN2606 for details.

3.10 Direct memory access (DMA)

The flexible 7-channel, general-purpose DMA is able to manage memory-to-memory, peripheral-to-memory and memory-to-peripheral transfers. The DMA controller supports circular buffer management, avoiding the generation of interrupts when the controller reaches the end of the buffer.

Each channel is connected to dedicated hardware DMA requests, with software trigger support for each channel. Configuration is done by software and transfer sizes between source and destination are independent.

The DMA can be used with the main peripherals: SPI, I²C, USART, LPUART, general-purpose timers, DAC, and ADC.

3.11 Liquid crystal display (LCD)

The LCD drives up to 8 common terminals and 32 segment terminals to drive up to 224 pixels.

- Internal step-up converter to guarantee functionality and contrast control irrespective of V_{DD}. This converter can be deactivated, in which case the V_{LCD} pin is used to provide the voltage to the LCD
- Supports static, 1/2, 1/3, 1/4 and 1/8 duty
- Supports static, 1/2, 1/3 and 1/4 bias
- Phase inversion to reduce power consumption and EMI
- Up to 8 pixels can be programmed to blink
- Unneeded segments and common pins can be used as general I/O pins
- LCD RAM can be updated at any time owing to a double-buffer
- The LCD controller can operate in Stop mode
- V_{I CD} rails decoupling capability

3.12 Analog-to-digital converter (ADC)

A native 12-bit, extended to 16-bit through hardware oversampling, analog-to-digital converter is embedded into STM32L053x6/8 device. It has up to 16 external channels and 3 internal channels (temperature sensor, voltage reference, V_{LCD} voltage measurement). Three channels, PA0, PA4 and PA5, are fast channels, while the others are standard channels.

The ADC performs conversions in single-shot or scan mode. In scan mode, automatic conversion is performed on a selected group of analog inputs.

The ADC frequency is independent from the CPU frequency, allowing maximum sampling rate of 1.14 MSPS even with a low CPU speed. The ADC consumption is low at all frequencies (\sim 25 μ A at 10 kSPS, \sim 200 μ A at 1MSPS). An auto-shutdown function guarantees that the ADC is powered off except during the active conversion phase.

The ADC can be served by the DMA controller. It can operate from a supply voltage down to 1.65 V.

The ADC features a hardware oversampler up to 256 samples, this improves the resolution to 16 bits (see AN2668).



An analog watchdog feature allows very precise monitoring of the converted voltage of one, some or all scanned channels. An interrupt is generated when the converted voltage is outside the programmed thresholds.

The events generated by the general-purpose timers (TIMx) can be internally connected to the ADC start triggers, to allow the application to synchronize A/D conversions and timers.

3.13 Temperature sensor

The temperature sensor (T_{SENSE}) generates a voltage V_{SENSE} that varies linearly with temperature.

The temperature sensor is internally connected to the ADC_IN18 input channel which is used to convert the sensor output voltage into a digital value.

The sensor provides good linearity but it has to be calibrated to obtain good overall accuracy of the temperature measurement. As the offset of the temperature sensor varies from chip to chip due to process variation, the uncalibrated internal temperature sensor is suitable for applications that detect temperature changes only.

To improve the accuracy of the temperature sensor measurement, each device is individually factory-calibrated by ST. The temperature sensor factory calibration data are stored by ST in the system memory area, accessible in read-only mode.

Calibration value name	Description	Memory address
TSENSE_CAL1	TS ADC raw data acquired at temperature of 30 °C, V _{DDA} = 3 V	0x1FF8 007A - 0x1FF8 007B
TSENSE_CAL2	TS ADC raw data acquired at temperature of 130 °C V _{DDA} = 3 V	0x1FF8 007E - 0x1FF8 007F

Table 6. Temperature sensor calibration values

3.13.1 Internal voltage reference (V_{REFINT})

The internal voltage reference (V_{REFINT}) provides a stable (bandgap) voltage output for the ADC and Comparators. V_{REFINT} is internally connected to the ADC_IN17 input channel. It enables accurate monitoring of the V_{DD} value (when no external voltage, V_{REF+} , is available for ADC). The precise voltage of V_{REFINT} is individually measured for each part by ST during production test and stored in the system memory area. It is accessible in read-only mode.

Table 7. Internal voltage reference measured values

Calibration value name	Description	Memory address
VREFINT_CAL	Raw data acquired at temperature of 25 °C V _{DDA} = 3 V	0x1FF8 0078 - 0x1FF8 0079

3.13.2 V_{LCD} voltage monitoring

This embedded hardware feature allows the application to measure the V_{LCD} supply voltage using the internal ADC channel ADC_IN16. As the V_{LCD} voltage may be higher than V_{DDA} , and thus outside the ADC input range, the ADC input is connected to LCD_VLCD1 (which provides $1/3V_{LCD}$ when the LCD is configured 1/3Bias and $1/4V_{LCD}$ when the LCD is configured 1/4Bias or 1/2Bias).

3.14 Digital-to-analog converter (DAC)

One 12-bit buffered DAC can be used to convert digital signal into analog voltage signal output. An optional amplifier can be used to reduce the output signal impedance.

This digital Interface supports the following features:

- One data holding register
- Left or right data alignment in 12-bit mode
- Synchronized update capability
- Noise-wave generation
- Triangular-wave generation
- DMA capability (including the underrun interrupt)
- External triggers for conversion
- Input reference voltage V_{RFF+}

Four DAC trigger inputs are used in the STM32L053x6/8. The DAC channel is triggered through the timer update outputs that are also connected to different DMA channels.

3.15 Ultra-low-power comparators and reference voltage

The STM32L053x6/8 embed two comparators sharing the same current bias and reference voltage. The reference voltage can be internal or external (coming from an I/O).

- One comparator with ultra low consumption
- One comparator with rail-to-rail inputs, fast or slow mode.
- The threshold can be one of the following:
 - DAC output
 - External I/O pins
 - Internal reference voltage (V_{RFFINT})
 - submultiple of Internal reference voltage(1/4, 1/2, 3/4) for the rail to rail comparator.

Both comparators can wake up the devices from Stop mode, and be combined into a window comparator.

The internal reference voltage is available externally via a low-power / low-current output buffer (driving current capability of 1 µA typical).

3.16 System configuration controller

The system configuration controller provides the capability to remap some alternate functions on different I/O ports.

The highly flexible routing interface allows the application firmware to control the routing of different I/Os to the TIM2, TIM21, TIM22 and LPTIM timer input captures. It also controls the routing of internal analog signals to the USB internal oscillator, ADC, COMP1 and COMP2 and the internal reference voltage $V_{\sf RFFINT}$.

3.17 Touch sensing controller (TSC)

The STM32L053x6/8 provide a simple solution for adding capacitive sensing functionality to any application. These devices offer up to 24 capacitive sensing channels distributed over 8 analog I/O groups.

Capacitive sensing technology is able to detect the presence of a finger near a sensor which is protected from direct touch by a dielectric (such as glass, plastic). The capacitive variation introduced by the finger (or any conductive object) is measured using a proven implementation based on a surface charge transfer acquisition principle. It consists of charging the sensor capacitance and then transferring a part of the accumulated charges into a sampling capacitor until the voltage across this capacitor has reached a specific threshold. To limit the CPU bandwidth usage, this acquisition is directly managed by the hardware touch sensing controller and only requires few external components to operate.

The touch sensing controller is fully supported by the STMTouch touch sensing firmware library, which is free to use and allows touch sensing functionality to be implemented reliably in the end application.

Table 8. Capacitive sensing GPIOs available on STM32L053x6/8 devices

	_		
Group	Capacitive sensing signal name	Pin name	G
	TSC_G1_IO1	PA0	
1	TSC_G1_IO2	PA1	
'	TSC_G1_IO3	PA2	
	TSC_G1_IO4	PA3	
	TSC_G2_IO1	PA4 ⁽¹⁾	
2	TSC_G2_IO2	PA5	
2	TSC_G2_IO3	PA6	
	TSC_G2_IO4	PA7	
3	TSC_G3_IO1	PC5	
	TSC_G3_IO2	PB0	
	TSC_G3_IO3	PB1	
	TSC_G3_IO4	PB2	

Group	Capacitive sensing signal name	Pin name
	TSC_G5_IO1	PB3
5	TSC_G5_IO2	PB4
	TSC_G5_IO3	PB6
	TSC_G5_IO4	PB7
	TSC_G6_IO1	PB11
6	TSC_G6_IO2	PB12
	TSC_G6_IO3	PB13
	TSC_G6_IO4	PB14
	TSC_G7_IO1	PC0
7	TSC_G7_IO2	PC1
,	TSC_G7_IO3	PC2
	TSC_G7_IO4	PC3

Group	Capacitive sensing signal name	Pin name	Group	Capacitive sensing signal name	Pin name
	TSC_G4_IO1	PA9		TSC_G8_IO1	PC6
4 -	TSC_G4_IO2	PA10	8	TSC_G8_IO2	PC7
	TSC_G4_IO3	PA11	0	TSC_G8_IO3	PC8
	TSC_G4_IO4	PA12		TSC_G8_IO4	PC9

Table 8. Capacitive sensing GPIOs available on STM32L053x6/8 devices

3.18 Timers and watchdogs

The ultra-low-power STM32L053x6/8 devices include three general-purpose timers, one low-power timer (LPTIM), one basic timer, two watchdog timers and the SysTick timer.

Table 9 compares the features of the general-purpose and basic timers.

DMA Counter Capture/compare Complementary Timer Counter type Prescaler factor request resolution channels outputs generation Up, down, Any integer between TIM2 16-bit Yes 4 No up/down 1 and 65536 TIM21, Up, down, Any integer between 16-bit No 2 No TIM22 up/down 1 and 65536 Any integer between TIM6 16-bit Up Yes 0 No 1 and 65536

Table 9. Timer feature comparison

3.18.1 General-purpose timers (TIM2, TIM21 and TIM22)

There are three synchronizable general-purpose timers embedded in the STM32L053x6/8 devices (see *Table 9* for differences).

TIM₂

TIM2 is based on 16-bit auto-reload up/down counter. It includes a 16-bit prescaler. It features four independent channels each for input capture/output compare, PWM or one-pulse mode output.

The TIM2 general-purpose timers can work together or with the TIM21 and TIM22 general-purpose timers via the Timer Link feature for synchronization or event chaining. Their counter can be frozen in debug mode. Any of the general-purpose timers can be used to generate PWM outputs.

TIM2 has independent DMA request generation.

This timer is capable of handling quadrature (incremental) encoder signals and the digital outputs from 1 to 3 hall-effect sensors.



[.] This GPIO offers a reduced touch sensing sensitivity. It is thus recommended to use it as sampling capacitor I/O.

TIM21 and TIM22

TIM21 and TIM22 are based on a 16-bit auto-reload up/down counter. They include a 16-bit prescaler. They have two independent channels for input capture/output compare, PWM or one-pulse mode output. They can work together and be synchronized with the TIM2, full-featured general-purpose timers.

They can also be used as simple time bases and be clocked by the LSE clock source (32.768 kHz) to provide time bases independent from the main CPU clock.

3.18.2 Low-power Timer (LPTIM)

The low-power timer has an independent clock and is running also in Stop mode if it is clocked by LSE, LSI or an external clock. It is able to wake up the devices from Stop mode.

This low-power timer supports the following features:

- 16-bit up counter with 16-bit autoreload register
- 16-bit compare register
- Configurable output: pulse, PWM
- Continuous / one shot mode
- Selectable software / hardware input trigger
- Selectable clock source
 - Internal clock source: LSE, LSI, HSI or APB clock
 - External clock source over LPTIM input (working even with no internal clock source running, used by the Pulse Counter Application)
- Programmable digital glitch filter
- Encoder mode

3.18.3 Basic timer (TIM6)

This timer can be used as a generic 16-bit timebase. It is mainly used for DAC trigger generation.

3.18.4 SysTick timer

This timer is dedicated to the OS, but could also be used as a standard downcounter. It is based on a 24-bit downcounter with autoreload capability and a programmable clock source. It features a maskable system interrupt generation when the counter reaches '0'.

3.18.5 Independent watchdog (IWDG)

The independent watchdog is based on a 12-bit downcounter and 8-bit prescaler. It is clocked from an independent 37 kHz internal RC and, as it operates independently of the main clock, it can operate in Stop and Standby modes. It can be used either as a watchdog to reset the device when a problem occurs, or as a free-running timer for application timeout management. It is hardware- or software-configurable through the option bytes. The counter can be frozen in debug mode.

3.18.6 Window watchdog (WWDG)

The window watchdog is based on a 7-bit downcounter that can be set as free-running. It can be used as a watchdog to reset the device when a problem occurs. It is clocked from the main clock. It has an early warning interrupt capability and the counter can be frozen in debug mode.

3.19 Communication interfaces

3.19.1 I²C bus

Two I²C interface (I2C1, I2C2) can operate in multicontroller or target modes.

Each I²C interface can support Standard mode (Sm, up to 100 kbit/s), Fast mode (Fm, up to 400 kbit/s) and Fast Mode Plus (Fm+, up to 1 Mbit/s) with 20 mA output drive on some I/Os.

7-bit and 10-bit addressing modes, multiple 7-bit target addresses (2 addresses, 1 with configurable mask) are also supported as well as programmable analog and digital noise filters.

Analog filter Digital filter Pulse width of Programmable length from 1 to 15 ≥ 50 ns I2C peripheral clocks suppressed spikes 1. Extra filtering capability vs. **Benefits** standard requirements. Available in Stop mode 2. Stable length Wake-up from Stop on address Variations depending on Drawbacks match is not available when digital temperature, voltage, process filter is enabled.

Table 10. Comparison of I2C analog and digital filters

In addition, I2C1 provides hardware support for SMBus 2.0 and PMBus 1.1: ARP capability, Host notify protocol, hardware CRC (PEC) generation/verification, timeouts verifications and ALERT protocol management. I2C1 also has a clock domain independent from the CPU clock, allowing the I2C1 to wake up the MCU from Stop mode on address match.

Each I2C interface can be served by the DMA controller.

Refer to Table 11 for an overview of I2C interface features.

Table 11. STM32L053x6/8 I²C implementation

I2C features ⁽¹⁾	I2C1	I2C2
7-bit addressing mode	Х	Х
10-bit addressing mode	Х	Х
Standard mode (up to 100 kbit/s)	Х	Х
Fast mode (up to 400 kbit/s)	Х	Х
Fast Mode Plus with 20 mA output drive I/Os (up to 1 Mbit/s)	Х	X ⁽²⁾
Independent clock	Х	-

Table 11. STM32L053x6/8 I²C implementation (continued)

I2C features ⁽¹⁾	I2C1	I2C2
SMBus	Х	-
Wake-up from Stop	Х	-

^{1.} X = supported.

3.19.2 Universal synchronous/asynchronous receiver transmitter (USART)

The two USART interfaces (USART1, USART2) are able to communicate at speeds of up to 4 Mbit/s.

They provide hardware management of the CTS, RTS and RS485 driver enable (DE) signals, multiprocessor communication mode, master synchronous communication and single-wire half-duplex communication mode. They also support SmartCard communication (ISO 7816), IrDA SIR ENDEC, LIN master/slave capability, auto baud rate feature and has a clock domain independent from the CPU clock, allowing to wake up the MCU from Stop mode using baudrates up to 42 Kbaud.

All USART interfaces can be served by the DMA controller.

Table 12 for the supported modes and features of USART interfaces.

Table 12. USART implementation

USART modes/features ⁽¹⁾	USART1 and USART2
Hardware flow control for modem	Х
Continuous communication using DMA	Х
Multiprocessor communication	Х
Synchronous SPI mode (master/slave)	Х
Smartcard mode	Х
Single-wire half-duplex communication	Х
IrDA SIR ENDEC block	Х
LIN mode	Х
Dual clock domain and wake-up from Stop mode	Х
Receiver timeout interrupt	Х
Modbus communication	Х
Auto baud rate detection (4 modes)	Х
Driver Enable	Х

^{1.} X = supported.

3.19.3 Low-power universal asynchronous receiver transmitter (LPUART)

The devices embed one Low-power UART. The LPUART supports asynchronous serial communication with minimum power consumption. It supports half duplex single wire communication and modem operations (CTS/RTS). It allows multiprocessor communication.



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See Table 15: STM32L053x6/8 pin definitions on page 41 for the list of I/Os that feature Fast Mode Plus capability

The LPUART has a clock domain independent from the CPU clock. It can wake up the system from Stop mode using baudrates up to 46 Kbaud. The wake-up events from Stop mode are programmable and can be:

- Start bit detection
- Or any received data frame
- Or a specific programmed data frame

Only a 32.768 kHz clock (LSE) is needed to allow LPUART communication up to 9600 baud. Therefore, even in Stop mode, the LPUART can wait for an incoming frame while having an extremely low energy consumption. Higher speed clock can be used to reach higher baudrates.

LPUART interface can be served by the DMA controller.

3.19.4 Serial peripheral interface (SPI)/Inter-integrated sound (I2S)

Up to two SPIs are able to communicate at up to 16 Mbits/s in slave and master modes in full-duplex and half-duplex communication modes. The 3-bit prescaler gives 8 master mode frequencies and the frame is configurable to 8 bits or 16 bits. The hardware CRC generation/verification supports basic SD Card/MMC modes.

The USARTs with synchronous capability can also be used as SPI master.

One standard I2S interfaces (multiplexed with SPI2) is available. It can operate in master or slave mode, and can be configured to operate with a 16-/32-bit resolution as input or output channels. Audio sampling frequencies from 8 kHz up to 192 kHz are supported. When the I2S interfaces is configured in master mode, the master clock can be output to the external DAC/CODEC at 256 times the sampling frequency.

The SPIs can be served by the DMA controller.

Refer to *Table 13* for the differences between SPI1 and SPI2.

 SPI features⁽¹⁾
 SPI1
 SPI2

 Hardware CRC calculation
 X
 X

 I2S mode
 X

 TI mode
 X
 X

Table 13. SPI/I2S implementation

3.19.5 Universal serial bus (USB)

The STM32L053x6/8 embed a full-speed USB device peripheral compliant with the USB specification version 2.0. The internal USB PHY supports USB FS signaling, embedded DP pull-up and also battery charging detection according to Battery Charging Specification Revision 1.2. The USB interface implements a full-speed (12 Mbit/s) function interface with added support for USB 2.0 Link Power Management. It has software-configurable endpoint setting with packet memory up to 1 Kbyte and suspend/resume support. It requires a precise 48 MHz clock which can be generated from the internal main PLL (the clock source must use a HSE crystal oscillator) or by the internal 48 MHz oscillator in automatic trimming mode. The synchronization for this oscillator can be taken from the USB data stream itself (SOF signalization) which allows crystal-less operation.



^{1.} X = supported.

3.20 Clock recovery system (CRS)

The STM32L053x6/8 embed a special block which allows automatic trimming of the internal 48 MHz oscillator to guarantee its optimal accuracy over the whole device operational range. This automatic trimming is based on the external synchronization signal, which could be either derived from USB SOF signalization, from LSE oscillator, from an external signal on CRS_SYNC pin or generated by user software. For faster lock-in during startup it is also possible to combine automatic trimming with manual trimming action.

3.21 Cyclic redundancy check (CRC) calculation unit

The CRC (cyclic redundancy check) calculation unit is used to get a CRC code using a configurable generator polynomial value and size.

Among other applications, CRC-based techniques are used to verify data transmission or storage integrity. In the scope of the EN/IEC 60335-1 standard, they offer a means of verifying the flash memory integrity. The CRC calculation unit helps compute a signature of the software during runtime, to be compared with a reference signature generated at linktime and stored at a given memory location.

3.22 Serial wire debug port (SW-DP)

An Arm SW-DP interface is provided to allow a serial wire debugging tool to be connected to the MCU.

4 Pin descriptions

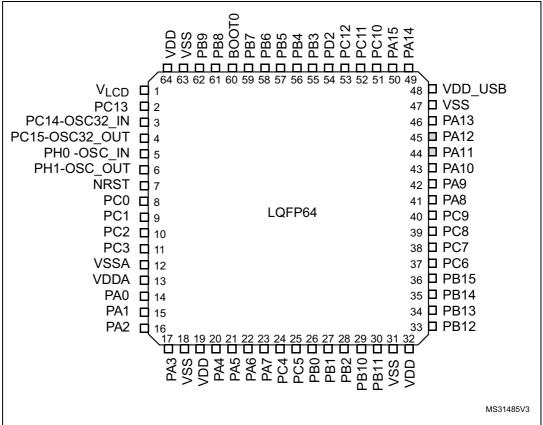


Figure 3. STM32L053x6/8 LQFP64 pinout

- 1. The above figure shows the package top view.
- 2. The I/O pins supplied by VDD_USB are shown in grey.

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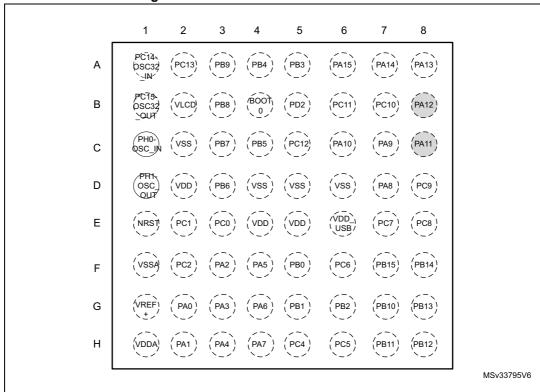


Figure 4. STM32L053x6/8 TFBGA64 ballout

- 1. The above figure shows the package top view.
- 2. the I/O pins supplied by VDD_USB are shown in grey.

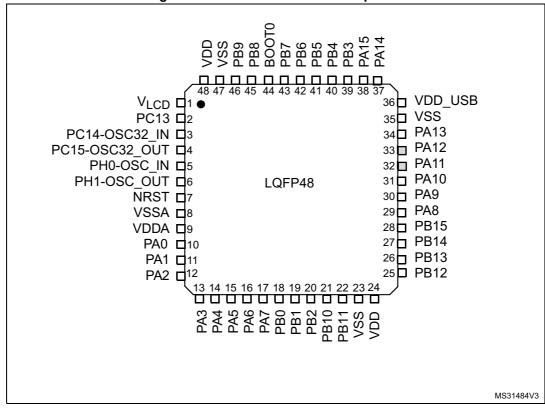


Figure 5. STM32L053x6/8 LQFP48 pinout

- 1. The above figure shows the package top view.
- 2. The I/O pins supplied by VDD_USB are shown in grey.

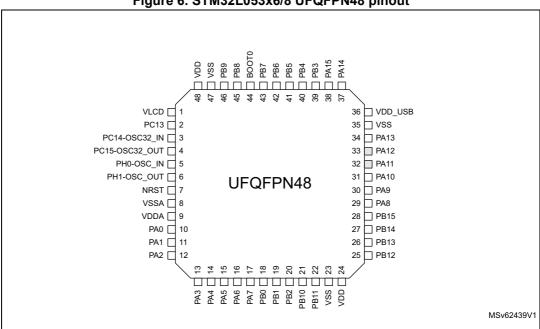


Figure 6. STM32L053x6/8 UFQFPN48 pinout

- The above figure shows the package top view.
- 2. The I/O pins supplied by VDD_USB are shown in grey.

Table 14. Legend/abbreviations used in the pinout table

Nar	ne	Abbreviation	Definition				
Pin na	ame	Unless otherwise specified in brackets below the pin name, the pin function during and after reset is the same as the actual pin name					
		S	Supply pin				
Pin t	ype	I	Input only pin				
		I/O	Input / output pin				
		FT	5 V tolerant I/O				
		FTf 5 V tolerant I/O, FM+ capable					
I/O stru	ucture	TC	Standard 3.3V I/O				
		B Dedicated BOOT0 pin					
		RST	Bidirectional reset pin with embedded weak pull-up resistor				
Not	es	Unless otherwise specifie	Unless otherwise specified by a note, all I/Os are set as floating inputs during and after reset.				
Pin functions	Alternate functions	Functions selected through GPIOx_AFR registers					
THITUHCUOTIS	Additional functions	Functions dire	ctly selected/enabled through peripheral registers				

Table 15. STM32L053x6/8 pin definitions

F	Pin nu	umbe	r						
LQFP48	UFQFPN48	LQFP64	TFBGA64	Pin name (function after reset)	Pin type	I/O structure	Notes	Alternate functions	Additional functions
1	1	1	B2	VLCD	S	-	-	-	-
2	2	2	A2	PC13	I/O	FT	-	-	RTC_TAMP1/RTC_TS/RT C_OUT/WKUP2
3	3	3	A1	PC14-OSC32_IN (PC14)	I/O	FT	-	•	OSC32_IN
4	4	4	B1	PC15- OSC32_OUT (PC15)	I/O	TC	-	-	OSC32_OUT
5	5	5	C1	PH0-OSC_IN (PH0)	I/O	TC	-	USB_CRS_SYNC	OSC_IN
6	6	6	D1	PH1-OSC_OUT (PH1)	I/O	TC	-	-	OSC_OUT

Table 15. STM32L053x6/8 pin definitions (continued)

F	Pin nu	ımbe	er					·	,
LQFP48	UFQFPN48	LQFP64	TFBGA64	Pin name (function after reset)	Pin type	I/O structure	Alternate functions		Additional functions
7	-	7	E1	NRST	I/O	RST	-	-	-
-	-	8	E3	PC0	I/O	FT	-	LPTIM1_IN1, LCD_SEG18, EVENTOUT, TSC_G7_IO1	ADC_IN10
-	-	9	E2	PC1	I/O	FT	-	LPTIM1_OUT, LCD_SEG19, EVENTOUT, TSC_G7_IO2	ADC_IN11
-	1	10	F2	PC2	I/O	FT	1	LPTIM1_IN2, LCD_SEG20, SPI2_MISO/I2S2_MCK, TSC_G7_IO3	ADC_IN12
-	1	11	1	PC3	I/O	FT	1	LPTIM1_ETR, LCD_SEG21, SPI2_MOSI/I2S2_SD, TSC_G7_IO4	ADC_IN13
8	8	12	F1	VSSA	S	-	-	-	-
-	1	ı	G1	VREF+	S	-	ı	-	-
9	9	13	H1	VDDA	S	-	-	-	-
10	10	14	G2	PA0	I/O	TC	-	TIM2_CH1,TSC_G1_IO1, USART2_CTS, TIM2_ETR, COMP1_OUT	COMP1_INM6, ADC_IN0, RTC_TAMP2/WKUP1
11	11	15	H2	PA1	I/O	FT	-	EVENTOUT, LCD_SEG0, TIM2_CH2, TSC_G1_IO2, USART2_RTS/ USART2_DE, TIM21_ETR	COMP1_INP, ADC_IN1
12	12	16	F3	PA2	I/O	FT	-	TIM21_CH1, LCD_SEG1, TIM2_CH3, TSC_G1_IO3, USART2_TX, COMP2_OUT	COMP2_INM6, ADC_IN2
13	13	17	G3	PA3	I/O	FT	-	TIM21_CH2, LCD_SEG2, TIM2_CH4, TSC_G1_IO4, USART2_RX	COMP2_INP, ADC_IN3
-	-	18	C2	VSS	S		-	-	-

Table 15. STM32L053x6/8 pin definitions (continued)

F	Pin nı	ımbe	r				-	,	,
LQFP48	UFQFPN48	LQFP64	TFBGA64	Pin name (function after reset)	Pin type	I/O structure	Notes	Alternate functions	Additional functions
-	-	19	D2	VDD	S		-	-	-
14	14	20	НЗ	PA4	I/O	TC	(1)	SPI1_NSS,TSC_G2_IO1, USART2_CK, TIM22_ETR	COMP1_INM4, COMP2_INM4, ADC_IN4, DAC_OUT
15	15	21	F4	PA5	I/O	TC	(1)	SPI1_SCK, TIM2_ETR, TSC_G2_IO2, TIM2_CH1	COMP1_INM5, COMP2_INM5, ADC_IN5
16	16	22	G4	PA6	I/O	FT	-	SPI1_MISO, LCD_SEG3, TSC_G2_IO3, LPUART1_CTS, TIM22_CH1, EVENTOUT, COMP1_OUT	ADC_IN6
17	17	23	H4	PA7	I/O	FT	-	SPI1_MOSI, LCD_SEG4, TSC_G2_IO4, TIM22_CH2, EVENTOUT, COMP2_OUT	ADC_IN7
-	-	24	H5	PC4	I/O	FT	-	EVENTOUT, LCD_SEG22, LPUART1_TX	ADC_IN14
-	-	25	H6	PC5	I/O	FT	-	LCD_SEG23, LPUART1_RX, TSC_G3_IO1	ADC_IN15
18	18	26	F5	PB0	I/O	FT	-	EVENTOUT, LCD_SEG5, TSC_G3_IO2	LCD_VLCD3, ADC_IN8, VREF_OUT
19	19	27	G5	PB1	I/O	FT	-	LCD_SEG6, TSC_G3_IO3, LPUART1_RTS/ LPUART1_DE	ADC_IN9, VREF_OUT
20	20	28	G6	PB2	I/O	FT	-	LPTIM1_OUT, TSC_G3_IO4	LCD_VLCD2
21	21	29	G7	PB10	I/O	FT	-	LCD_SEG10, TIM2_CH3, TSC_SYNC, LPUART1_TX, SPI2_SCK, I2C2_SCL	-
22	22	30	H7	PB11	I/O	FT	-	EVENTOUT, LCD_SEG11, TIM2_CH4, TSC_G6_IO1, LPUART1_RX, I2C2_SDA	-

Table 15. STM32L053x6/8 pin definitions (continued)

F	Pin nu	ımbe	r	10.0010				definitions (continued	,
LQFP48	UFQFPN48	LQFP64	TFBGA64	Pin name (function after reset)	Pin type	I/O structure	Notes	Alternate functions	Additional functions
23	23	31	D6	VSS	S		-	-	-
24	24	32	E5	VDD	S		-	-	-
25	25	33	Н8	PB12	I/O	FT	-	SPI2_NSS/I2S2_WS, LCD_SEG12, LPUART1_RTS/ LPUART1_DE, TSC_G6_IO2, I2C2_SMBA, EVENTOUT	LCD_VLCD1
26	26	34	G8	PB13	I/O	FTf	-	SPI2_SCK/I2S2_CK, LCD_SEG13, TSC_G6_IO3, LPUART1_CTS, I2C2_SCL, TIM21_CH1	-
27	27	35	F8	PB14	I/O	FTf	1	SPI2_MISO/I2S2_MCK, LCD_SEG14, RTC_OUT, TSC_G6_IO4, LPUART1_RTS/ LPUART1_DE, I2C2_SDA, TIM21_CH2	-
28	28	36	F7	PB15	I/O	FT	-	SPI2_MOSI/I2S2_SD, LCD_SEG15, RTC_REFIN	-
-	-	37	F6	PC6	I/O	FT	-	TIM22_CH1, LCD_SEG24, TSC_G8_IO1	-
-	-	38	E7	PC7	I/O	FT	-	TIM22_CH2, LCD_SEG25, TSC_G8_IO2	-
-	-	39	E8	PC8	I/O	FT	-	TIM22_ETR, LCD_SEG26, TSC_G8_IO3	-
-	-	40	D8	PC9	I/O	FT	-	TIM21_ETR, LCD_SEG27, USB_NOE, TSC_G8_IO4	-

Table 15. STM32L053x6/8 pin definitions (continued)

F	Pin nı	ımbe	r				•	r deminions (continued	,
LQFP48	UFQFPN48	LQFP64	TFBGA64	Pin name (function after reset)	Pin type	I/O structure	Notes	Alternate functions	Additional functions
29	29	41	D7	PA8	I/O	FT	-	MCO, LCD_COM0, USB_CRS_SYNC, EVENTOUT, USART1_CK	-
30	30	42	C7	PA9	I/O	FT	-	MCO, LCD_COM1, TSC_G4_IO1, USART1_TX	-
31	31	43	C6	PA10	I/O	FT	-	LCD_COM2, TSC_G4_IO2, USART1_RX	-
32	32	44	C8	PA11	I/O	FT	(2)	SPI1_MISO, EVENTOUT, TSC_G4_IO3, USART1_CTS, COMP1_OUT	USB_DM
33	33	45	B8	PA12	I/O	FT	(2)	SPI1_MOSI, EVENTOUT, TSC_G4_IO4, USART1_RTS/ USART1_DE, COMP2_OUT	USB_DP
34	34	46	A8	PA13	I/O	FT	-	SWDIO, USB_NOE	-
35	35	47	D5	VSS	S		-	-	-
36	36	48	E6	VDD_USB	S		-	-	-
37	37	49	A7	PA14	I/O	FT	-	SWCLK, USART2_TX	-
38	38	50	A6	PA15	I/O	FT	-	SPI1_NSS, LCD_SEG17, TIM2_ETR, EVENTOUT, USART2_RX, TIM2_CH1	-
-	-	51	В7	PC10	I/O	FT	-	LPUART1_TX, LCD_COM4/LCD_SEG28 /LCD_SEG40	-
-	-	52	В6	PC11	I/O	FT	-	LPUART1_RX, LCD_COM5/LCD_SEG29 /LCD_SEG41	-
-	-	53	C5	PC12	I/O	FT	-	LCD_COM6/LCD_SEG30 /LCD_SEG42	-

Table 15. STM32L053x6/8 pin definitions (continued)

F	Pin nu	ımbe	r				•	r deminions (continued	
LQFP48	UFQFPN48	LQFP64	TFBGA64	Pin name (function after reset)	Pin type	I/O structure	Notes	Alternate functions	Additional functions
-	-	54	B5	PD2	I/O	FT	ı	LPUART1_RTS/ LPUART1_DE, LCD_COM7/LCD_SEG31 /LCD_SEG43	-
39	39	55	A5	PB3	I/O	FT	-	SPI1_SCK, LCD_SEG7, TIM2_CH2, TSC_G5I_O1, EVENTOUT	COMP2_INN
40	40	56	A4	PB4	I/O	FT	-	SPI1_MISO, LCD_SEG8, EVENTOUT, TSC_G5_IO2, TIM22_CH1	COMP2_INP
41	41	57	C4	PB5	I/O	FT	-	SPI1_MOSI, LCD_SEG9, LPTIM1_IN1, I2C1_SMBA, TIM22_CH2	COMP2_INP
42	42	58	D3	PB6	I/O	FTf	-	USART1_TX, I2C1_SCL, LPTIM1_ETR, TSC_G5_IO3	COMP2_INP
43	43	59	СЗ	PB7	I/O	FTf	-	USART1_RX, I2C1_SDA, LPTIM1_IN2, TSC_G5_IO4	COMP2_INP, PVD_IN
44	44	60	В4	BOOT0	-	В	-	-	-
45	45	61	В3	PB8	I/O	FTf	ı	LCD_SEG16, TSC_SYNC, I2C1_SCL	-
46	46	62	А3	PB9	I/O	FTf	-	LCD_COM3, EVENTOUT, I2C1_SDA, SPI2_NSS/I2S2_WS	-
47	47	63	D4	VSS	S	-	-	-	-
48	48	64	E4	VDD	S	-	-	-	-

^{1.} PA4 and PA5 offer a reduced touch sensing sensitivity. It is thus recommended to use them as sampling capacitor I/Os.

^{2.} These pins are powered by VDD_USB. For all characteristics that refer to V_{DD} , V_{DD_USB} must be used instead.



Table 16. Alternate function port A

		AF0	AF1	AF2	AF3	AF4	AF5	AF6	AF7
Po	ort	SPI1/TIM21/SYS_A F/EVENTOUT/	LCD	USB/TIM2/ EVENTOUT/	TSC/ EVENTOUT	USART1/2/3	TIM2/21/22	EVENTOUT	COMP1/2
	PA0	-	-	TIM2_CH1	TSC_G1_IO1	USART2_CTS	TIM2_ETR	-	COMP1_OUT
	PA1	EVENTOUT	LCD_SEG0	TIM2_CH2	TSC_G1_IO2	USART2_RTS/ USART2_DE	TIM21_ETR	-	-
	PA2	TIM21_CH1	LCD_SEG1	TIM2_CH3	TSC_G1_IO3	USART2_TX	-	-	COMP2_OUT
	PA3	TIM21_CH2	LCD_SEG2	TIM2_CH4	TSC_G1_IO4	USART2_RX	-	-	-
	PA4 (1)	SPI1_NSS	-	-	TSC_G2_IO1	USART2_CK	TIM22_ETR	-	-
	PA5 ⁽	SPI1_SCK	-	TIM2_ETR	TSC_G2_IO2	-	TIM2_CH1	-	-
	PA6	SPI1_MISO	LCD_SEG3	-	TSC_G2_IO3	LPUART1_CTS	TIM22_CH1	EVENTOUT	COMP1_OUT
Port A	PA7	SPI1_MOSI	LCD_SEG4	-	TSC_G2_IO4	-	TIM22_CH2	EVENTOUT	COMP2_OUT
	PA8	MCO	LCD_COM0	USB_CRS_SYNC	EVENTOUT	USART1_CK	-	-	-
	PA9	MCO	LCD_COM1	-	TSC_G4_IO1	USART1_TX	-	-	-
	PA10	-	LCD_COM2	-	TSC_G4_IO2	USART1_RX	-	-	-
	PA11	SPI1_MISO	-	EVENTOUT	TSC_G4_IO3	USART1_CTS	-	-	COMP1_OUT
	PA12	SPI1_MOSI	-	EVENTOUT	TSC_G4_IO4	USART1_RTS/ USART1_DE	-	-	COMP2_OUT
	PA13	SWDIO	-	USB_NOE	-	-	-	-	-
	PA14	SWCLK	-	-	-	USART2_TX	-	-	-
	PA15	SPI1_NSS	LCD_SEG17	TIM2_ETR	EVENTOUT	USART2_RX	TIM2_CH1	-	-

^{1.} PA4 and PA5 offer a reduced touch sensing sensitivity. It is thus recommended to use them as sampling capacitor I/Os.

Pin descriptions

Table	17. Alternate fund	tion port B
	_	

		AF0	AF1	AF2	AF3	AF4	AF5	AF6
Po	ort	SPI1/SPI2/I2S2/ USART1/ EVENTOUT/	I2C1/LCD	LPUART1/LPTIM /TIM2/SYS_AF/ EVENTOUT	I2C1/TSC	I2C1/TIM22/ EVENTOUT/ LPUART1	SPI2/I2S2/I2C2	I2C2/TIM21/ EVENTOUT
	PB0	EVENTOUT	LCD_SEG5	-	TSC_G3_IO2	-	-	-
	PB1	-	LCD_SEG6	-	TSC_G3_IO3	LPUART1_RTS/ LPUART1_DE	-	-
	PB2	-	-	LPTIM1_OUT	TSC_G3_IO4	-	-	-
	PB3	SPI1_SCK	LCD_SEG7	TIM2_CH2	TSC_G5I_O1	EVENTOUT	-	-
	PB4	SPI1_MISO	LCD_SEG8	EVENTOUT	TSC_G5_IO2	TIM22_CH1	-	-
	PB5	SPI1_MOSI	LCD_SEG9	LPTIM1_IN1	I2C1_SMBA	TIM22_CH2	-	-
	PB6	USART1_TX	I2C1_SCL	LPTIM1_ETR	TSC_G5_IO3	-	-	-
	PB7	USART1_RX	I2C1_SDA	LPTIM1_IN2	TSC_G5_IO4	-	-	-
Port B	PB8	-	LCD_SEG16	-	TSC_SYNC	I2C1_SCL	-	-
	PB9	-	LCD_COM3	EVENTOUT	-	I2C1_SDA	SPI2_NSS/I2S2_ WS	-
	PB10	-	LCD_SEG10	TIM2_CH3	TSC_SYNC	LPUART1_TX	SPI2_SCK	I2C2_SCL
	PB11	EVENTOUT	LCD_SEG11	TIM2_CH4	TSC_G6_IO1	LPUART1_RX	-	I2C2_SDA
	PB12	SPI2_NSS/I2S2_WS	LCD_SEG12	LPUART1_RTS/ LPUART1_DE	TSC_G6_IO2	-	I2C2_SMBA	EVENTOUT
	PB13	SPI2_SCK/I2S2_CK	LCD_SEG13	-	TSC_G6_IO3	LPUART1_CTS	I2C2_SCL	TIM21_CH1
	PB14	SPI2_MISO/I2S2_MCK	LCD_SEG14	RTC_OUT	TSC_G6_IO4	LPUART1_RTS/ LPUART1_DE	I2C2_SDA	TIM21_CH2
	PB15	SPI2_MOSI/I2S2_SD	LCD_SEG15	RTC_REFIN	-	-	-	-

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- 1

Table 18. Alternate function port C

	Table 10: Alternate function port 0											
		AF0	AF1	AF2	AF3							
P	ort	LPUART1/LPTIM/ TIM21/12/ EVENTOUT/	LCD	SPI2/I2S2/USB/ LPUART1/ EVENTOUT	TSC							
	PC0	LPTIM1_IN1	LCD_SEG18	EVENTOUT	TSC_G7_IO1							
	PC1	LPTIM1_OUT	LCD_SEG19	EVENTOUT	TSC_G7_IO2							
	PC2	LPTIM1_IN2	LCD_SEG20	SPI2_MISO/I2S2_MCK	TSC_G7_IO3							
	PC3	LPTIM1_ETR	LCD_SEG21	SPI2_MOSI/I2S2_SD	TSC_G7_IO4							
	PC4	EVENTOUT	LCD_SEG22	LPUART1_TX	-							
	PC5	-	LCD_SEG23	LPUART1_RX	TSC_G3_IO1							
	PC6	TIM22_CH1	LCD_SEG24	-	TSC_G8_IO1							
Port C	PC7	TIM22_CH2	LCD_SEG25	-	TSC_G8_IO2							
Fort	PC8	TIM22_ETR	LCD_SEG26	-	TSC_G8_IO3							
	PC9	TIM21_ETR	LCD_SEG27	USB_NOE	TSC_G8_IO4							
	PC10	LPUART1_TX	LCD_COM4/LCD_SEG28	-	-							
	PC11	LPUART1_RX	LCD_COM5/LCD_SEG29	-	-							
	PC12	-	LCD_COM6/LCD_SEG30	-	-							
	PC13	-	-	-	-							
	PC14	-	-	-	-							
	PC15	-	-	-	-							

Table 19. Alternate function port D

Port		AF0	AF1
Port		LPUART1 LCD	
Port D	PD2	LPUART1_RTS/LPUART1_DE	LCD_COM7/LCD_SEG31

	Table 20. Alternate function port H			
Port		AF0		
		USB		
Port H	PH0	USB_CRS_SYNC		
POIL H	PH1	-		

5 Memory mapping

Refer to the product line reference manual for details on the memory mapping as well as the boundary addresses for all peripherals.

6 Electrical characteristics

6.1 Parameter conditions

Unless otherwise specified, all voltages are referenced to V_{SS}.

6.1.1 Minimum and maximum values

Unless otherwise specified the minimum and maximum values are guaranteed in the worst conditions of ambient temperature, supply voltage and frequencies by tests in production on 100% of the devices with an ambient temperature at $T_A = 25$ °C and $T_A = T_A$ max (given by the selected temperature range).

Data based on characterization results, design simulation and/or technology characteristics are indicated in the table footnotes and are not tested in production. Based on characterization, the minimum and maximum values refer to sample tests and represent the mean value plus or minus three times the standard deviation (mean±3 σ).

6.1.2 Typical values

Unless otherwise specified, typical data are based on T_A = 25 °C, V_{DD} = 3.6 V (for the 1.65 V \leq V $_{DD}$ \leq 3.6 V voltage range). They are given only as design guidelines and are not tested.

Typical ADC accuracy values are determined by characterization of a batch of samples from a standard diffusion lot over the full temperature range, where 95% of the devices have an error less than or equal to the value indicated (mean $\pm 2\sigma$).

6.1.3 Typical curves

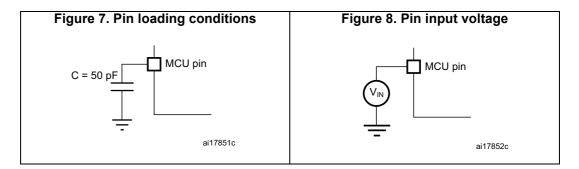
Unless otherwise specified, all typical curves are given only as design guidelines and are not tested.

6.1.4 Loading capacitor

The loading conditions used for pin parameter measurement are shown in Figure 7.

6.1.5 Pin input voltage

The input voltage measurement on a pin of the device is described in Figure 8.



6.1.6 Power supply scheme

Standby-power circuitry (OSC32,RTC,Wake-up logic, RTC backup registers) 10 GP I/Os Logic Kernel logic (CPU, Digital & Memories) Regulator N × 100 nF + 1 × 10 µF V_{DDA} V_{DDA} V_{REF} 100 nF + 1 μF Analog: RC,PLL,COMP, ADC/ 100 nF V_{REF} DAC + 1 µF V_{SSA} $V_{\text{LCD}} \ V_{\text{SS}}$ LCD V_{SS} USB $V_{\text{DD_USB}} \big[$ transceiver MSv33790V1

Figure 9. Power supply scheme

6.1.7 Optional LCD power supply scheme

Option 2

CEXT

VDD

VSEL

VSEL

VSEL

VLCD

VLCD

VLCD

VLCD

VLCD

VLCD

VLCD

VLCD

VSEL

VS

Figure 10. Optional LCD power supply scheme

- 1. Option 1: LCD power supply is provided by a dedicated VLCD supply source, VSEL switch is open.
- 2. Option 2: LCD power supply is provided by the internal step-up converter, VSEL switch is closed, an external capacitance is needed for correct behavior of this converter.

6.1.8 Current consumption measurement

Figure 11. Current consumption measurement scheme

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6.2 Absolute maximum ratings

Stresses above the absolute maximum ratings listed in *Table 21: Voltage characteristics*, *Table 22: Current characteristics*, and *Table 23: Thermal characteristics* may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these conditions is not implied. Exposure to maximum rating conditions for extended periods may affect device reliability. Device mission profile (application conditions) is compliant with JEDEC JESD47 Qualification Standard. Extended mission profiles are available on demand.

Table 21	. Voltage	characteristics
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Symbol	Definition	Min	Max	Unit	
V _{DD} -V _{SS}	External main supply voltage (including V _{DDA} , V _{DD_USB} , V _{DD}) ⁽¹⁾	-0.3	4.0		
	Input voltage on FT and FTf pins	V _{SS} -0.3	Min(Min(V _{DD} , V _{DDA}) + 3.6 V, 5.5 V)	V	
V _{IN} ⁽²⁾	Input voltage on TC pins	V _{SS} -0.3	4.0		
	Input voltage on BOOT0	V _{SS}	V _{DD} +4.0		
	Input voltage on any other pin	V _{SS} -0.3	4.0		
$ \Delta V_{DD} $	Variations between different V _{DDx} power pins	-	50		
V _{DDA} -V _{DDx}	Variations between any V_{DDx} and V_{DDA} power pins ⁽³⁾	-	300	mV	
ΔV _{SS}	Variations between all different ground pins	-	50		
V _{REF+} –V _{DDA}	Allowed voltage difference for V _{REF+} > V _{DDA}	-	0.4	V	
V _{ESD(HBM)}	Electrostatic discharge voltage (human body model)	see	see Section 6.3.11		

All main power (V_{DD}, V_{DD} _{USB}, V_{DDA}) and ground (V_{SS}, V_{SSA}) pins must always be connected to the external power supply, in the permitted range.

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^{2.} V_{IN} maximum must always be respected. Refer to Table 22 for maximum allowed injected current values.

^{3.} It is recommended to power V_{DD} and V_{DDA} from the same source. A maximum difference of 300 mV between V_{DD} and V_{DDA} can be tolerated during power-up and device operation. V_{DD_USB} is independent from V_{DD} and V_{DDA}: its value does not need to respect this rule.

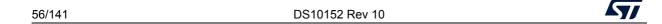
Table 22. Current characteristics

Symbol	Ratings	Max.	Unit
ΣI _{VDD} ⁽²⁾	Total current into sum of all V _{DD} power lines (source) ⁽¹⁾	105	
ΣI _{VSS} ⁽²⁾	Total current out of sum of all V _{SS} ground lines (sink) ⁽¹⁾	105	
ΣI _{VDD_USB}	Total current into V _{DD_USB} power lines (source)	25	
I _{VDD(PIN)}	Maximum current into each V _{DD} power pin (source) ⁽¹⁾	100	
I _{VSS(PIN)}	Maximum current out of each V _{SS} ground pin (sink) ⁽¹⁾	100	
	Output current sunk by any I/O and control pin except FTf pins	16	
I _{IO}	Output current sunk by FTf pins	22	
	Output current sourced by any I/O and control pin		mA
	Total output current sunk by sum of all IOs and control pins except PA11 and PA12 ⁽²⁾	90	
$\Sigma I_{IO(PIN)}$	Total output current sunk by PA11 and PA12	25	
	Total output current sourced by sum of all IOs and control pins ⁽²⁾	-90	
I	Injected current on FT, FTf, RST and B pins		
I _{INJ(PIN)}	Injected current on TC pin	± 5 ⁽⁴⁾	
ΣΙ _{ΙΝJ(PIN)}	Total injected current (sum of all I/O and control pins) ⁽⁵⁾	± 25	

- All main power (V_{DD}, V_{DDA}) and ground (V_{SS}, V_{SSA}) pins must always be connected to the external power supply, in the permitted range.
- This current consumption must be correctly distributed over all I/Os and control pins. The total output current must not be sunk/sourced between two consecutive power supply pins referring to high pin count LQFP packages.
- Positive current injection is not possible on these I/Os. A negative injection is induced by V_{IN}<V_{SS}. I_{INJ(PIN)} must never be exceeded. Refer to *Table 21* for maximum allowed input voltage values.
- A positive injection is induced by V_{IN} > V_{DD} while a negative injection is induced by V_{IN} < V_{SS}. I_{INJ(PIN)} must never be exceeded. Refer to *Table 21: Voltage characteristics* for the maximum allowed input voltage values.
- 5. When several inputs are submitted to a current injection, the maximum $\Sigma I_{INJ(PIN)}$ is the absolute sum of the positive and negative injected currents (instantaneous values).

Table 23. Thermal characteristics

Symbol	Ratings	Value	Unit
T _{STG}	Storage temperature range	-65 to +150	°C
T _J	Maximum junction temperature	150	°C



6.3 Operating conditions

6.3.1 General operating conditions

Table 24. General operating conditions

Symbol	Parameter	Conditions	Min	Max	Unit
f_{HCLK}	Internal AHB clock frequency	-	0	32	
f _{PCLK1}	Internal APB1 clock frequency	-	0	32	MHz
f _{PCLK2}	Internal APB2 clock frequency	-	0	32	
		BOR detector disabled	1.65	3.6	
V_{DD}	Standard operating voltage	BOR detector enabled, at power-on	1.8	3.6	V
		BOR detector disabled, after power-on	1.65	3.6	
V_{DDA}	Analog operating voltage (DAC not used)	Must be the same voltage as V _{DD} ⁽¹⁾	1.65	3.6	V
V_{DDA}	Analog operating voltage (all features)	Must be the same voltage as V _{DD} ⁽¹⁾	1.8	3.6	V
V _{DD} _	Standard operating voltage, USB domain ⁽²⁾ USB peripheral used USB peripheral not used		3.0	3.6	V
USB			0	3.6	V
	Input voltage on FT, FTf and RST	2.0 V ≤V _{DD} ≤3.6 V	-0.3	5.5	
\ <i>/</i>	pins ⁽³⁾	1.65 V ≤V _{DD} ≤2.0 V	-0.3	5.2	V
V_{IN}	Input voltage on BOOT0 pin	-	0	5.5	
	Input voltage on TC pin	-	-0.3	V _{DD} +0.3	
		TFBGA64	-	327	
	Power dissipation at T _A = 85 °C	LQFP64	-	444	
	Power dissipation at T _A = 85 °C (range 6) or T _A =105 °C (rage 7) ⁽⁴⁾	LQFP48	-	363	
Б		UFQFPN48	-	654	mW
P_{D}		TFBGA64	-	81	IIIVV
	Power dissipation at T _A = 125 °C	LQFP64	-	111	
	(range 3) ⁽⁴⁾	LQFP48 packge	-	91	
		UFQFPN48	-	163	
		Maximum power dissipation (range 6)	-4 0	85	
TA	Temperature range	Maximum power dissipation (range 7)	-4 0	105	
		Maximum power dissipation (range 3)	-40	125	°C
	Junction temperature range (range 6)	-40 °C ≤T _A ≤85 °	-4 0	105	
TJ	Junction temperature range (range 7)	-40 °C ≤T _A ≤105 °C	-4 0	125	
	Junction temperature range (range 3)	-40 °C ≤T _A ≤125 °C	-4 0	130	

It is recommended to power V_{DD} and V_{DDA} from the same source. A maximum difference of 300 mV between V_{DD} and V_{DDA} can be tolerated during power-up and normal operation.



- 2. V_{DD_USB} must respect the following conditions: When V_{DD} is powered-on ($V_{DD} < V_{DD_min}$), V_{DD_USB} should be always lower than V_{DD} spowered-down ($V_{DD} < V_{DD_min}$), V_{DD_USB} should be always lower than V_{DD} . In operating mode, V_{DD_USB} could be lower or higher V_{DD} . If the USB is not used, V_{DD_USB} must range from V_{DD_min} to V_{DD_max} to be able to use PA11 and PA12 as standard I/Os. If the USB is not used and PA11/PA12 are not used as standard I/Os, VDD_USB must be connected to a V_{SS} or V_{DD} power supply voltage (VDD_USB must not be left floating).
- 3. To sustain a voltage higher than V_{DD} +0.3V, the internal pull-up/pull-down resistors must be disabled.
- If T_A is lower, higher P_D values are allowed as long as T_J does not exceed T_J max (see Table 85: Thermal characteristics on page 130).

6.3.2 Embedded reset and power control block characteristics

The parameters given in the following table are derived from the tests performed under the ambient temperature condition summarized in *Table 24*.

Table 25. Embedded reset and power control block characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
	V rice time rate	BOR detector enabled	0	-	∞	
t _{VDD} ⁽¹⁾	V _{DD} rise time rate	BOR detector disabled	0	-	1000	µs/V
, NDD, , ,	\/ fall time note	BOR detector enabled	20	-	∞	
	V _{DD} fall time rate	BOR detector disabled	0	-	1000	
т (1)	Poset temperization	V _{DD} rising, BOR enabled	-	2	3.3	mo
T _{RSTTEMPO} ⁽¹⁾	Reset temporization	V _{DD} rising, BOR disabled ⁽²⁾	0.4	0.7	1.6	ms
V	Power-on/power down reset	Falling edge	1	1.5	1.65	
V _{POR/PDR}	threshold	Rising edge	1.3	1.5	1.65	
V	Brown-out reset threshold 0	Falling edge	1.67	1.7	1.74	
V _{BOR0}	Brown-out reset threshold o	Rising edge	1.69	1.76	1.8	
V	Brown-out reset threshold 1	Falling edge	1.87	1.93	1.97	
V _{BOR1}	Brown-out reset threshold 1	Rising edge	1.96	2.03	2.07	
V	Brown-out reset threshold 2	Falling edge	2.22	2.30	2.35	
V _{BOR2}		Rising edge	2.31	2.41	2.44	
V	Drawn and recat three-hald 2	Falling edge	2.45	2.55	2.6	
V _{BOR3}	Brown-out reset threshold 3	Rising edge	2.54	2.66	2.7	
M	Drown out road throshold 4	Falling edge	2.68	2.8	2.85	
V _{BOR4}	Brown-out reset threshold 4	Rising edge	2.78	2.9	2.95	V
\/	Programmable voltage detector	Falling edge	1.8	1.85	1.88	\ \ \
V_{PVD0}	threshold 0	Rising edge	1.88	1.94	1.99	
\/	D\/D throubold 1	Falling edge	1.98	2.04	2.09	
V _{PVD1}	PVD threshold 1	Rising edge	2.08	2.14	2.18	
\/	D\/D throobold 2	Falling edge	2.20	2.24	2.28	
V _{PVD2}	PVD threshold 2	Rising edge	2.28	2.34	2.38	
\/	DVD throubold 2	Falling edge	2.39	2.44	2.48	
V _{PVD3}	PVD threshold 3	Rising edge	2.47	2.54	2.58	
V	DVD throshold 4	Falling edge	2.57	2.64	2.69	
V _{PVD4}	PVD threshold 4	Rising edge	2.68	2.74	2.79	
\/	DVD throshold 5	Falling edge	2.77	2.83	2.88]
V_{PVD5}	PVD threshold 5	Rising edge	2.87	2.94	2.99]



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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V	DVD throshold 6	Falling edge	2.97	3.05	3.09	V
VPVD6	V _{PVD6} PVD threshold 6	Rising edge	3.08	3.15	3.20	V
		BOR0 threshold	-	40	-	
V_{hyst}	Hysteresis voltage	All BOR and PVD thresholds excepting BOR0	-	100	-	mV

Table 25. Embedded reset and power control block characteristics (continued)

6.3.3 Embedded internal reference voltage

The parameters given in *Table 27* are based on characterization results, unless otherwise specified.

Table 26. Embedded internal reference voltage calibration values

Calibration value name	Description	Memory address
VREFINT_CAL	Raw data acquired at temperature of 25 °C V _{DDA} = 3 V	0x1FF8 0078 - 0x1FF8 0079

Table 27. Embedded internal reference voltage⁽¹⁾

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{REFINT out} ⁽²⁾	Internal reference voltage	$-40 ^{\circ}\text{C} < \text{T}_{\text{J}} < +125 ^{\circ}\text{C}$	1.202	1.224	1.242	V
T _{VREFINT}	Internal reference startup time	-	-	2	3	ms
V _{VREF_MEAS}	V _{DDA} and V _{REF+} voltage during V _{REFINT} factory measure	-	2.99	3	3.01	V
A _{VREF_MEAS}	Accuracy of factory-measured V _{REFINT} value ⁽³⁾	Including uncertainties due to ADC and V_{DDA}/V_{REF+} values	ı	1	±5	mV
T _{Coeff} ⁽⁴⁾	Temperature coefficient	-40 °C < T _J < +125 °C	-	25	100	ppm/°C
A _{Coeff} ⁽⁴⁾	Long-term stability	1000 hours, T= 25 °C	-	-	1000	ppm
V _{DDCoeff} ⁽⁴⁾	Voltage coefficient	3.0 V < V _{DDA} < 3.6 V	-	-	2000	ppm/V
T _{S_vrefint} (4)(5)	ADC sampling time when reading the internal reference voltage	-	5	10	-	μs
T _{ADC_BUF} ⁽⁴⁾	Startup time of reference voltage buffer for ADC	-	-	-	10	μs
I _{BUF_ADC} ⁽⁴⁾	Consumption of reference voltage buffer for ADC	-	-	13.5	25	μA
I _{VREF_OUT} ⁽⁴⁾	VREF_OUT output current ⁽⁶⁾	-	-	-	1	μΑ
C _{VREF_OUT} ⁽⁴⁾	VREF_OUT output load	-	-	-	50	pF



^{1.} Guaranteed by characterization results.

^{2.} Valid for device version without BOR at power up. Please see option "D" in Ordering information scheme for more details.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{LPBUF} ⁽⁴⁾	Consumption of reference voltage buffer for VREF_OUT and COMP	-	-	730	1200	nA
V _{REFINT_DIV1} ⁽⁴⁾	1/4 reference voltage	-	24	25	26	
V _{REFINT_DIV2} ⁽⁴⁾	1/2 reference voltage	-	49	50	51	% V _{REFINT}
V _{REFINT_DIV3} ⁽⁴⁾	3/4 reference voltage	-	74	75	76	INEI IIVI

Table 27. Embedded internal reference voltage⁽¹⁾ (continued)

- Refer to Table 39: Peripheral current consumption in Stop and Standby mode for the value of the internal reference current consumption (I_{REFINT}).
- 2. Guaranteed by test in production.
- 3. The internal V_{REF} value is individually measured in production and stored in dedicated EEPROM bytes.
- 4. Guaranteed by design.
- 5. Shortest sampling time can be determined in the application by multiple iterations.
- 6. To guarantee less than 1% VREF_OUT deviation.

6.3.4 Supply current characteristics

The current consumption is a function of several parameters and factors such as the operating voltage, temperature, I/O pin loading, device software configuration, operating frequencies, I/O pin switching rate, program location in memory and executed binary code. The current consumption is measured as described in *Figure 11: Current consumption measurement scheme*.

All Run-mode current consumption measurements given in this section are performed with a reduced code that gives a consumption equivalent to Dhrystone 2.1 code if not specified otherwise.

The current consumption values are derived from the tests performed under ambient temperature and V_{DD} supply voltage conditions summarized in *Table 24: General operating conditions* unless otherwise specified.

The MCU is placed under the following conditions:

- All I/O pins are configured in analog input mode
- All peripherals are disabled except when explicitly mentioned
- The flash memory access time and prefetch is adjusted depending on fHCLK frequency and voltage range to provide the best CPU performance unless otherwise specified.
- When the peripherals are enabled f_{APB1} = f_{APB2} = f_{APB}
- When PLL is ON, the PLL inputs are equal to HSI = 16 MHz (if internal clock is used) or HSE = 16 MHz (if HSE bypass mode is used)
- The HSE user clock applied to OSCI_IN input follows the characteristic specified in Table 41: High-speed external user clock characteristics
- For maximum current consumption V_{DD} = V_{DDA} = 3.6 V is applied to all supply pins
- For typical current consumption V_{DD} = V_{DDA} = 3.0 V is applied to all supply pins if not specified otherwise

The parameters given in *Table 49*, *Table 24* and *Table 25* are derived from tests performed under ambient temperature and V_{DD} supply voltage conditions summarized in *Table 24*.



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Table 28. Current consumption in Run mode, code with data processing running from flash

Symbol	Parameter	Co	nditions	f _{HCLK}	Тур	Max ⁽¹⁾	Unit
			D 0.1/ 10.1/	1 MHz	165	230	
			Range 3, V _{CORE} =1.2 V VOS[1:0]=11	2 MHz	290	360	μA
				4 MHz	555	630	
		f _{HSE} = f _{HCLK} up to		4 MHz	0.665	0.74	
Supply current is		16 MHz included, f _{HSE} = f _{HCLK} /2 above 16 MHz (PLL ON) ⁽²⁾	Range 2, V _{CORE} =1.5 V, VOS[1:0]=10,	8 MHz	1.3	1.4	
	Supply current in			16 MHz	2.6	2.8	mA
			Range 1, V _{CORE} =1.8 V, VOS[1:0]=01	8 MHz	1.55	1.7	
(Run from	Run mode, code			16 MHz	3.1	3.4	
flash)	executed			32 MHz	6.3	6.8	
	from flash			65 kHz	36.5	110	
		MSI clock	Range 3, V _{CORE} =1.2 V, VOS[1:0]=11	524 kHz	99.5	190	μA
				4.2 MHz	620	700	
		HSI clock	Range 2, V _{CORE} =1.5 V, VOS[1:0]=10,	16 MHz	2.6	2.9	
			Range 1, V _{CORE} =1.8 V, VOS[1:0]=01	32 MHz	6.25	7	- mA

^{1.} Guaranteed by characterization results at 125 °C, unless otherwise specified.

Table 29. Current consumption in Run mode vs code type, code with data processing running from flash

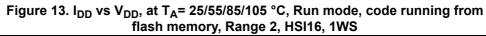
Symbol	Parameter		Conditions		f _{HCLK}	Тур	Unit
				Dhrystone		555	
Currh			Range 3, V _{CORE} =1.2 V, VOS[1:0]=11	CoreMark		585	μA mA
				Fibonacci	4 MHz	440	
	Cupply			while(1)		355	
I _{DD} (Run	Supply current in Run mode,			while(1), prefetch OFF		353	
from flash)	code executed			Dhrystone		6.3	
liasii)	from flash			CoreMark		6.3	
			Range 1, V _{CORE} =1.8 V,	Fibonacci	32 MHz	6.55	
			VOS[1:0]=01	while(1)		5.4	
				while(1), prefetch OFF		5.2	

^{1.} Oscillator bypassed (HSEBYP = 1 in RCC_CR register).

^{2.} Oscillator bypassed (HSEBYP = 1 in RCC_CR register).

3.00 2.50 2.00 1.50 1.00 0.50 0 VDD (V) 2.00E+00 2.20E+00 2.40E+00 3.00E+00 3.20E+00 3.40E+00 2 60F+00 2.80E+00 3.60E+00 Dhrystone 2.1 - 1 WS - 55°C Dhrystone 2.1- 1 WS - 85°C Dhrystone 2.1- 1 WS – 25°C Dhrystone 2.1- 1 WS - 105°C MSv34792V1

Figure 12. I_{DD} vs V_{DD} , at T_A = 25/55/85/105 °C, Run mode, code running from flash memory, Range 2, HSE, 1WS



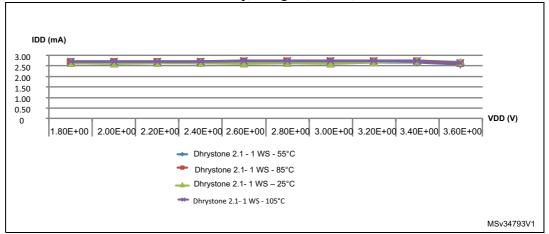


Table 30. Current consumption in Run mode, code with data processing running from RAM

Symbol	Parameter	Conc	litions	f _{HCLK}	Тур	Max ⁽¹⁾	Unit
			Range 3,	1 MHz	135	170	
			V _{CORE} =1.2 V,	2 MHz	240	270	μΑ
		f _{HSE} = f _{HCLK} up to 16 MHz included, f _{HSE} = f _{HCLK} /2 above	VOS[1:0]=11	4 MHz	450	480	
			Range 2,	4 MHz	0.52	0.6	
			V _{CORE} =1.5 ,V,	8 MHz	1	1.2	mA μA
		16 MHz (PLL ON) ⁽²⁾	VOS[1:0]=10	16 MHz	2	2.3	
	Supply current in		Range 1, V _{CORE} =1.8 V, VOS[1:0]=01	8 MHz	1.25	1.4	
I _{DD} (Run	Run mode, code executed from RAM, flash switched off			16 MHz	2.45	2.8	
from RAM)				32 MHz	5.1	5.4	
TV-tivi)			Range 3, V _{CORE} =1.2 V,	65 kHz	34.5	75	
		MSI clock		524 kHz	83	120	
			VOS[1:0]=11	4.2 MHz	485	540	
		HSI16 clock source	Range 2, V _{CORE} =1.5 V, VOS[1:0]=10	16 MHz	2.1	2.3	
		(16 MHz)	Range 1, V _{CORE} =1.8 V, VOS[1:0]=01	32 MHz	5.1	5.6	mA

^{1.} Guaranteed by characterization results at 125 °C, unless otherwise specified.

Table 31. Current consumption in Run mode vs code type, code with data processing running from RAM⁽¹⁾

Symbol	Parameter			f _{HCLK}	Тур	Unit	
				Dhrystone		450	
Supply current in	f - f	Range 3, V _{CORE} =1.2 V, VOS[1:0]=11	CoreMark	4 MHz	575	μA	
			Fibonacci	4 1011 12	370		
I _{DD} (Run from	Run mode, code executed from	$f_{HSE} = f_{HCLK}$ up to 16 MHz included, $f_{HSE} = f_{HCLK}/2$ above 16 MHz (PLL ON) ⁽²⁾		while(1)		340	
RAM)	RAM, flash			Dhrystone		5.1	- mA
	switched off	10 WHZ (1 LL ON)**	Range 1, V _{CORE} =1.8 V,	CoreMark	32 MHz	6.25	
			V _{CORE} -1.6 V, VOS[1:0]=01	Fibonacci	- 32 IVITZ	4.4	
				while(1)		4.7	

^{1.} Guaranteed by characterization results, unless otherwise specified.

^{2.} Oscillator bypassed (HSEBYP = 1 in RCC_CR register).

^{2.} Oscillator bypassed (HSEBYP = 1 in RCC_CR register).

Table 32. Current consumption in Sleep mode

Symbol	Parameter	Cond	itions	f _{HCLK}	Тур	Max ⁽¹⁾	Unit
			Range 3,	1 MHz	43.5	90	
			V _{CORE} =1.2 V,	2 MHz	72	120	
			VOS[1:0]=11	4 MHz	130	180	1
		f _{HSE} = f _{HCLK} up to	Range 2,	4 MHz	160	210	
		16 MHz included, f _{HSE} = f _{HCLK} /2 above	V _{CORE} =1.5 V,	8 MHz	305	370	
		16 MHz (PLL ON) ⁽²⁾	VOS[1:0]=10	16 MHz	590	710	
			Range 1,	8 MHz	370	430	
	Supply current		V _{CORE} =1.8 V,	16 MHz	715	860	
	in Sleep mode, flash		VOS[1:0]=01	32 MHz	1650	1900	
	OFF		Range 3, V _{CORE} =1.2 V, VOS[1:0]=11	65 kHz	18	65	
		MSI clock		524 kHz	31.5	75	
				4.2 MHz	140	210	
		HSI16 clock source (16 MHz)	Range 2, V _{CORE} =1.5 V, VOS[1:0]=10	16 MHz	665	830	-
(0)			Range 1, V _{CORE} =1.8 V, VOS[1:0]=01	32 MHz	1750	2100	
I _{DD} (Sleep)		f _{HSE} = f _{HCLK} up to 16 MHz included, f _{HSE} = f _{HCLK} /2 above	Range 3,	1 MHz	57.5	130	- μA - - -
			V _{CORE} =1.2 V,	2 MHz	84	170	
			VOS[1:0]=11	4 MHz	150	280	
			Range 2, CORE=1.5 V, VOS[1:0]=10	4 MHz	170	310	
				8 MHz	315	420	
		16 MHz (PLL ON) ⁽²⁾		16 MHz	605	770	
			Range 1,	8 MHz	380	460	
	Supply current in Sleep		V _{CORE} =1.8 V,	16 MHz	730	950	
	mode, flash		VOS[1:0]=01	32 MHz	1650	2400	
	ON		Range 3,	65 kHz	29.5	110	
		MSI clock	V _{CORE} =1.2 V,	524 kHz	44.5	130	
			VOS[1:0]=11	4.2 MHz	150	270	
		HSI16 clock source (16 MHz)	Range 2, V _{CORE} =1.5 V, VOS[1:0]=10	16 MHz	680	950	
			Range 1, V _{CORE} =1.8 V, VOS[1:0]=01	32 MHz	1750	2100	

^{1.} Guaranteed by characterization results at 125 $^{\circ}\text{C},$ unless otherwise specified.



2. Oscillator bypassed (HSEBYP = 1 in RCC_CR register).

Table 33. Current consumption in Low-power run mode

Symbol	Parameter		Conditions		Тур	Max ⁽¹⁾	Unit
				$T_A = -40 \text{ to } 25^{\circ}\text{C}$	8.5	10	
			MSI clock = 65 kHz,	T _A = 85 °C	11.5	48	
			f _{HCLK} = 32 kHz	T _A = 105 °C	15.5	53	
				T _A = 125 °C	27.5	130	
		All peripherals		T _A =-40 °C to 25 °C	10	15	
		OFF, code executed from	MSI clock= 65 kHz,	T _A = 85 °C	15.5	50	
	RAM, flash	f _{HCLK} = 65 kHz	T _A = 105 °C	19.5	54		
		switched off, V _{DD} from 1.65		T _A = 125 °C	31.5	130	
		to 3.6 V		T _A = - 40 to 25°C	20	25	
			T _A = 55 °C	23	50		
		MSI clock= 131 kHz, f _{HCLK} = 131 kHz	T _A = 85 °C	25.5	55		
	Cummb		HOLK	T _A = 105 °C	29.5	64	μА
I _{DD}	Supply current in			T _A = 125 °C	40	140	
(LP Run)	Low-power run mode		MSI clock= 65 kHz, f _{HCLK} = 32 kHz	T _A = - 40 to 25°C	22	28	
	run mode			T _A = 85 °C	26	68	
				T _A = 105 °C	31	75	
				T _A = 125 °C	44	95	
		All peripherals		T _A = - 40 to 25°C	27.5	33	
		OFF, code	MSI clock = 65 kHz,	T _A = 85 °C	31.5	73	
		executed from flash, V _{DD}	f _{HCLK} = 65 kHz	T _A = 105 °C	36.5	80	
		from 1.65 V to		T _A = 125 °C	49	100	
		3.6 V		T _A = - 40 to 25°C	39	46	
			MSI clock =	T _A = 55 °C	41	80	
			131 kHz,	T _A = 85 °C	44	86	
			f _{HCLK} = 131 kHz	T _A = 105 °C	49.5	100	
				T _A = 125 °C	60	120	

^{1.} Guaranteed by characterization results at 125 °C, unless otherwise specified.



IDD (mA) 3.50E-02 3.00E-02 1.50E-02 1.00E-02 5.00E-03 VDD (V) 1.80 2.00 2.40 2.60 3.00 3.20 3.40 3.60 0 WS - 85°C 0 WS - 125°C MSv34794V3

Figure 14. I_{DD} vs V_{DD} , at T_A = 25/55/ 85/105/125 °C, Low-power run mode, code running from RAM, Range 3, MSI (Range 0) at 64 KHz, 0 WS

Table 34. Current consumption in Low-power sleep mode

Symbol	Parameter		Conditions		Тур	Max ⁽¹⁾	Unit
			MSI clock = 65 kHz, f _{HCLK} = 32 kHz, flash OFF	T _A = -40 to 25°C	4.7 ⁽²⁾	-	
			MSI clock = 65 kHz,	$T_A = -40 \text{ to } 25^{\circ}\text{C}$	17	23	
				T _A = 85 °C	19.5	63	
			f _{HCLK} = 32 kHz, flash ON	T _A = 105 °C	23	69	
		All peripherals OFF, V _{DD} from 1.65 to 3.6 V		T _A = 125 °C	32.5	90	
	Supply current in		MSI clock =65 kHz, f _{HCLK} = 65 kHz, flash ON	$T_A = -40 \text{ to } 25^{\circ}\text{C}$	17	23	
I _{DD} (LP Sleep)	Low-power sleep mode			T _A = 85 °C	20	63	μΑ
				T _A = 105 °C	23.5	69	
				T _A = 125 °C	32.5	90	
				$T_A = -40 \text{ to } 25^{\circ}\text{C}$	19.5	36	
			MSI clock = 131 kHz,	T _A = 55 °C	20.5	64	
			f _{HCLK} = 131 kHz,	T _A = 85 °C	22.5	66	1
			flash ON	T _A = 105 °C	26	72	
				T _A = 125 °C	35	95	

^{1.} Guaranteed by characterization results at 125 °C, unless otherwise specified.

^{2.} As the CPU is in Sleep mode, the difference between the current consumption with flash ON and OFF (nearly 12 μ A) is the same whatever the clock frequency.

Table 66. Typical and maximum current consumptions in Geop mode									
Symbol	Parameter	Conditions	Тур	Max ⁽¹⁾	Unit				
		$T_A = -40 \text{ to } 25^{\circ}\text{C}$	0.41	1					
		T _A = 55°C	0.63	2.1					
I _{DD} (Stop)	Supply current in Stop mode	T _A = 85°C	1.7	4.5	μΑ				
		T _A = 105°C	4	9.6					
		T _A = 125°C	11	24 ⁽²⁾					

Table 35. Typical and maximum current consumptions in Stop mode

- 1. Guaranteed by characterization results at 125 °C, unless otherwise specified.
- 2. Guaranteed by test in production.

Figure 15. I_{DD} vs V_{DD} , at T_A = 25/55/ 85/105/125 °C, Stop mode with RTC enabled and running on LSE Low drive

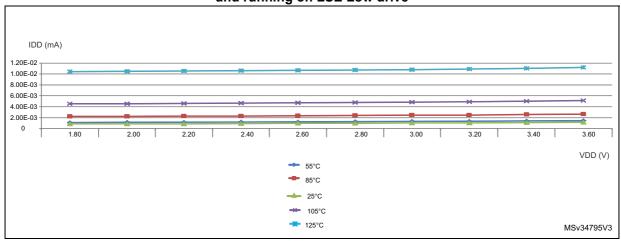


Figure 16. I_{DD} vs V_{DD} , at T_A = 25/55/85/105/125 °C, Stop mode with RTC disabled, all clocks OFF

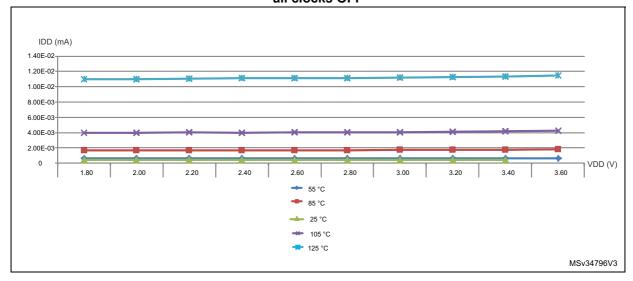


Table 36. Typical and maximum current consumptions in Standby mode

Symbol	Parameter	Conditi	ons	Тур	Max ⁽¹⁾	Unit
			$T_A = -40 \text{ to } 25^{\circ}\text{C}$	1.3	1.7	
			T _A = 55 °C	-	2.9	
		Independent watchdog and LSI enabled	T _A = 85 °C	-	3.3	
			T _A = 105 °C -		4.1	
I _{DD}	Supply current in Standby		T _A = 125 °C	-	8.5	
(Standby)	mode		$T_A = -40 \text{ to } 25^{\circ}\text{C}$	0.29	0.6	μA
			T _A = 55 °C	0.32	0.9	
		and LSI OFF	T _A = 85 °C	0.5	2.3	
			T _A = 105 °C	0.94	3	
			T _A = 125 °C	2.6	7	

^{1.} Guaranteed by characterization results at 125 $^{\circ}\text{C},$ unless otherwise specified

Table 37. Average current consumption during wake-up

Symbol	parameter	System frequency	Current consumption during wake-up	Unit
		HSI	1	
	Supply current during Wake-up from Stop mode	HSI/4	0,7	
I _{DD} (Wake-up from Stop)		MSI clock = 4,2 MHz	0,7	
J. 5.5p)	otop moud	MSI clock = 1,05 MHz	0,4	
		MSI clock = 65 KHz	0,1	mA
I _{DD} (Reset)	Reset pin pulled down	-	0,21	
I _{DD} (Power-up)	BOR ON	-	0,23	
I _{DD} (Wake-up from	With Fast wake-up set	MSI clock = 2,1 MHz	0,5	
StandBy)	With Fast wake-up disabled	MSI clock = 2,1 MHz	0,12	

On-chip peripheral current consumption

The current consumption of the on-chip peripherals is given in the following tables. The MCU is placed under the following conditions:

- all I/O pins are in input mode with a static value at V_{DD} or V_{SS} (no load)
- all peripherals are disabled unless otherwise mentioned
- the given value is calculated by measuring the current consumption
 - with all peripherals clocked OFF
 - with only one peripheral clocked on

Table 38. Peripheral current consumption in Run or Sleep mode⁽¹⁾

		Typical	consumption, V	/ _{DD} = 3.0 V, T _A =	25 °C	
Per	ripheral	Range 1, V _{CORE} =1.8 V VOS[1:0] = 01	Range 2, V _{CORE} =1.5 V VOS[1:0] = 10	Range 3, V _{CORE} =1.2 V VOS[1:0] = 11	Low-power sleep and run	Unit
	CRS	2.5	2	2	2	
	DAC1	4	3.5	3	2.5	
	I2C1	11	9.5	7.5	9	
	I2C2	4	3.5	3	2.5	
APB1	LCD1	4	3.5	3	2.5	
	LPTIM1	10	8.5	6.5	8	
	LPUART1	8	6.5	5.5	6	μΑ/MHz (f _{HCLK})
	SPI2	9	4.5	3.5	4	
	USB	8.5	4.5	4	4.5	
	USART2	14.5	12	9.5	11	
	TIM2	10.5	8.5	7	9	
	TIM6	3.5	3	2.5	2	
	WWDG	3	2	2	2	
	ADC1 ⁽²⁾	5.5	5	3.5	4	
	SPI1	4	3	3	2.5	
	USART1	14.5	11.5	9.5	12	
APB2	TIM21	7.5	6	5	5.5	μΑ/MHz
AFD2	TIM22	7	6	5	6	(f _{HCLK})
	FIREWALL	1.5	1	1	0.5	
	DBGMCU	1.5	1	1	0.5	
	SYSCFG	2.5	2	2	1.5	

Table 38. Peripheral current consumption in Run or Sleep mode⁽¹⁾ (continued)

		Typical	consumption, V	v _{DD} = 3.0 V, T _A =	25 °C		
Peri	ipheral	Range 1, V _{CORE} =1.8 V VOS[1:0] = 01	Range 2, V _{CORE} =1.5 V VOS[1:0] = 10	Range 3, V _{CORE} =1.2 V VOS[1:0] = 11	Low-power sleep and run	Unit	
	GPIOA	3.5	3	2.5	2.5		
Cortex- M0+ core I/O port	GPIOB	3.5	2.5	2	2.5		
	GPIOC	8.5	6.5	5.5	7	μΑ/MHz (f _{HCLK})	
	GPIOD	1	0.5	0.5	0.5	('HCLK)	
	GPIOH	1.5	1	1	0.5		
	CRC	1.5	1	1	1		
	FLASH	0(3)	0 ⁽³⁾	0(3)	0(3)		
AHB	DMA1	10	8	6.5	8.5	μΑ/MHz (f _{HCLK})	
	RNG	5.5	1	0.5	0.5	('HCLK)	
	TSC	3	2.5	2	3		
All enabled		283	225	222.5	212.5	μΑ/ΜΗz (f _{HCLK})	
PWR		2.5	2	2	1	μΑ/ΜΗz (f _{HCLK})	

Data based on differential I_{DD} measurement between all peripherals OFF an one peripheral with clock enabled, in the following conditions: f_{HCLK} = 32 MHz (range 1), f_{HCLK} = 16 MHz (range 2), f_{HCLK} = 4 MHz (range 3), f_{HCLK} = 64kHz (Low-power run/sleep), f_{APB1} = f_{HCLK}, f_{APB2} = f_{HCLK}, default prescaler value for each peripheral. The CPU is in Sleep mode in both cases. No I/O pins toggling. Not tested in production.

^{2.} HSI oscillator is OFF for this measure.

^{3.} Current consumption is negligible and close to 0 μA .

Symbol	Peripheral –	Typical consumption, T _A = 25 °C		Unit
		V _{DD} =1.8 V	V _{DD} =3.0 V	- Unit
I _{DD(PVD / BOR)}	-	0.7	1.2	μΑ
I _{REFINT}	-	-	1.4	
-	LSE Low drive ⁽²⁾	0,1	0,1	
-	LPTIM1, Input 100 Hz	0,01	0,01	
-	LPTIM1, Input 1 MHz	6	6	
-	LPUART1	0,2	0,2	
-	RTC	0,3	0,48	
-	LCD1 (static duty)	0,15	0,15	μА
-	LCD1 (1/8 duty)	1,6	2,6	

Table 39. Peripheral current consumption in Stop and Standby mode⁽¹⁾

6.3.5 Wake-up time from low-power mode

The wake-up times given in the following table are measured with the MSI or HSI16 RC oscillator. The clock source used to wake up the device depends on the current operating mode:

- Sleep mode: the clock source is the clock that was set before entering Sleep mode
- Stop mode: the clock source is either the MSI oscillator in the range configured before entering Stop mode, the HSI16 or HSI16/4.
- Standby mode: the clock source is the MSI oscillator running at 2.1 MHz

All timings are derived from tests performed under ambient temperature and V_{DD} supply voltage conditions summarized in *Table 24*.

^{1.} LPTIM peripheral cannot operate in Standby mode.

^{2.} LSE Low drive consumption is the difference between an external clock on OSC32_IN and a quartz between OSC32_IN and OSC32_OUT.-

Table 40. Low-power mode wake-up timings

Symbol	Parameter	Conditions	Тур	Max	Unit
t _{WUSLEEP}	Wake-up from Sleep mode	f _{HCLK} = 32 MHz	7	8	
	Wake-up from Low-power sleep mode,	f _{HCLK} = 262 kHz flash memory enabled	7	8	Number of clock
twusleep_lp	f _{HCLK} = 262 kHz	f _{HCLK} = 262 kHz flash memory switched OFF	9	10	cycles
		f _{HCLK} = f _{MSI} = 4.2 MHz	5.0	8	
	Wake-up from Stop mode, regulator in Run mode	f _{HCLK} = f _{HSI} = 16 MHz	4.9	7	
		f _{HCLK} = f _{HSI} /4 = 4 MHz	8.0	11	
		f _{HCLK} = f _{MSI} = 4.2 MHz Voltage range 1	5.0	8	
		f _{HCLK} = f _{MSI} = 4.2 MHz Voltage range 2	5.0	8	
		f _{HCLK} = f _{MSI} = 4.2 MHz Voltage range 3	5.0	8	μs
		f _{HCLK} = f _{MSI} = 2.1 MHz	7.3	13	
t _{WUSTOP}	Wake-up from Stop mode, regulator in low-power mode	f _{HCLK} = f _{MSI} = 1.05 MHz	13	23	
		f _{HCLK} = f _{MSI} = 524 kHz	28	38	
		f _{HCLK} = f _{MSI} = 262 kHz	51	65	
		f _{HCLK} = f _{MSI} = 131 kHz	100	120	
		f _{HCLK} = MSI = 65 kHz	190	260	
		f _{HCLK} = f _{HSI} = 16 MHz	4.9	7	
		f _{HCLK} = f _{HSI} /4 = 4 MHz	8.0	11	
		f _{HCLK} = f _{HSI} = 16 MHz	4.9	7	
	Wake-up from Stop mode, regulator in low-power mode, code running from RAM	f _{HCLK} = f _{HSI} /4 = 4 MHz	7.9	10	
	lear points interest and raining noise and	f _{HCLK} = f _{MSI} = 4.2 MHz	4.7	8	
	Wake-up from Standby mode, FWU bit = 1	f _{HCLK} = MSI = 2.1 MHz	65	130	μs
t _{WUSTDBY}	Wake-up from Standby mode, FWU bit = 0	f _{HCLK} = MSI = 2.1 MHz	2.2	3	ms
t _{WUUSART}	Wake-up time required to calculate the maximum USART/LPUART baudrate while waking up from Stop mode using the USART/LPUART	Stop mode, regulator in Run mode	^t wustop		μs



6.3.6 **External clock source characteristics**

High-speed external user clock generated from an external source

In bypass mode the HSE oscillator is switched off and the input pin is a standard GPIO.The external clock signal has to respect the I/O characteristics in Section 6.3.12. However, the recommended clock input waveform is shown in Figure 17.

Table 41. High-speed external user clock characteristics⁽¹⁾

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
f	User external clock source	CSS is ON or PLL is used	1	8	32	MHz
f _{HSE_ext}	frequency	CSS is OFF, PLL not used	0	8	32	MHz
V _{HSEH}	OSC_IN input pin high level voltage		-	V_{DD}	-	V
V _{HSEL}	OSC_IN input pin low level voltage		1	V_{SS}	ı	V
$t_{w(HSE)} \ t_{w(HSE)}$	OSC_IN high or low time		12	i	ı	ns
t _{r(HSE)}	OSC_IN rise or fall time	-	-	1	20	113
C _{in(HSE)}	OSC_IN input capacitance		-	2.6	-	pF
DuCy _(HSE)	Duty cycle		45	-	55	%
ΙL	OSC_IN Input leakage current	$V_{SS} \leq V_{IN} \leq V_{DD}$	-	-	±1	μA

^{1.} Guaranteed by design.

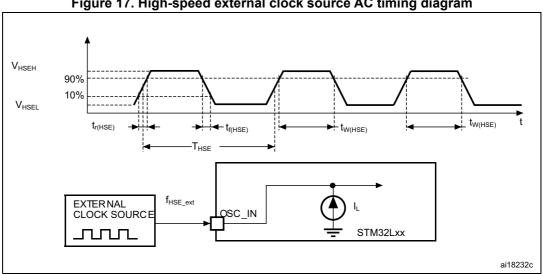


Figure 17. High-speed external clock source AC timing diagram

Low-speed external user clock generated from an external source

The characteristics given in the following table result from tests performed using a lowspeed external clock source, and under ambient temperature and supply voltage conditions summarized in Table 24.

Table 42. Low-speed external user clock characteristics⁽¹⁾

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
f _{LSE_ext}	User external clock source frequency		1	32.768	1000	kHz
V _{LSEH}	OSC32_IN input pin high level voltage		-	V _{DD}	-	V
V _{LSEL}	OSC32_IN input pin low level voltage	-	-	V _{SS}	-	V
t _{w(LSE)}	OSC32_IN high or low time		465	-	ı	ns
$\begin{matrix} t_{r(LSE)} \\ t_{f(LSE)} \end{matrix}$	OSC32_IN rise or fall time		-	-	10	113
C _{IN(LSE)}	OSC32_IN input capacitance	-	-	0.6	-	pF
DuCy _(LSE)	Duty cycle	-	45	-	55	%
IL	OSC32_IN Input leakage current	$V_{SS} \leq V_{IN} \leq V_{DD}$	-	-	±1	μΑ

^{1.} Guaranteed by design, not tested in production

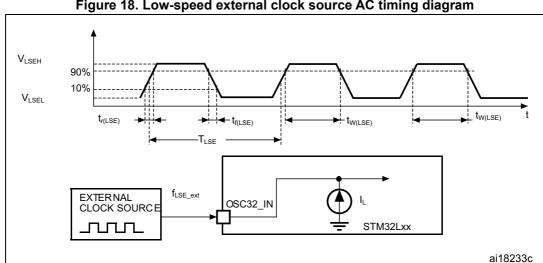


Figure 18. Low-speed external clock source AC timing diagram

High-speed external clock generated from a crystal/ceramic resonator

The high-speed external (HSE) clock can be supplied with a 1 to 25 MHz crystal/ceramic resonator oscillator. All the information given in this paragraph are based on characterization results obtained with typical external components specified in *Table 43*. In the application, the resonator and the load capacitors have to be placed as close as possible to the oscillator pins in order to minimize output distortion and startup stabilization time. Refer to the crystal resonator manufacturer for more details on the resonator characteristics (frequency, package, accuracy).

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
f _{OSC_IN}	Oscillator frequency	-	1		25	MHz
R _F	Feedback resistor	-	-	200	-	kΩ
G _m	Maximum critical crystal transconductance	Startup	-	-	700	μA /V
t _{SU(HSE)}	Startup time	V _{DD} is stabilized	i	2	-	ms

Table 43. HSE oscillator characteristics⁽¹⁾

For C_{L1} and C_{L2} , it is recommended to use high-quality external ceramic capacitors in the 5 pF to 25 pF range (typ.), designed for high-frequency applications, and selected to match the requirements of the crystal or resonator (see *Figure 19*). C_{L1} and C_{L2} are usually the same size. The crystal manufacturer typically specifies a load capacitance which is the series combination of C_{L1} and C_{L2} . PCB and MCU pin capacitance must be included (10 pF can be used as a rough estimate of the combined pin and board capacitance) when sizing C_{L1} and C_{L2} . Refer to the application note AN2867 "Oscillator design guide for ST microcontrollers" available from the ST website *www.st.com*.

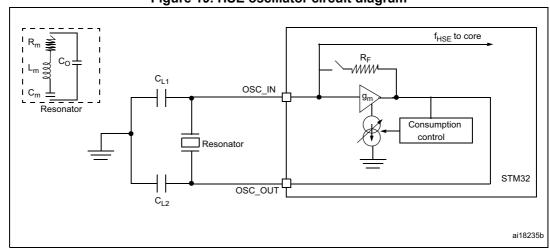


Figure 19. HSE oscillator circuit diagram

^{1.} Guaranteed by design.

Guaranteed by characterization results. t_{SU(HSE)} is the startup time measured from the moment it is enabled (by software) to a stabilized 8 MHz oscillation is reached. This value is measured for a standard crystal resonator and it can vary significantly with the crystal manufacturer.

Low-speed external clock generated from a crystal/ceramic resonator

The low-speed external (LSE) clock can be supplied with a 32.768 kHz crystal/ceramic resonator oscillator. All the information given in this paragraph are based on characterization results obtained with typical external components specified in *Table 44*. In the application, the resonator and the load capacitors have to be placed as close as possible to the oscillator pins in order to minimize output distortion and startup stabilization time. Refer to the crystal resonator manufacturer for more details on the resonator characteristics (frequency, package, accuracy).

Symbol	Parameter	Conditions ⁽²⁾	Min ⁽²⁾	Тур	Max	Unit
f_{LSE}	LSE oscillator frequency		-	32.768	-	kHz
		LSEDRV[1:0]=00 lower driving capability	-	-	0.5	
G	Maximum critical crystal	LSEDRV[1:0]= 01 medium low driving capability	-	-	0.75	uA/V
G _m	transconductance	LSEDRV[1:0] = 10 medium high driving capability	-	-	1.7	μΑνν
		LSEDRV[1:0]=11 higher driving capability	-	-	2.7	
t _{SU(LSE)} ⁽³⁾	Startup time	V _{DD} is stabilized	-	2	-	s

Table 44. LSE oscillator characteristics⁽¹⁾

Note: For information on selecting the crystal, refer to the application note AN2867 "Oscillator design guide for ST microcontrollers" available from the ST website www.st.com.

Resonator with integrated capacitors

OSC32_IN

Drive programmable amplifier

OSC32_OUT

MS30253V2

Figure 20. Typical application with a 32.768 kHz crystal

Note:

An external resistor is not required between OSC32_IN and OSC32_OUT and it is forbidden to add one.



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^{1.} Guaranteed by design.

^{2.} Refer to the note and caution paragraphs below the table, and to the application note AN2867 "Oscillator design guide for ST microcontrollers"

Guaranteed by characterization results. t_{SU(LSE)} is the startup time measured from the moment it is enabled (by software) to a stabilized 32.768 kHz oscillation is reached. This value is measured for a standard crystal resonator and it can vary significantly with the crystal manufacturer. To increase speed, address a lower-drive quartz with a high- driver mode.

6.3.7 Internal clock source characteristics

The parameters given in *Table 45* are derived from tests performed under ambient temperature and V_{DD} supply voltage conditions summarized in *Table 24*.

High-speed internal 16 MHz (HSI16) RC oscillator

Table 45. 16 MHz HSI16 oscillator characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
f _{HSI16}	Frequency	V _{DD} = 3.0 V	-	16	-	MHz
TD114(1)(2)	HSI16 user-	Trimming code is not a multiple of 16	-	±0.4	0.7	%
	trimmed resolution	Trimming code is a multiple of 16	-	-	±1.5	%
		V _{DDA} = 3.0 V, T _A = 25 °C	-1 ⁽³⁾	-	1 ⁽³⁾	%
		$V_{DDA} = 3.0 \text{ V}, T_A = 0 \text{ to } 55 ^{\circ}\text{C}$	-1.5	-	1.5	%
ACC	Accuracy of the factory-calibrated HSI16 oscillator	V_{DDA} = 3.0 V, T_A = -10 to 70 °C	-2	-	2	%
ACC _{HSI16}		V_{DDA} = 3.0 V, T_A = -10 to 85 °C	-2.5	-	2	%
		$V_{DDA} = 3.0 \text{ V}, T_{A} = -10 \text{ to } 105 ^{\circ}\text{C}$	-4	ı	2	%
		V _{DDA} = 1.65 V to 3.6 V T _A = -40 to 125 °C	-5.45	ı	3.25	%
t _{SU(HSI16)} ⁽²⁾	HSI16 oscillator startup time	-	-	3.7	6	μs
I _{DD(HSI16)} ⁽²⁾	HSI16 oscillator power consumption	-	-	100	140	μA

^{1.} The trimming step differs depending on the trimming code. It is usually negative on the codes which are multiples of 16 (0x00, 0x10, 0x20, 0x30...0xE0).

- 2. Guaranteed by characterization results.
- 3. Guaranteed by test in production.

Figure 21. HSI16 minimum and maximum value versus temperature 4.00° 3.00% 2.00% 1.65V min 0,00 ■ 3V typ 20 40 60 3.6V max 1.65V max ■ 3.6V min 5.00% -6.00% MSv34791V1

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High-speed internal 48 MHz (HSI48) RC oscillator

Table 46. HSI48 oscillator characteristics⁽¹⁾

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
f _{HSI48}	Frequency		-	48	-	MHz
TRIM	HSI48 user-trimming step		0.09 ⁽²⁾	0.14	0.2 ⁽²⁾	%
DuCy _(HSI48)	Duty cycle		45 ⁽²⁾	-	55 ⁽²⁾	%
ACC _{HSI48}	Accuracy of the HSI48 oscillator (factory calibrated before CRS calibration)	T _A = 25 °C	-4 ⁽³⁾	-	4 ⁽³⁾	%
t _{su(HSI48)}	HSI48 oscillator startup time		-	-	6 ⁽²⁾	μs
I _{DDA(HSI48)}	HSI48 oscillator power consumption		-	330	380 ⁽²⁾	μΑ

- 1. V_{DDA} = 3.3 V, T_A = -40 to 125 °C unless otherwise specified.
- 2. Guaranteed by design.
- 3. Guaranteed by characterization results.

Low-speed internal (LSI) RC oscillator

Table 47. LSI oscillator characteristics

	Symbol	Parameter	Min	Тур	Max	Unit
	f _{LSI} ⁽¹⁾	LSI frequency	26	38	56	kHz
	D _{LSI} ⁽²⁾	LSI oscillator frequency drift 0°C ≤T _A ≤ 85°C	-10	-	4	%
t,	su(LSI) ⁽³⁾	LSI oscillator startup time	-	-	200	μs
I	DD(LSI) ⁽³⁾	LSI oscillator power consumption	-	400	510	nA

- 1. Guaranteed by test in production.
- 2. This is a deviation for an individual part, once the initial frequency has been measured.
- 3. Guaranteed by design.

Multi-speed internal (MSI) RC oscillator

Table 48. MSI oscillator characteristics

Symbol	Parameter	Condition	Тур	Max	Unit
		MSI range 0	65.5	-	
		MSI range 1	131	-	kHz
	f_{MSI} Frequency after factory calibration, done at V_{DD} = 3.3 V and T_A = 25 °C	MSI range 2	262	-	NI IZ
f _{MSI}		MSI range 3	524	-	
	The are a sure of the	MSI range 4	1.05	-	
		MSI range 5	2.1	-	MHz
		MSI range 6	4.2	-	



Table 48. MSI oscillator characteristics (continued)

Symbol	Parameter	Condition	Тур	Max	Unit
ACC _{MSI}	Frequency error after factory calibration	-	±0.5	-	%
	MSI oscillator frequency drift 0 °C ≤T _A ⊴85 °C	-	±3	-	
		MSI range 0	- 8.9	+7.0	
		MSI range 1	- 7.1	+5.0	
D _{TEMP(MSI)} ⁽¹⁾		MSI range 2	- 6.4	+4.0	%
()	MSI oscillator frequency drift V_{DD} = 3.3 V, -40 °C \leq T _A \leq 110 °C	MSI range 3	- 6.2	+3.0	
		MSI range 4	- 5.2	+3.0	
		MSI range 5	- 4.8	+2.0	
		MSI range 6	- 4.7	+2.0	
D _{VOLT(MSI)} ⁽¹⁾	MSI oscillator frequency drift 1.65 V ≤V _{DD} ≤3.6 V, T _A = 25 °C	-	-	2.5	%/V
		MSI range 0	0.75	-	
	MSI oscillator power consumption	MSI range 1	1	-	
		MSI range 2	1.5	-	
I _{DD(MSI)} ⁽²⁾		MSI range 3	2.5	-	μΑ
		MSI range 4	4.5	-	
		MSI range 5	8	-	
		MSI range 6	15	-	
		MSI range 0	30	-	
		MSI range 1	20	-	
		MSI range 2	15	-	
		MSI range 3	10	-	
+	MSI oscillator startup time	MSI range 4	6	-	116
^t su(MSI)	INIST OSCINATOR STATUP TIME	MSI range 5	5	-	μs
		MSI range 6, Voltage range 1 and 2	3.5	-	
		MSI range 6, Voltage range 3	5	-	

Symbol	Parameter	Condition	Тур	Max	Unit
		MSI range 0	-	40	
		MSI range 1	-	20	
t _{STAB(MSI)} ⁽²⁾	N	MSI range 2	-	10	
		MSI range 3	-	4	μs
	MSI oscillator stabilization time	MSI range 4	-	2.5	
		MSI range 5	-	2	
		MSI range 6, Voltage range 1 and 2	-	2	
		MSI range 3, Voltage range 3	-	3	
f _{OVER(MSI)}	MSI oscillator frequency overshoot	Any range to range 5	-	4	MHz
		Any range to range 6	-	6	IVII IZ

Table 48. MSI oscillator characteristics (continued)

6.3.8 PLL characteristics

The parameters given in *Table 49* are derived from tests performed under ambient temperature and V_{DD} supply voltage conditions summarized in *Table 24*.

Value **Symbol Parameter** Unit Max⁽¹⁾ Min Typ PLL input clock⁽²⁾ MHz 2 24 f_{PLL IN} % PLL input clock duty cycle 45 55 PLL output clock 2 32 MHz f_{PLL_OUT} PLL input = 16 MHz t_{LOCK} 115 160 μs PLL VCO = 96 MHz Jitter ±600 Cycle-to-cycle jitter ps I_{DDA}(PLL) Current consumption on V_{DDA} 220 450 μΑ I_{DD}(PLL) Current consumption on $V_{\mbox{\scriptsize DD}}$ 120 150

Table 49. PLL characteristics

^{1.} This is a deviation for an individual part, once the initial frequency has been measured.

^{2.} Guaranteed by characterization results.

^{1.} Guaranteed by characterization results.

Take care of using the appropriate multiplier factors so as to have PLL input clock values compatible with the range defined by f_{PLL_OUT}.

6.3.9 Memory characteristics

RAM memory

Table 50. RAM and hardware registers

	Symbol	Parameter	Conditions	Min	Тур	Max	Unit
ĺ	VRM	Data retention mode ⁽¹⁾	Stop mode (or reset)	1.65	-	-	V

Minimum supply voltage without losing data stored in RAM (in Stop mode or under Reset) or in hardware registers (only in Stop mode).

Flash memory and data EEPROM

Table 51. Flash memory and data EEPROM characteristics

Symbol	Parameter	Conditions	Min	Тур	Max ⁽¹⁾	Unit
V _{DD}	Operating voltage Read / Write / Erase	-	1.65	-	3.6	V
+	Programming time for Erasing		-	3.28	3.94	ms
t _{prog}	word or half-page	Programming	-	3.28	3.94	1115
	Average current during the whole programming / erase operation	e whole programming /		500	700	μA
I _{DD}	Maximum current (peak) during the whole programming / erase operation	T _A = 25 °C, V _{DD} = 3.6 V	-	1.5	2.5	mA

^{1.} Guaranteed by design.

Table 52. Flash memory and data EEPROM endurance and retention

Symbol	Parameter	Conditions	Value	Unit
Syllibol	raiailletei	Conditions	Min ⁽¹⁾	Oille
	Cycling (erase / write) Program memory	T _A = -40°C to 105 °C	10	
N _{CYC} ⁽²⁾	Cycling (erase / write) EEPROM data memory	1 A = -40 C to 105 C	100	kcycles
CYC,	Cycling (erase / write) Program memory	data memory prase / write) memory	0.2	ROYOICS
	Cycling (erase / write) EEPROM data memory	T _A = -40°C to 125 °C	2	

Cumbal	Parameter	Conditions	Value	Unit
Symbol	Parameter	Conditions	Min ⁽¹⁾	Unit
	Data retention (program memory) after 10 kcycles at T _A = 85 °C	- T _{RFT} = +85 °C	30	
	Data retention (EEPROM data memory) after 100 kcycles at T _A = 85 °C	1 RET - +03 C	30	
t _{RET} ⁽²⁾	Data retention (program memory) after 10 kcycles at T _A = 105 °C	ory) after		voare
'RET`	Data retention (EEPROM data memory) after 100 kcycles at T _A = 105 °C	T _{RET} = +105 °C	10	years
	Data retention (program memory) after 200 cycles at T _A = 125 °C	T _{RFT} = +125 °C		
	Data retention (EEPROM data memory) after 2 kcycles at T _A = 125 °C	TREL - 1125 O		

Table 52. Flash memory and data EEPROM endurance and retention (continued)

6.3.10 EMC characteristics

Susceptibility tests are performed on a sample basis during device characterization.

Functional EMS (electromagnetic susceptibility)

While a simple application is executed on the device (toggling 2 LEDs through I/O ports). the device is stressed by two electromagnetic events until a failure occurs. The failure is indicated by the LEDs:

- Electrostatic discharge (ESD) (positive and negative) is applied to all device pins until a functional disturbance occurs. This test is compliant with the IEC 61000-4-2 standard.
- FTB: A Burst of Fast Transient voltage (positive and negative) is applied to V_{DD} and V_{SS} through a 100 pF capacitor, until a functional disturbance occurs. This test is compliant with the IEC 61000-4-4 standard.

A device reset allows normal operations to be resumed.

pins to induce a functional disturbance

The test results are given in *Table 53*. They are based on the EMS levels and classes defined in the application note AN1709 "EMC design guide for STM8, STM32 and legacy MCUs".

Symbol	Parameter	Conditions	Level/ Class
V _{FESD}	Voltage limits to be applied on any I/O pin to induce a functional disturbance	V_{DD} = 3.3 V, LQFP64, T_{A} = +25 °C, f_{HCLK} = 32 MHz conforms to IEC 61000-4-2	3B
V _{EFTB}	Fast transient voltage burst limits to be applied through 100 pF on V _{DD} and V _{SS}	$V_{DD} = 3.3 \text{ V, LQFP64, } T_{A} = +25 \text{ °C,} $ $f_{HCLK} = 32 \text{ MHz}$	4A

conforms to IEC 61000-4-4

Table 53. EMS characteristics

^{1.} Guaranteed by characterization results.

^{2.} Characterization is done according to JEDEC JESD22-A117.

Designing hardened software to avoid noise problems

EMC characterization and optimization are performed at component level with a typical application environment and simplified MCU software. It should be noted that good EMC performance is highly dependent on the user application and the software in particular.

Therefore it is recommended that the user applies EMC software optimization and prequalification tests in relation with the EMC level requested for his application.

Software recommendations

The software flowchart must include the management of runaway conditions such as:

- Corrupted program counter
- Unexpected reset
- Critical data corruption (control registers...)

Prequalification trials

Most of the common failures (unexpected reset and program counter corruption) can be reproduced by manually forcing a low state on the NRST pin or the oscillator pins for 1 second.

To complete these trials, ESD stress can be applied directly on the device, over the range of specification values. When unexpected behavior is detected, the software can be hardened to prevent unrecoverable errors occurring (see application note AN1015).

Electromagnetic Interference (EMI)

The electromagnetic field emitted by the device are monitored while a simple application is executed (toggling 2 LEDs through the I/O ports). This emission test is compliant with IEC 61967-2 standard which specifies the test board and the pin loading.

Symbol		Conditions	Monitored	Valu			
	Parameter		frequency band	8 MHz/ 4 MHz	8 MHz/ 16 MHz	8 MHz/ 32 MHz	Unit
	Peak ⁽¹⁾	Peak ⁽¹⁾ V _{DD} = 3.6 V, T _A = 25 °C, compliant with IEC 61967-2	0.1 to 30 MHz	-21	-15	-12	
9			30 to 130 MHz	-14	-12	-1	dΒμV
S _{EMI}			130 MHz to 1 GHz	-10	-11	-7	
	Level ⁽²⁾		0.1 MHz to 1 GHz	1	1	1	-

Table 54. EMI characteristics



^{1.} Refer to the EMI radiated test section of the application note AN1709 "EMC design guide for STM8, STM32 and legacy MCUs".

^{2.} Refer to the EMI level classification section of the application note AN1709 "EMC design guide for STM8, STM32 and legacy MCUs'

6.3.11 Electrical sensitivity characteristics

Based on three different tests (ESD, LU) using specific measurement methods, the device is stressed in order to determine its performance in terms of electrical sensitivity.

Electrostatic discharge (ESD)

Electrostatic discharges (a positive then a negative pulse separated by 1 second) are applied to the pins of each sample according to each pin combination. The sample size depends on the number of supply pins in the device (3 parts × (n+1) supply pins). This test conforms to the ANSI/JEDEC standard.

Table 55. ESD absolute maximum ratings

Symbol	Ratings	Conditions	Class	Maximum value ⁽¹⁾	Unit
V _{ESD(HBM)}	Electrostatic discharge voltage (human body model)	T _A = +25 °C, conforming to ANSI/JEDEC JS-001	2	2000	٧
V _{ESD(CDM)}	Electrostatic discharge voltage (charge device model)	T _A = +25 °C, conforming to ANSI/ESD STM5.3.1.	C4	500	V

^{1.} Guaranteed by characterization results.

Static latch-up

Two complementary static tests are required on six parts to assess the latch-up performance:

- A supply overvoltage is applied to each power supply pin
- A current injection is applied to each input, output and configurable I/O pin

These tests are compliant with EIA/JESD 78A IC latch-up standard.

Table 56. Electrical sensitivities

Symbol	Parameter	Conditions	Class
LU	Static latch-up class	T _A = +125 °C conforming to JESD78A	II level A

6.3.12 I/O current injection characteristics

As a general rule, current injection to the I/O pins, due to external voltage below V_{SS} or above V_{DD} (for standard pins) should be avoided during normal product operation. However, in order to give an indication of the robustness of the microcontroller in cases when abnormal injection accidentally happens, susceptibility tests are performed on a sample basis during device characterization.

Functional susceptibility to I/O current injection

While a simple application is executed on the device, the device is stressed by injecting current into the I/O pins programmed in floating input mode. While current is injected into the I/O pin, one at a time, the device is checked for functional failures.

The failure is indicated by an out of range parameter: ADC error above a certain limit (higher than 5 LSB TUE), out of conventional limits of induced leakage current on adjacent pins (out of $-5 \mu A/+0 \mu A$ range), or other functional failure (for example reset occurrence oscillator frequency deviation, LCD levels).

The test results are given in the Table 57.

Table 57. I/O current injection susceptibility

		Functional s		
Symbol	Description	Negative injection	Positive injection	Unit
	Injected current on BOOT0	-0	NA ⁽¹⁾	
I _{INJ}	Injected current on PA0, PA4, PA5, PA11, PA12, PC15, PH0 and PH1	-5	0	mA
	Injected current on any other FT, FTf pins	-5 ⁽²⁾	NA ⁽¹⁾	
	Injected current on any other pins	-5 ⁽²⁾	+5	

^{1.} Current injection is not possible.

^{2.} It is recommended to add a Schottky diode (pin to ground) to analog pins which may potentially inject negative currents

6.3.13 I/O port characteristics

General input/output characteristics

Unless otherwise specified, the parameters given in *Table 58* are derived from tests performed under the conditions summarized in *Table 24*. All I/Os are CMOS and TTL compliant.

Note:

For information on GPIO configuration, refer to application note AN4899 "STM32 GPIO configuration for hardware settings and low-power consumption" available from the ST website www.st.com. In addition, it is recommended to use a GPIO low-level voltage $\leq 0.1 \times V_{DD}$ and a GPIO high-level voltage $\geq 0.9 \times V_{DD}$, in order to have enough margin regarding the application transient or ripple on V_{DD} supply.

Table 58. I/O static characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{IL}	Input low level voltage	TC, FT, FTf, RST I/Os	-	-	0.3V _{DD}	
		BOOT0 pin	-	-	0.14V _{DD} ⁽¹⁾	
V _{IH}	Input high level voltage	All I/Os	0.7 V _{DD}	-	-	V
V.	I/O Schmitt trigger voltage hysteresis	Standard I/Os	-	10% V _{DD} ⁽³⁾	-	
V _{hys}	(2)	BOOT0 pin	1	0.01	-	
		$V_{\rm SS} \le V_{\rm IN} \le V_{\rm DD}$ All I/Os except for PA11, PA12, BOOT0 and FTf I/Os	ı	-	±50	
	Input leakage current ⁽⁴⁾	V _{SS} ≤V _{IN} ≤V _{DD} , PA11 and PA12 I/Os	-	-	-50/+250	nA
		V _{SS} ≤V _{IN} ≤V _{DD} FTf I/Os	-	-	±100	
l _{lkg}		V _{DD} ≤V _{IN} ≤5 V All I/Os except for PA11, PA12, BOOT0 and FTf I/Os	-	-	200	nA
		V _{DD} ≤V _{IN} ≤5 V FTf I/Os	-	-	500	
		V _{DD} ≤V _{IN} ≤5 V PA11, PA12 and BOOT0	-	-	10	μА
R _{PU}	Weak pull-up equivalent resistor ⁽⁵⁾	$V_{IN} = V_{SS}$	25	45	65	kΩ
R _{PD}	Weak pull-down equivalent resistor ⁽⁵⁾	$V_{IN} = V_{DD}$	25	45	65	kΩ
C _{IO}	I/O pin capacitance	-	-	5	-	pF

^{1.} Guaranteed by characterization.

^{4.} The max. value may be exceeded if negative current is injected on adjacent pins.



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^{2.} Hysteresis voltage between Schmitt trigger switching levels. Guaranteed by characterization results.

^{3.} With a minimum of 200 mV. Guaranteed by characterization results.

Pull-up and pull-down resistors are designed with a true resistance in series with a switchable PMOS/NMOS. This MOS/NMOS contribution to the series resistance is minimum (~10% order).

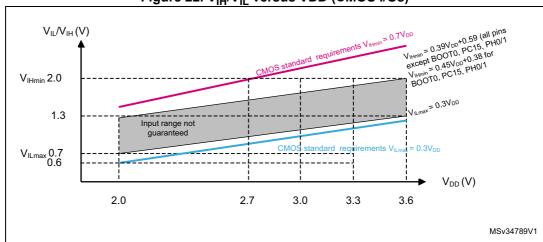
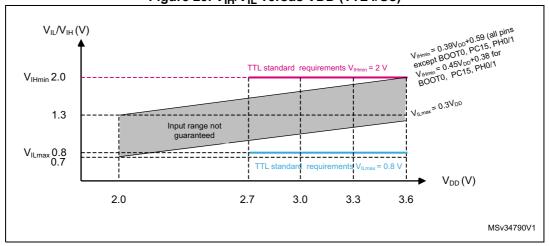


Figure 22. V_{IH}/V_{IL} versus VDD (CMOS I/Os)

Figure 23. V_{IH}/V_{IL} versus VDD (TTL I/Os)



Output driving current

The GPIOs (general purpose input/outputs) can sink or source up to ± 8 mA, and sink or source up to ± 15 mA with the non-standard V_{OL}/V_{OH} specifications given in *Table 59*.

In the user application, the number of I/O pins which can drive current must be limited to respect the absolute maximum rating specified in *Section 6.2*:

- The sum of the currents sourced by all the I/Os on V_{DD} , plus the maximum Run consumption of the MCU sourced on V_{DD} , cannot exceed the absolute maximum rating $I_{VDD(\Sigma)}$ (see *Table 22*).
- The sum of the currents sunk by all the I/Os on V_{SS} plus the maximum Run consumption of the MCU sunk on V_{SS} cannot exceed the absolute maximum rating I_{VSS(Σ)} (see *Table 22*).

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Output voltage levels

Unless otherwise specified, the parameters given in *Table 59* are derived from tests performed under ambient temperature and V_{DD} supply voltage conditions summarized in *Table 24*. All I/Os are CMOS and TTL compliant.

Table 59. Output voltage characteristics

Symbol	Parameter	Conditions	Min	Max	Unit
V _{OL} ⁽¹⁾	Output low level voltage for an I/O pin	CMOS port ⁽²⁾ , I _{IO} = +8 mA	-	0.4	
V _{OH} ⁽³⁾	Output high level voltage for an I/O pin	10^{-40} IIA $2.7 \text{ V} \le \text{V}_{DD} \le 3.6 \text{ V}$	V _{DD} -0.4	-	
V _{OL} ⁽¹⁾	Output low level voltage for an I/O pin	TTL port ⁽²⁾ , $I_{IO} = + 8 \text{ mA}$ $2.7 \text{ V} \leq V_{DD} \leq 3.6 \text{ V}$	-	0.4	
V _{OH} (3)(4)	Output high level voltage for an I/O pin	TTL port ⁽²⁾ , $I_{IO} = -6 \text{ mA}$ $2.7 \text{ V} \le V_{DD} \le 3.6 \text{ V}$	2.4	-	
V _{OL} ⁽¹⁾⁽⁴⁾	Output low level voltage for an I/O pin	I_{IO} = +15 mA 2.7 V \leq V _{DD} \leq 3.6 V	-	1.3	V
V _{OH} ⁽³⁾⁽⁴⁾	Output high level voltage for an I/O pin	I_{IO} = -15 mA 2.7 V \leq V _{DD} \leq 3.6 V	V _{DD} -1.3	-	
V _{OL} ⁽¹⁾⁽⁴⁾	Output low level voltage for an I/O pin	I _{IO} = +4 mA 1.65 V ≤V _{DD} < 3.6 V	-	0.45	
V _{OH} ⁽³⁾⁽⁴⁾	Output high level voltage for an I/O pin	$I_{IO} = -4 \text{ mA}$ 1.65 V \leq V _{DD} \leq 3.6 V	V _{DD} -0.45	-	
V _{OLFM+} (1)(4)	Output low level voltage for an FTf	$I_{IO} = 20 \text{ mA}$ 2.7 V \leq V _{DD} \leq 3.6 V	-	0.4	
VOLFM+```	I/O pin in Fm+ mode	I_{IO} = 10 mA 1.65 V \leq V _{DD} \leq 3.6 V	-	0.4	

The I_{IO} current sunk by the device must always respect the absolute maximum rating specified in Table 22.
 The sum of the currents sunk by all the I/Os (I/O ports and control pins) must always be respected and must not exceed ΣI_{IO(PIN)}.

 $^{2. \}quad {\sf TTL} \ {\sf and} \ {\sf CMOS} \ {\sf outputs} \ {\sf are} \ {\sf compatible} \ {\sf with} \ {\sf JEDEC} \ {\sf standards} \ {\sf JESD36} \ {\sf and} \ {\sf JESD52}.$

The I_{IO} current sourced by the device must always respect the absolute maximum rating specified in Table 22. The sum of the currents sourced by all the I/Os (I/O ports and control pins) must always be respected and must not exceed ΣI_{IO(PIN)}.

^{4.} Guaranteed by characterization results.

Input/output AC characteristics

The definition and values of input/output AC characteristics are given in *Figure 24* and *Table 60*, respectively.

Unless otherwise specified, the parameters given in *Table 60* are derived from tests performed under ambient temperature and V_{DD} supply voltage conditions summarized in *Table 24*.

Table 60. I/O AC characteristics⁽¹⁾

OSPEEDRx[1:0] bit value ⁽¹⁾	Symbol	Parameter	Conditions	Min	Max ⁽²⁾	Unit	
	f us	Maximum frequency ⁽³⁾	$C_L = 50 \text{ pF}, V_{DD} = 2.7 \text{ V to } 3.6 \text{ V}$	-	400	kHz	
00	f _{max(IO)out}	maximam nequency	$C_L = 50 \text{ pF}, V_{DD} = 1.65 \text{ V to } 2.7 \text{ V}$	-	100	NI IZ	
00	t _{f(IO)out}	Output rise and fall time	$C_L = 50 \text{ pF}, V_{DD} = 2.7 \text{ V to } 3.6 \text{ V}$	-	125	ns	
	t _{r(IO)out}	Output fise and fair time	$C_L = 50 \text{ pF}, V_{DD} = 1.65 \text{ V to } 2.7 \text{ V}$	-	320	113	
	f	Maximum frequency ⁽³⁾	$C_L = 50 \text{ pF}, V_{DD} = 2.7 \text{ V to } 3.6 \text{ V}$	-	2	MHz	
0.4	f _{max(IO)out}	Maximum frequency.	C _L = 50 pF, V _{DD} = 1.65 V to 2.7 V	-	0.6	IVII IZ	
01	t _{f(IO)out}	Output rise and fall time	C _L = 50 pF, V _{DD} = 2.7 V to 3.6 V	-	30	no	
	t _{r(IO)out}	Output rise and fall time	C _L = 50 pF, V _{DD} = 1.65 V to 2.7 V	-	65	ns	
	F	Marian (3)	C _L = 50 pF, V _{DD} = 2.7 V to 3.6 V	-	10	N 41 1-	
10	F _{max(IO)out}	Maximum frequency ⁽³⁾	C _L = 50 pF, V _{DD} = 1.65 V to 2.7 V	-	2	MHz	
10	t _{f(IO)out}		C _L = 50 pF, V _{DD} = 2.7 V to 3.6 V	-	13		
	t _{r(IO)out}		C _L = 50 pF, V _{DD} = 1.65 V to 2.7 V	-	28	ns	
	F	t Maximum frequency ⁽³⁾	Maximum fra quan au (3)	$C_L = 30 \text{ pF}, V_{DD} = 2.7 \text{ V to } 3.6 \text{ V}$	-	35	N 41 1-
44	F _{max(IO)out}		C _L = 50 pF, V _{DD} = 1.65 V to 2.7 V	-	10	MHz	
11	t _{f(IO)out}	Outside and fall times	C _L = 30 pF, V _{DD} = 2.7 V to 3.6 V	-	6		
	t _{r(IO)out}	Output rise and fall time	C _L = 50 pF, V _{DD} = 1.65 V to 2.7 V	-	17	ns	
	f _{max(IO)out}	Maximum frequency ⁽³⁾		-	1	MHz	
	t _{f(IO)out}	Output fall time	$C_L = 50 \text{ pF}, V_{DD} = 2.5 \text{ V to } 3.6 \text{ V}$	-	10		
Fm+	t _{r(IO)out}	Output rise time		-	30	ns	
configuration ⁽⁴⁾	f _{max(IO)out}	Maximum frequency ⁽³⁾		-	350	KHz	
	t _{f(IO)out}	Output fall time	$C_L = 50 \text{ pF}, V_{DD} = 1.65 \text{ V to } 3.6 \text{ V}$	-	15		
	t _{r(IO)out}	Output rise time		-	60	ns	
-	t _{EXTIpw}	Pulse width of external signals detected by the EXTI controller	-	8	-	ns	

^{1.} The I/O speed is configured using the OSPEEDRx[1:0] bits. Refer to the line reference manual for a description of GPIO Port configuration register.



^{2.} Guaranteed by design.

^{3.} The maximum frequency is defined in Figure 24.

^{4.} When Fm+ configuration is set, the I/O speed control is bypassed. Refer to the line reference manual for a detailed description of Fm+ I/O configuration.

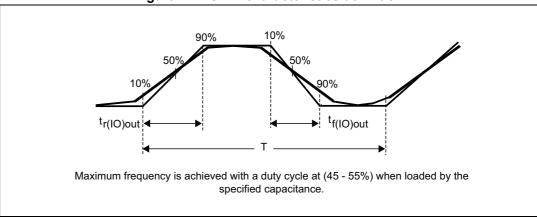


Figure 24. I/O AC characteristics definition

6.3.14 NRST pin characteristics

The NRST pin input driver uses CMOS technology. It is connected to a permanent pull-up resistor, R_{PU}, except when it is internally driven low (see *Table 61*).

Unless otherwise specified, the parameters given in *Table 61* are derived from tests performed under ambient temperature and V_{DD} supply voltage conditions summarized in *Table 24*.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{IL(NRST)} ⁽¹⁾	NRST input low level voltage	-	V_{SS}	-	0.8	
V _{IH(NRST)} ⁽¹⁾	NRST input high level voltage	-	1.4	-	V_{DD}	
V _{OL(NRST)} ⁽¹⁾	NRST output low level	I _{OL} = 2 mA 2.7 V < V _{DD} < 3.6 V	-	-	0.4	V
VOL(NRST)	voltage	I _{OL} = 1.5 mA 1.65 V < V _{DD} < 2.7 V	-	-	0.4	
V _{hys(NRST)} ⁽¹⁾	NRST Schmitt trigger voltage hysteresis	-	ı	10%V _{DD} ⁽²⁾	ı	mV
R _{PU}	Weak pull-up equivalent resistor ⁽³⁾	$V_{IN} = V_{SS}$	25	45	65	kΩ
V _{F(NRST)} ⁽¹⁾	NRST input filtered pulse	-	-	-	50	ns
V _{NF(NRST)} ⁽¹⁾	NRST input not filtered pulse	-	350	-	-	ns

Table 61. NRST pin characteristics

^{1.} Guaranteed by design.

^{2. 200} mV minimum value

^{3.} The pull-up is designed with a true resistance in series with a switchable PMOS. This PMOS contribution to the series resistance is around 10%.

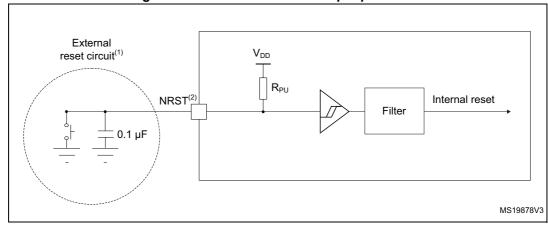


Figure 25. Recommended NRST pin protection

- The reset network protects the device against parasitic resets.
- 2. The external capacitor must be placed as close as possible to the device.
- The user must ensure that the level on the NRST pin can go below the V_{IL(NRST)} max level specified in Table 61. Otherwise the reset will not be taken into account by the device.

6.3.15 12-bit ADC characteristics

Unless otherwise specified, the parameters given in *Table 62* are derived from tests performed under ambient temperature, f_{PCLK} frequency and V_{DDA} supply voltage conditions summarized in *Table 24: General operating conditions*.

Note: It is recommended to perform a calibration after each power-up.

Symbol Min Unit **Parameter Conditions** Typ Max Fast channel 1.65 3.6 Analog supply voltage for V V_{DDA} ADC ON $1.75^{(1)}$ Standard channel 3.6 V_{REF+} Positive reference voltage 1.65 ٧ V_{DDA} 1.14 Msps 200 Current consumption of the ADC on VDDAand VREF+ 10 ksps 40 μΑ I_{DDA (ADC)} 1.14 Msps 70 Current consumption of the ADC on $V_{DD}^{(2)}$ 10 ksps 1 Voltage scaling Range 1 0.14 16 ADC clock frequency Voltage scaling Range 2 0.14 8 f_{ADC} MHz Voltage scaling Range 3 0.14 4 $f_{S}^{(3)}$ 0.01 Sampling rate 12-bit resolution 1.14 MHz $f_{ADC} = 16 \text{ MHz},$ 941 kHz 12-bit resolution f_{TRIG}⁽³⁾ External trigger frequency

Table 62. ADC characteristics



1/f_{ADC}

17

 V_{REF+}

0

92/141 DS10152 Rev 10

Conversion voltage range

 V_{AIN}

Table 62. ADC characteristics (continued)

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{AIN} ⁽³⁾	External input impedance	See Equation 1 and Table 63 for details	-	-	50	kΩ
R _{ADC} (3)(4)	Sampling switch resistance	-	-	-	1	kΩ
C _{ADC} ⁽³⁾	Internal sample and hold capacitor	-	-	-	8	pF
t _{CAL} (3)(5)	Calibration time	f _{ADC} = 16 MHz		5.2		μs
CAL' /` /	Calibration time	-		83		1/f _{ADC}
W _{LATENCY} ⁽⁶⁾		ADC clock = HSI16	1.5 ADC cycles + 2 f _{PCLK} cycles	ı	1.5 ADC cycles + 3 f _{PCLK} cycles	-
	ADC_DR register write latency	ADC clock = PCLK/2	-	4.5	-	f _{PCLK} cycle
		ADC clock = PCLK/4	-	8.5	-	f _{PCLK} cycle
		$f_{ADC} = f_{PCLK}/2 = 16 \text{ MHz}$		0.266		μs
		$f_{ADC} = f_{PCLK}/2$	8.5		1/f _{PCLK}	
t _{latr} (3)	Trigger conversion latency	$f_{ADC} = f_{PCLK}/4 = 8 \text{ MHz}$		0.516		
		$f_{ADC} = f_{PCLK}/4$	16.5			1/f _{PCLK}
		$f_{ADC} = f_{HSI16} = 16 \text{ MHz}$	0.252	-	0.260	μs
Jitter _{ADC}	ADC jitter on trigger conversion	f _{ADC} = f _{HSI16}	-	1	-	1/f _{HSI16}
ts ⁽³⁾	Sampling time	f _{ADC} = 16 MHz	0.093	-	10.03	μs
ıs. ,	Sampling time	-	1.5	-	160.5	1/f _{ADC}
t _{UP_LDO} (3)(5)	Internal LDO power-up time	-	-	-	10	μs
t _{STAB} (3)(5)	ADC stabilization time	-		14		1/f _{ADC}
. (3)	Total conversion time	f _{ADC} = 16 MHz, 12-bit resolution	0.875	-	10.81	μs
t _{ConV} ⁽³⁾	(including sampling time)	12-bit resolution	14 to 173 (t _S for sampling +12.5 for successive approximation)		1/f _{ADC}	

^{1.} V_{DDA} minimum value can be decreased in specific temperature conditions. Refer to Table 63: R_{AIN} max for f_{ADC} = 16 MHz.



^{2.} A current consumption proportional to the APB clock frequency has to be added (see *Table 38: Peripheral current consumption in Run or Sleep mode*).

^{3.} Guaranteed by design.

Standard channels have an extra protection resistance which depends on supply voltage. Refer to Table 63: R_{AIN} max for f_{ADC} = 16 MHz.

^{5.} This parameter only includes the ADC timing. It does not take into account register access latency.

^{6.} This parameter specifies the latency to transfer the conversion result into the ADC_DR register. EOC bit is set to indicate the conversion is complete and has the same latency.

Equation 1: R_{AIN} max formula

$$R_{AIN} < \frac{T_S}{f_{ADC} \times C_{ADC} \times ln(2^{N+2})} - R_{ADC}$$

The simplified formula above (Equation 1) is used to determine the maximum external impedance allowed for an error below 1/4 of LSB. Here N = 12 (from 12-bit resolution).

Table 63. R_{AIN} max for $f_{ADC} = 16 \text{ MHz}^{(1)}$

		R _{AIN} max for	R _{AIN} max for standard channels (kΩ)						
T _s t _S (μs)		fast channels (kΩ)	V _{DD} > 2.7 V	V _{DD} > 2.4 V	V _{DD} > 2.0 V	V _{DD} > 1.8 V	V _{DD} > 1.75 V	V _{DD} > 1.65 V and T _A > -10 °C	V _{DD} > 1.65 V and T _A > 25 °C
1.5	0.09	0.5	< 0.1	NA	NA	NA	NA	NA	NA
3.5	0.22	1	0.2	< 0.1	NA	NA	NA	NA	NA
7.5	0.47	2.5	1.7	1.5	< 0.1	NA	NA	NA	NA
12.5	0.78	4	3.2	3	1	NA	NA	NA	NA
19.5	1.22	6.5	5.7	5.5	3.5	NA	NA	NA	< 0.1
39.5	2.47	13	12.2	12	10	NA	NA	NA	5
79.5	4.97	27	26.2	26	24	< 0.1	NA	NA	19
160.5	10.03	50	49.2	49	47	32	< 0.1	< 0.1	42

^{1.} Guaranteed by design.

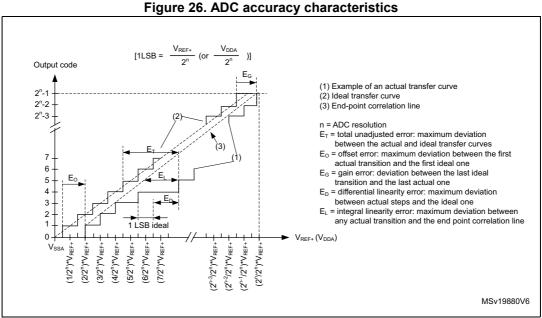
Table 64. ADC accuracy⁽¹⁾⁽²⁾⁽³⁾

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
ET	Total unadjusted error		-	2	4	
EO	Offset error		-	1	2.5	
EG	Gain error		-	1	2	LSB
EL	Integral linearity error		-	1.5	2.5	
ED	Differential linearity error	1.65 V < V _{DDA} = V _{REF+} < 3.6 V, range 1/2/3	-	1	1.5	
	Effective number of bits		10.2	11		
ENOB	Effective number of bits (16-bit mode oversampling with ratio =256) ⁽⁴⁾		11.3	12.1	-	bits
SINAD	Signal-to-noise distortion		63	69	-	
	Signal-to-noise ratio		63	69	-	dB
SNR	Signal-to-noise ratio (16-bit mode oversampling with ratio =256) ⁽⁴⁾		70	76	-	
THD	Total harmonic distortion		-	-85	-73	

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
ET	Total unadjusted error		-	2	5	
EO	Offset error		-	1	2.5	
EG	Gain error		-	1	2	LSB
EL	Integral linearity error		-	1.5	3	
ED	Differential linearity error	1.65 V < V _{REF+} < V _{DDA} < 3.6 V, range 1/2/3	-	1	2	
ENOB	Effective number of bits		10.0	11.0	-	bits
SINAD	Signal-to-noise distortion		62	69	-	
SNR	Signal-to-noise ratio		61	69	-	dB
THD	Total harmonic distortion		-	-85	-65	

Table 64. ADC accuracy(1)(2)(3) (continued)

- 1. ADC DC accuracy values are measured after internal calibration.
- ADC Accuracy vs. Negative Injection Current: Injecting negative current on any of the standard (non-robust) analog input pins should be avoided as this significantly reduces the accuracy of the conversion being performed on another analog input. It is recommended to add a Schottky diode (pin to ground) to standard analog pins which may potentially inject negative current. Any positive injection current within the limits specified for $I_{INJ(PIN)}$ and $\Sigma I_{INJ(PIN)}$ in Section 6.3.12 does not affect the ADC accuracy.
- 3. Better performance may be achieved in restricted V_{DDA}, frequency and temperature ranges.
- 4. This number is obtained by the test board without additional noise, resulting in non-optimized value for oversampling mode.



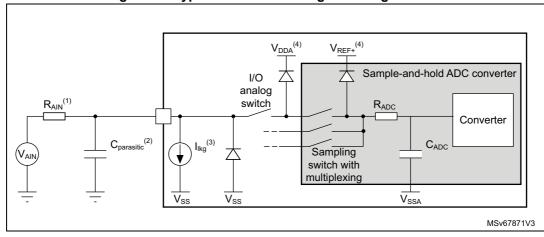


Figure 27. Typical connection diagram using the ADC

- 1. Refer to *Table 62: ADC characteristics* for the values of R_{AIN} and C_{ADC}.
- C_{parasitic} represents the capacitance of the PCB (dependent on soldering and PCB layout quality) plus the pad capacitance (refer to *Table 58: I/O static characteristics*). A high C_{parasitic} value downgrades conversion accuracy. To remedy this, f_{ADC} must be reduced.
- 3. Refer to Table 58: I/O static characteristics for the value of I_{lkq}.
- 4. Refer to Figure 9: Power supply scheme.

General PCB design guidelines

Power supply decoupling should be performed as shown in *Figure 28* or *Figure 29*, depending on whether V_{REF+} is connected to V_{DDA} or not. The 10 nF capacitors should be ceramic (good quality). They should be placed as close as possible to the chip.

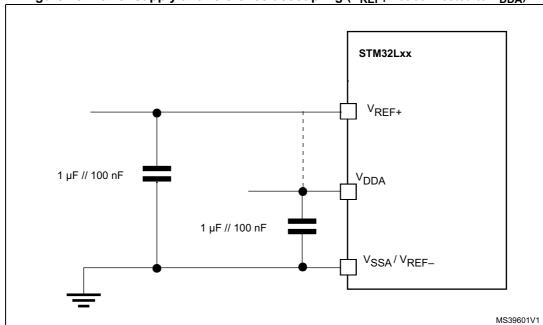


Figure 28. Power supply and reference decoupling (V_{REF+} not connected to V_{DDA})

4

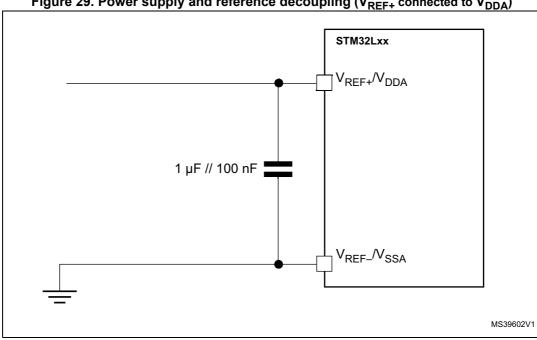


Figure 29. Power supply and reference decoupling (V_{REF+} connected to V_{DDA})

6.3.16 DAC electrical characteristics

Data guaranteed by design, not tested in production, unless otherwise specified.

Table 65. DAC characteristics

Symbol	Parameter	Cond	litions	Min	Тур	Max	Unit	
V_{DDA}	Analog supply voltage	-		1.8	-	3.6	V	
V _{REF+}	Reference supply voltage	V _{REF+} must always be below V _{DDA}		1.8	-	3.6	٧	
V _{REF-}	Lower reference voltage	-			V _{SSA}		V	
I _{DDVREF+} (1)	Current consumption on V _{REF+}	No load, mid (0x800)	ldle code	-	130	220		
'DDVREF+` '	supply $V_{REF+} = 3.3 \text{ V}$	No load, wor (0x000)	st code	-	220	350	μΑ	
I _{DDA} ⁽²⁾	Current consumption on V _{DDA} supply,	No load, middle code (0x800)		-	210	320		
	V _{DDA} = 3.3 V	No load, worst code (0xF1C)		-	320	520	μA	
R _I ⁽³⁾	Resistive load	DAC output	R _L connected to V _{SSA}	5	-	-	10	
RL ^(*)		ON	R _L connected to V _{DDA}	25	-	-	kΩ	
C _L ⁽³⁾	Capacitive load	DAC output	buffer ON	-	-	50	pF	
R _O	Output impedance	DAC output	buffer OFF	12	16	20	kΩ	
V		DAC output buffer ON		0.2	-	V _{DDA} – 0.2	٧	
V _{DAC_OUT}	Voltage on DAC_OUT output	DAC output buffer OFF		0.5	-	V _{REF+} – 1LSB	mV	

Table 65. DAC characteristics (continued)

Symbol	Parameter	Conditions	Min	Тур	Max	Unit	
DNL ⁽²⁾	Differential non linearity ⁽⁴⁾	$C_L \le 50$ pF, $R_L \ge 5$ k Ω DAC output buffer ON	-	1.5	3		
		No R _{LOAD} , C _L ≤ 50 pF DAC output buffer OFF	-	1.5	3		
INL ⁽²⁾	Integral non linearity ⁽⁵⁾	$C_L \le 50 \text{ pF, } R_L \ge 5 \text{ k}\Omega$ DAC output buffer ON	_	2	4		
	integral non lineanty.	No R_{LOAD} , $C_{L} \le 50 pF$ DAC output buffer OFF	-	2	4	LSB	
Offset ⁽²⁾	Offset error at code 0x800 ⁽⁶⁾	$C_L \le 50$ pF, $R_L \ge 5$ k Ω DAC output buffer ON	-	±10	±25		
	Offset error at code 0x800 (9)	No R _{LOAD} , C _L ≤50 pF DAC output buffer OFF	-	±5	±8		
Offset1 ⁽²⁾	Offset error at code 0x001 ⁽⁷⁾	No R _{LOAD} , C _L ≤ 50 pF DAC output buffer OFF	-	±1.5	±5		
(0)	Offset error temperature coefficient (code 0x800)	$V_{DDA} = 3.3V$ $V_{REF+} = 3.0 V$ $T_{A} = 0 \text{ to } 50 ^{\circ}\text{C}$ DAC output buffer OFF	-20	-10	0	μV/°C	
dOffset/dT ⁽²⁾		$V_{DDA} = 3.3V$ $V_{REF+} = 3.0 V$ $T_{A} = 0 \text{ to } 50 ^{\circ}\text{C}$ DAC output buffer ON	0	20	50	μν/ Ο	
Gain ⁽²⁾	Gain error ⁽⁸⁾	$C_L \le 50$ pF, $R_L \ge 5$ k Ω DAC output buffer ON	-	+0.1 / -0.2%	+0.2 / -0.5%	0/	
Gain	Gain enor	No R _{LOAD} , C _L ≤ 50 pF DAC output buffer OFF	-	+0 / -0.2%	+0 / -0.4%	- %	
dGain/dT ⁽²⁾	Gain error temperature	$V_{DDA} = 3.3V$ $V_{REF+} = 3.0 V$ $T_{A} = 0 \text{ to } 50 ^{\circ}\text{C}$ DAC output buffer OFF	-10	-2	0	uV/°C	
ugaii/u1	coefficient	$V_{DDA} = 3.3V$ $V_{REF+} = 3.0 V$ $T_{A} = 0 \text{ to } 50 ^{\circ}\text{C}$ DAC output buffer ON	-40	-8	0	- μV/°C	
TUE ⁽²⁾	Total unadjusted error	$C_L \le 50$ pF, $R_L \ge 5$ k Ω DAC output buffer ON	-	12	30	LSB	
TUE`	Total unaujusted effor	No R_{LOAD} , $C_{L} \le 50 pF$ DAC output buffer OFF	-	8	12	LOD	



Symbol	Parameter	Conditions	Min	Тур	Max	Unit
t _{SETTLING}	Settling time (full scale: for a 12-bit code transition between the lowest and the highest input codes till DAC_OUT reaches final value ±1LSB	$C_L \le 50 \text{ pF, } R_L \ge 5 \text{ k}\Omega$	-	7	12	μs
Update rate	Max frequency for a correct DAC_OUT change (95% of final value) with 1 LSB variation in the input code	$C_L \le 50 \text{ pF, } R_L \ge 5 \text{ k}\Omega$	-	-	1	Msps
t _{WAKEUP}	Wake-up time from off state (setting the ENx bit in the DAC Control register) ⁽⁹⁾	$C_L \le 50 \text{ pF, } R_L \ge 5 \text{ k}\Omega$	-	9	15	μs
PSRR+	V _{DDA} supply rejection ratio (static DC measurement)	$C_L \le 50 \text{ pF, } R_L \ge 5 \text{ k}\Omega$	-	-60	-35	dB

Table 65. DAC characteristics (continued)

- 1. Guaranteed by characterization results.
- 2. Guaranteed by design, not tested in production.
- 3. Connected between DAC_OUT and V_{SSA}.
- 4. Difference between two consecutive codes 1 LSB.
- 5. Difference between measured value at Code i and the value at Code i on a line drawn between Code 0 and last Code 4095.
- 6. Difference between the value measured at Code (0x800) and the ideal value = $V_{REF+}/2$.
- 7. Difference between the value measured at Code (0x001) and the ideal value.
- Difference between ideal slope of the transfer function and measured slope computed from code 0x000 and 0xFFF when buffer is OFF, and from code giving 0.2 V and (V_{DDA} – 0.2) V when buffer is ON.
- 9. In buffered mode, the output can overshoot above the final value for low input code (starting from min value).

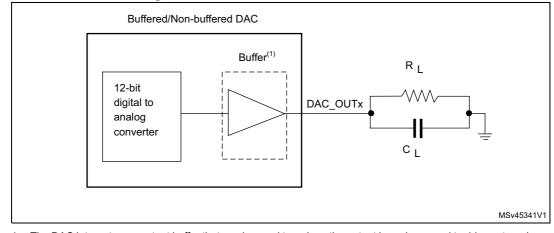


Figure 30. 12-bit buffered/non-buffered DAC

 The DAC integrates an output buffer that can be used to reduce the output impedance and to drive external loads directly without the use of an external operational amplifier. The buffer can be bypassed by configuring the BOFFx bit in the DAC_CR register.

6.3.17 Temperature sensor characteristics

Table 66. Temperature sensor calibration values

Calibration value name	Description	Memory address
TS_CAL1	TS ADC raw data acquired at temperature of 30 °C, V _{DDA} = 3 V	0x1FF8 007A - 0x1FF8 007B
TS_CAL2	TS ADC raw data acquired at temperature of 130 °C, V _{DDA} = 3 V	0x1FF8 007E - 0x1FF8 007F

Table 67. Temperature sensor characteristics

Symbol	Parameter		Тур	Max	Unit
T _L ⁽¹⁾	V _{SENSE} linearity with temperature	-	±1	<u>+2</u>	°C
Avg_Slope ⁽¹⁾	Average slope	1.48	1.61	1.75	mV/°C
V ₁₃₀	Voltage at 130°C ±5°C ⁽²⁾	640	670	700	mV
I _{DDA(TEMP)} (3)	Current consumption	-	3.4	6	μA
t _{START} (3)	Startup time	-	-	10	110
T _{S_temp} ⁽⁴⁾⁽³⁾	ADC sampling time when reading the temperature	10	-	-	μs

- 1. Guaranteed by characterization results.
- 2. Measured at V_{DD} = 3 V ±10 mV. V130 ADC conversion result is stored in the TS_CAL2 byte.
- 3. Guaranteed by design.
- 4. Shortest sampling time can be determined in the application by multiple iterations.

6.3.18 Comparators

Table 68. Comparator 1 characteristics

Symbol	Parameter	Conditions	Min ⁽¹⁾	Тур	Max ⁽¹⁾	Unit
V_{DDA}	Analog supply voltage	-	1.65		3.6	V
V _{IN}	Comparator 1 input voltage range	-	0.6	-	V_{DDA}	V
t _{START}	Comparator startup time	-	-	7	10	ue
t _d	Propagation delay ⁽²⁾	-	-	3	10	μs
V _{offset}	Comparator offset	-	-	±3	±10	mV
d _{Voffset} /dt	Comparator offset variation in worst voltage stress conditions	$V_{DDA} = 3.6 \text{ V}, V_{IN+} = 0 \text{ V},$ $V_{IN-} = V_{REFINT}, T_A = 25 ^{\circ}C$	0	1.5	10	mV/1000 h
I _{COMP1}	Current consumption ⁽³⁾	-	-	160	260	nA

^{1.} Guaranteed by characterization.

3. Comparator consumption only. Internal reference voltage not included.

^{2.} The delay is characterized for 100 mV input step with 10 mV overdrive on the inverting input, the non-inverting input set to the reference.

Table 69. Comparator 2 characteristics

Symbol	Parameter	Conditions	Min	Тур	Max ⁽¹⁾	Unit	
V_{DDA}	Analog supply voltage	-	1.65	-	3.6	V	
V _{IN}	Comparator 2 input voltage range	-	0	-	V_{DDA}	V	
+	Comparator startup time	Fast mode	-	15	20		
t _{START}	Comparator startup time	Slow mode	-	20	25		
+	Propagation delay ⁽²⁾ in slow mode	1.65 V ≤V _{DDA} ≤2.7 V	-	1.8	3.5		
t _{d slow}		2.7 V ≤V _{DDA} ≤3.6 V	-	2.5	6	- μs -	
+	Propagation delay ⁽²⁾ in fast mode	1.65 V ≤V _{DDA} ≤2.7 V	-	0.8	2		
t _{d fast}		2.7 V ≤V _{DDA} ≤3.6 V	-	1.2	4		
V _{offset}	Comparator offset error		-	<u>±</u> 4	±20	mV	
d _{Threshold} /	Threshold voltage temperature coefficient	$V_{DDA} = 3.3V, T_A = 0 \text{ to } 50 \text{ °C},$ $V = V_{REFINT},$ $3/4 V_{REFINT},$ $1/2 V_{REFINT},$ $1/4 V_{REFINT}.$	-	15	30	ppm /°C	
1	Current consumption(3)	Fast mode	-	3.5	5		
I _{COMP2}	Current consumption ⁽³⁾	Slow mode	-	0.5	2	μA	

^{1.} Guaranteed by characterization results.

^{2.} The delay is characterized for 100 mV input step with 10 mV overdrive on the inverting input, the non-inverting input set to the reference.

^{3.} Comparator consumption only. Internal reference voltage (required for comparator operation) is not included.

6.3.19 Timer characteristics

TIM timer characteristics

The parameters given in the *Table 70* are guaranteed by design.

Refer to Section 6.3.13: I/O port characteristics for details on the input/output alternate function characteristics (output compare, input capture, external clock, PWM output).

Symbol	Parameter	Conditions	Min	Max	Unit				
t	Timer resolution time		1	-	t _{TIMxCLK}				
^t res(TIM)	Time resolution time	f _{TIMxCLK} = 32 MHz	31.25	-	ns				
f _{EXT}	Timer external clock frequency on CH1		0	f _{TIMxCLK} /2	MHz				
	to CH4	f _{TIMxCLK} = 32 MHz	0	16	MHz				
Res _{TIM}	Timer resolution	-		16	bit				
	16-bit counter clock period when	-	1	65536	t _{TIMxCLK}				
t _{COUNTER}	internal clock is selected (timer's prescaler disabled)	f _{TIMxCLK} = 32 MHz	0.0312	2048	μs				
t _{MAX_COUNT}	Maximum possible count	-	-	65536 × 65536	t _{TIMxCLK}				
	Iwaxiiiidiii possible coulit	f _{TIMxCLK} = 32 MHz	-	134.2	S				

Table 70. TIMx characteristics⁽¹⁾

6.3.20 Communications interfaces

I²C interface characteristics

The I²C interface meets the timings requirements of the I²C-bus specification and user manual rev. 03 for:

- Standard-mode (Sm): with a bit rate up to 100 kbit/s
- Fast-mode (Fm): with a bit rate up to 400 kbit/s
- Fast-mode Plus (Fm+): with a bit rate up to 1 Mbit/s.

The I^2C timing requirements are guaranteed by design when the I^2C peripheral is properly configured (refer to the reference manual for details). The SDA and SCL I/O requirements are met with the following restrictions: the SDA and SCL I/O pins are not "true" open-drain. When configured as open-drain, the PMOS connected between the I/O pin and VDDIOx is disabled, but is still present. Only FTf I/O pins support Fm+ low level output current maximum requirement (refer to Section 6.3.13: I/O port characteristics for the I2C I/Os characteristics).

All I²C SDA and SCL I/Os embed an analog filter (see *Table 71* for the analog filter characteristics).

^{1.} TIMx is used as a general term to refer to the TIM2, TIM6, TIM21, and TIM22 timers.

The analog spike filter is compliant with I²C timings requirements only for the following voltage ranges:

- Fast mode Plus: 2.7 V ≤V_{DD} ≤3.6 V and voltage scaling Range 1
- Fast mode:
 - 2 V ≤V_{DD} ≤3.6 V and voltage scaling Range 1 or Range 2.
 - V_{DD} < 2 V, voltage scaling Range 1 or Range 2, C_{load} < 200 pF.

In other ranges, the analog filter should be disabled. The digital filter can be used instead.

In Standard mode, no spike filter is required. Note:

Table 71. I2C analog filter characteristics⁽¹⁾

Symbol	Parameter	Conditions	Min	Max	Unit
t _{AF}	Maximum pulse width of spikes that are suppressed by the analog filter	Range 1		100 ⁽³⁾	
		Range 2	50 ⁽²⁾	-	ns
		Range 3		-	

- 1. Guaranteed by characterization results.
- 2. Spikes with widths below t_{AF(min)} are filtered.
- 3. Spikes with widths above $t_{AF(max)}$ are not filtered

SPI characteristics

Unless otherwise specified, the parameters given in the following tables are derived from tests performed under ambient temperature, f_{PCLKx} frequency and V_{DD} supply voltage conditions summarized in Table 24.

Refer to Section 6.3.12: I/O current injection characteristics for more details on the input/output alternate function characteristics (NSS, SCK, MOSI, MISO).

Table 72. SPI characteristics in voltage Range 1 (1)

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
f _{SCK} 1/t _{c(SCK)}	SPI clock frequency	Master mode	-	-	16	-
		Slave mode receiver			16	
		Slave mode Transmitter 1.71 <v<sub>DD<3.6V</v<sub>	-	-	12 ⁽²⁾	MHz
		Slave mode Transmitter 2.7 <v<sub>DD<3.6V</v<sub>	-	-	16 ⁽²⁾	
Duty _(SCK)	Duty cycle of SPI clock frequency	Slave mode	30	50	70	%





Table 72. SPI characteristics in voltage Range 1 ⁽¹⁾ (continued)

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
t _{su(NSS)}	NSS setup time	Slave mode, SPI presc = 2	4*Tpclk	-	-	
t _{h(NSS)}	NSS hold time	Slave mode, SPI presc = 2	2*Tpclk	ı	-	
t _{w(SCKH)} t _{w(SCKL)}	SCK high and low time	Master mode	Tpclk-2	Tpclk	Tpclk+	
t _{su(MI)}	Data input setup time	Master mode	0	-	-	
t _{su(SI)}	Data input setup time	Slave mode	3	-	-	
t _{h(MI)}	Data input hold time	Master mode	7	-	-	
t _{h(SI)}		Slave mode	3.5	-	-	ns
t _{a(SO}	Data output access time	Slave mode	15	-	36	
t _{dis(SO)}	Data output disable time	Slave mode	10	-	30	
+	SO) Data output valid time	Slave mode 1.65 V <v<sub>DD<3.6 V</v<sub>	-	18	41	
t _{v(SO)}		Slave mode 2.7 V <v<sub>DD<3.6 V</v<sub>	-	18	25	
t _{v(MO)}		Master mode	-	4	7	
t _{h(SO)}	Data output hold time	Slave mode	10	-	-	
t _{h(MO)}		Master mode	0	-	-	

^{1.} Guaranteed by characterization results.

^{2.} The maximum SPI clock frequency in slave transmitter mode is determined by the sum of $t_{v(SO)}$ and $t_{su(MI)}$ which has to fit into SCK low or high phase preceding the SCK sampling edge. This value can be achieved when the SPI communicates with a master having $t_{su(MI)} = 0$ while Duty_(SCK) = 50%.

Table 73. SPI characteristics in voltage Range 2 (1)

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
		Master mode		-	8	MHz
f _{SCK} 1/t _{c(SCK)}	SPI clock frequency	Slave mode Transmitter 1.65 <v<sub>DD<3.6V</v<sub>	-		8	
···C(SCK)		Slave mode Transmitter 2.7 <v<sub>DD<3.6V</v<sub>			8 ⁽²⁾	
Duty _(SCK)	Duty cycle of SPI clock frequency	Slave mode	30	50	70	%
t _{su(NSS)}	NSS setup time	Slave mode, SPI presc = 2	4*Tpclk	-	-	
t _{h(NSS)}	NSS hold time	Slave mode, SPI presc = 2	2*Tpclk	-	-	
t _{w(SCKH)}	SCK high and low time	Master mode	Tpclk-2	Tpclk	Tpclk+2	
t _{su(MI)}	Data input setup time	Master mode	0	-	-	
t _{su(SI)}		Slave mode	3	-	-	
t _{h(MI)}	Data input hold time	Master mode	11	-	-	
t _{h(SI)}		Slave mode	4.5	-	-	ns
t _{a(SO}	Data output access time	Slave mode	18	-	52	
t _{dis(SO)}	Data output disable time	Slave mode	12	-	42	
t _{v(SO)}	Data output valid time	Slave mode	-	20	56.5	
t _{v(MO)}		Master mode	-	5	9	
t _{h(SO)}	Data output hold time	Slave mode	13	-	-	
t _{h(MO)}		Master mode	3	-	-	

^{1.} Guaranteed by characterization results.

^{2.} The maximum SPI clock frequency in slave transmitter mode is determined by the sum of $t_{v(SO)}$ and $t_{su(MI)}$ which has to fit into SCK low or high phase preceding the SCK sampling edge. This value can be achieved when the SPI communicates with a master having $t_{su(MI)} = 0$ while Duty_(SCK) = 50%.

Table 74. SPI characteristics in voltage Range 3 (1)

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
f _{SCK}	CDI plank fraguancy	Master mode			2	MHz
1/t _{c(SCK)}	SPI clock frequency	Slave mode	-	-	2 ⁽²⁾	IVITZ
Duty _(SCK)	Duty cycle of SPI clock frequency	Slave mode	30	50	70	%
t _{su(NSS)}	NSS setup time	Slave mode, SPI presc = 2	4*Tpclk	-	-	
t _{h(NSS)}	NSS hold time	Slave mode, SPI presc = 2	2*Tpclk	-	-	
t _{w(SCKH)}	SCK high and low time	Master mode	Tpclk-2	Tpclk	Tpclk+2	
t _{su(MI)}	Data input setup time	Master mode	1.5	-	-	
t _{su(SI)}		Slave mode	6	-	-	
t _{h(MI)}	Data input hold time	Master mode	13.5	-	-	
t _{h(SI)}		Slave mode	16	-	-	ns
t _{a(SO}	Data output access time	Slave mode	30	-	70	
t _{dis(SO)}	Data output disable time	Slave mode	40	-	80	
t _{v(SO)}	Data output valid time	Slave mode	-	30	70	
t _{v(MO)}		Master mode	-	7	9	
t _{h(SO)}	Data output hold time	Slave mode	25	-	-	
t _{h(MO)}		Master mode	8		-	

^{1.} Guaranteed by characterization results.

The maximum SPI clock frequency in slave transmitter mode is determined by the sum of t_{v(SO)} and t_{su(MI)} which has to fit
into SCK low or high phase preceding the SCK sampling edge. This value can be achieved when the SPI communicates
with a master having t_{su(MI)} = 0 while Duty_(SCK) = 50%.

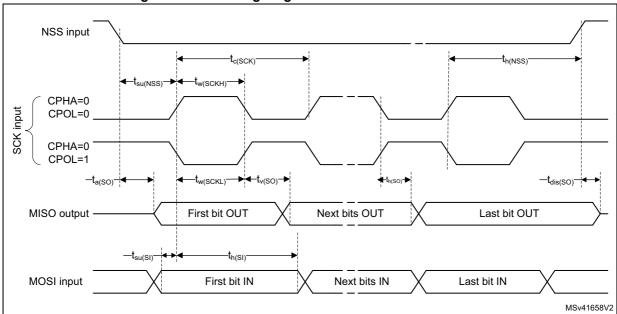
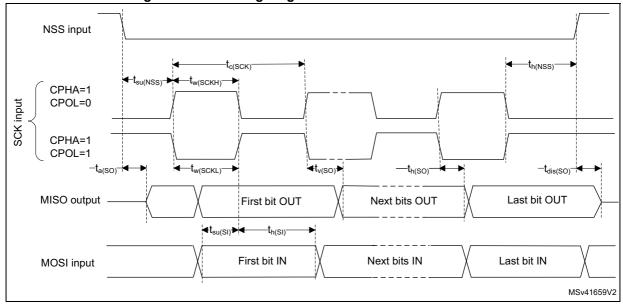


Figure 31. SPI timing diagram - slave mode and CPHA = 0





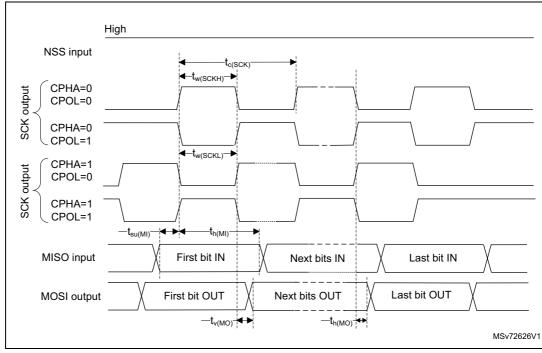


Figure 33. SPI timing diagram - master mode

I2S characteristics

Table 75. I2S characteristics⁽¹⁾

Symbol	Parameter	Conditions	Min	Max	Unit
f _{MCK}	I2S Main clock output	-	256 x 8K	256xFs ⁽²⁾	MHz
f	ICC aloak fraguanay	Master data: 32 bits	-	64xFs	MHz
f _{CK}	I2S clock frequency	Slave data: 32 bits	-	64xFs	IVI□∠
D _{CK}	I2S clock frequency duty cycle	Slave receiver	30	70	%
t _{v(WS)}	WS valid time Master mode		-	15	
t _{h(WS)}	WS hold time	Master mode	11	-	
t _{su(WS)}	WS setup time	Slave mode	6	-	
t _{h(WS)}	WS hold time	Slave mode	2	-	
t _{su(SD_MR)}	Data input setup time	Master receiver	0	-	
t _{su(SD_SR)}	Data input setup time	Slave receiver	6.5	-	ns
t _{h(SD_MR)}	Data input hold time	Master receiver	18	-	113
t _{h(SD_SR)}	Data input noid time	Slave receiver	15.5	-	
t _{v(SD_ST)}	Data output valid time	Slave transmitter (after enable edge)	-	77	
t _{v(SD_MT)}	Data Output valid tillie	Master transmitter (after enable edge)		8	
t _{h(SD_ST)}	Data output hold time	Slave transmitter (after enable edge)	18	-	
t _{h(SD_MT)}	Data output noid time	Master transmitter (after enable edge)	1.5	-	

^{1.} Guaranteed by characterization results.

Note:

Refer to the I2S section of the product reference manual for more details about the sampling frequency (Fs), f_{MCK} , f_{CK} and D_{CK} values. These values reflect only the digital peripheral behavior, source clock precision might slightly change them. DCK depends mainly on the ODD bit value, digital contribution leads to a min of (I2SDIV/(2*I2SDIV+ODD) and a max of (I2SDIV+ODD)/(2*I2SDIV+ODD). Fs max is supported for each mode/condition.

^{2. 256}xFs maximum value is equal to the maximum clock frequency.

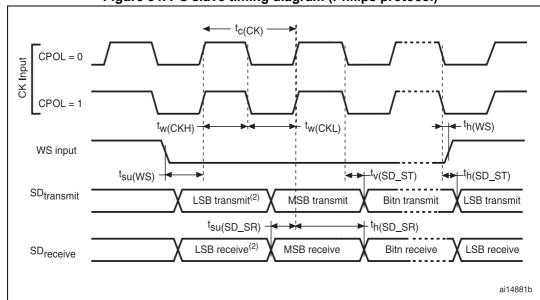


Figure 34. I²S slave timing diagram (Philips protocol)⁽¹⁾

- 1. Measurement points are done at CMOS levels: $0.3 \times V_{DD}$ and $0.7 \times V_{DD}$.
- LSB transmit/receive of the previously transmitted byte. No LSB transmit/receive is sent before the first byte.

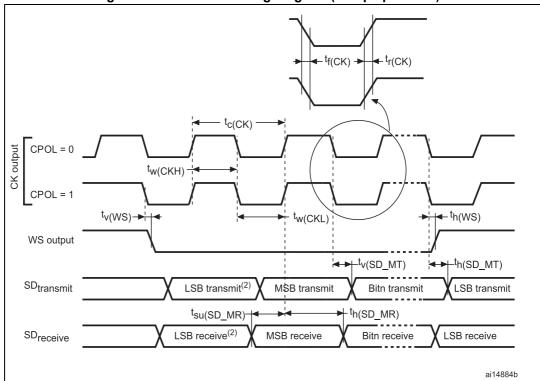


Figure 35. I²S master timing diagram (Philips protocol)⁽¹⁾

- 1. Guaranteed by characterization results.
- LSB transmit/receive of the previously transmitted byte. No LSB transmit/receive is sent before the first byte.

4

USB characteristics

The USB interface is USB-IF certified (full speed).

Table 76. USB startup time

Symbol	Parameter	Max	Unit
t _{STARTUP} ⁽¹⁾	USB transceiver startup time	1	μs

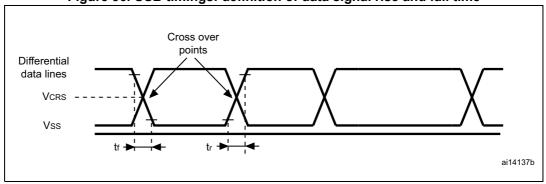
^{1.} Guaranteed by design.

Table 77. USB DC electrical characteristics

Symbol	Parameter	Conditions	Min. ⁽¹⁾	Max. ⁽¹⁾	Unit
Input leve	ls				
V _{DD}	USB operating voltage	-	3.0	3.6	V
V _{DI} ⁽²⁾	Differential input sensitivity	I(USB_DP, USB_DM)	0.2	-	
V _{CM} ⁽²⁾	Differential common mode range	Includes V _{DI} range	0.8	2.5	V
V _{SE} ⁽²⁾	Single ended receiver threshold	-	1.3	2.0	
Output levels					
V _{OL} ⁽³⁾	Static output level low	R_L of 1.5 k Ω to 3.6 $V^{(4)}$	-	0.3	V
V _{OH} ⁽³⁾	Static output level high	R_L of 15 k Ω to $V_{SS}^{(4)}$	2.8	3.6] '

- 1. All the voltages are measured from the local ground potential.
- 2. Guaranteed by characterization results.
- 3. Guaranteed by test in production.
- 4. R_L is the load connected on the USB drivers.

Figure 36. USB timings: definition of data signal rise and fall time





Driver characteristics⁽¹⁾ **Symbol Parameter Conditions** Min Max Unit Rise time⁽²⁾ $C_L = 50 pF$ 4 20 t_{r} ns Fall Time⁽²⁾ $C_{I} = 50 pF$ 4 t_f 20 ns Rise/ fall time matching t_r/t_f 90 110 % t_{rfm} Output signal crossover voltage 1.3 2.0 V V_{CRS}

Table 78. USB: full speed electrical characteristics

6.3.21 LCD controller

The devices embed a built-in step-up converter to provide a constant LCD reference voltage independently from the V_{DD} voltage. An external capacitor C_{ext} must be connected to the V_{LCD} pin to decouple this converter.

Table 79. LCD controller characteristics

Symbol	Parameter		Тур	Max	Unit
V_{LCD}	LCD external voltage	-	-	3.6	
V _{LCD0}	LCD internal reference voltage 0	-	2.6	-	
V _{LCD1}	LCD internal reference voltage 1	-	2.73	-	
V _{LCD2}	LCD internal reference voltage 2	-	2.86	-	
V _{LCD3}	LCD internal reference voltage 3	-	2.98	-	V
V _{LCD4}	LCD internal reference voltage 4	-	3.12	-	
V _{LCD5}	LCD internal reference voltage 5	-	3.26	-	
V _{LCD6}	LCD internal reference voltage 6	-	3.4	-	
V _{LCD7}	LCD internal reference voltage 7	-	3.55	-	
C _{ext}	V _{LCD} external capacitance	0.1	-	2	μF
I _{LCD} ⁽¹⁾	Supply current at V _{DD} = 2.2 V	-	3.3	-	μA
'LCD`	Supply current at V _{DD} = 3.0 V		3.1	-	μΛ
R _{Htot} ⁽²⁾	Low drive resistive network overall value	5.28	6.6	7.92	ΜΩ
R _L ⁽²⁾	High drive resistive network total value	192	240	288	kΩ
V ₄₄	Segment/Common highest level voltage	-	-	V _{LCD}	V

^{1.} Guaranteed by design.

Measured from 10% to 90% of the data signal. For more detailed informations, please refer to USB Specification - Chapter 7 (version 2.0).

Table 79. LCD controller characteristics (continued)

Symbol	Parameter	Min	Тур	Max	Unit
V ₃₄	Segment/Common 3/4 level voltage	-	3/4 V _{LCD}	-	
V ₂₃	Segment/Common 2/3 level voltage	-	2/3 V _{LCD}	-	
V ₁₂	Segment/Common 1/2 level voltage - 1/2 V _{LCD} -				V
V ₁₃	Segment/Common 1/3 level voltage	-	1/3 V _{LCD}	-	V
V ₁₄	Segment/Common 1/4 level voltage	-	1/4 V _{LCD}	-	
V ₀	Segment/Common lowest level voltage 0		-	,	
ΔVxx ⁽³⁾	Segment/Common level voltage error T _A = -40 to 85 ° C	-	-	± 50	mV

LCD enabled with 3 V internal step-up active, 1/8 duty, 1/4 bias, division ratio= 64, all pixels active, no LCD connected.

^{2.} Guaranteed by design.

^{3.} Guaranteed by characterization results.

7 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK packages, depending on their level of environmental compliance. ECOPACK specifications, grade definitions and product status *are available at www.st.com.* ECOPACK is an ST trademark.

7.1 Device marking

Refer to technical note "Reference device marking schematics for STM32 microcontrollers and microprocessors" (TN1433) available on www.st.com, for the location of pin 1 / ball A1 as well as the location and orientation of the marking areas versus pin 1 / ball A1.

Parts marked as "ES", "E" or accompanied by an engineering sample notification letter, are not yet qualified and therefore not approved for use in production. ST is not responsible for any consequences resulting from such use. In no event will ST be liable for the customer using any of these engineering samples in production. ST's Quality department must be contacted prior to any decision to use these engineering samples to run a qualification activity.

A WLCSP simplified marking example (if any) is provided in the corresponding package information subsection.



115/141

7.2 LQFP64 package information (5W)

This LQFP is 64-pin, 10 x 10 mm low-profile quad flat package.

Note: See list of notes in the notes section.

Figure 37. LQFP64 - Outline⁽¹⁵⁾

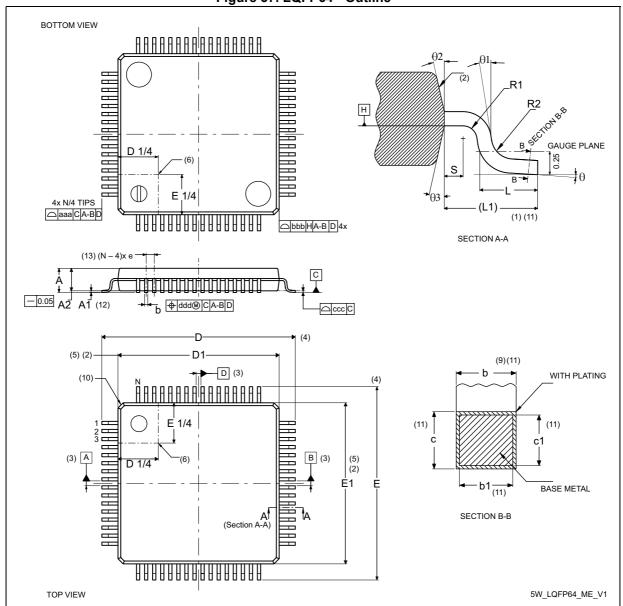
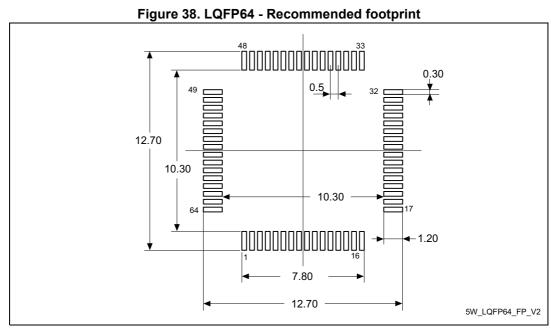


Table 80. LQFP64 - Mechanical data

Comple of		millimeters		inches ⁽¹⁴⁾			
Symbol	Min	Тур	Max	Min	Тур	Max	
А	-	-	1.60	-	-	0.0630	
A1 ⁽¹²⁾	0.05	-	0.15	0.0020	-	0.0059	
A2	1.35	1.40	1.45	0.0531	0.0551	0.0570	
b ⁽⁹⁾⁽¹¹⁾	0.17	0.22	0.27	0.0067	0.0087	0.0106	
b1 ⁽¹¹⁾	0.17	0.20	0.23	0.0067	0.0079	0.0091	
c ⁽¹¹⁾	0.09	-	0.20	0.0035	-	0.0079	
c1 ⁽¹¹⁾	0.09	-	0.16	0.0035	-	0.0063	
D ⁽⁴⁾		12.00 BSC			0.4724 BSC		
D1 ⁽²⁾⁽⁵⁾		10.00 BSC			0.3937 BSC		
E ⁽⁴⁾	12.00 BSC			0.4724 BSC			
E1 ⁽²⁾⁽⁵⁾		10.00 BSC		0.3937 BSC			
е		0.50 BSC		0.1970 BSC			
L	0.45	0.60	0.75	0.0177	0.0236	0.0295	
L1		1.00 REF		0.0394 REF			
N ⁽¹³⁾			(64			
θ	0°	3.5°	7°	0°	3.5°	7°	
θ1	0°	-	-	0°	-	-	
θ2	10°	12°	14°	10°	12°	14°	
θ3	10°	12°	14°	10°	12°	14°	
R1	0.08	-	-	0.0031	-	-	
R2	0.08	-	0.20	0.0031	-	0.0079	
S	0.20	-	-	0.0079	-	-	
aaa ⁽¹⁾	0.20		0.0079				
bbb ⁽¹⁾	0.20		0.0079				
ccc ⁽¹⁾		0.08		0.0031			
ddd ⁽¹⁾		0.08		0.0031			

Notes:

- 1. Dimensioning and tolerancing schemes conform to ASME Y14.5M-1994.
- 2. The Top package body size may be smaller than the bottom package size by as much as 0.15 mm.
- 3. Datums A-B and D to be determined at datum plane H.
- 4. To be determined at seating datum plane C.
- 5. Dimensions D1 and E1 do not include mold flash or protrusions. Allowable mold flash or protrusions is "0.25 mm" per side. D1 and E1 are Maximum plastic body size dimensions including mold mismatch.
- 6. Details of pin 1 identifier are optional but must be located within the zone indicated.
- 7. All Dimensions are in millimeters.
- 8. No intrusion allowed inwards the leads.
- 9. Dimension "b" does not include dambar protrusion. Allowable dambar protrusion shall not cause the lead width to exceed the maximum "b" dimension by more than 0.08 mm. Dambar cannot be located on the lower radius or the foot. Minimum space between protrusion and an adjacent lead is 0.07 mm for 0.4 mm and 0.5 mm pitch packages.
- 10. Exact shape of each corner is optional.
- 11. These dimensions apply to the flat section of the lead between 0.10 mm and 0.25 mm from the lead tip.
- 12. A1 is defined as the distance from the seating plane to the lowest point on the package body.
- 13. "N" is the number of terminal positions for the specified body size.
- 14. Values in inches are converted from mm and rounded to 4 decimal digits.
- 15. Drawing is not to scale.



1. Dimensions are expressed in millimeters.

Device marking for LQFP64

The following figure gives an example of topside marking versus pin 1 position identifier location.

The printed markings may differ depending on the supply chain.

Other optional marking or inset/upset marks, which depend on supply chain operations, are not indicated below.

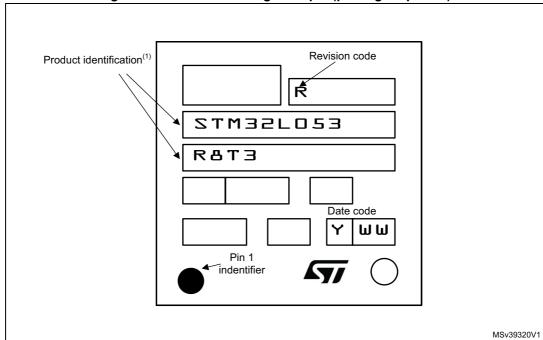
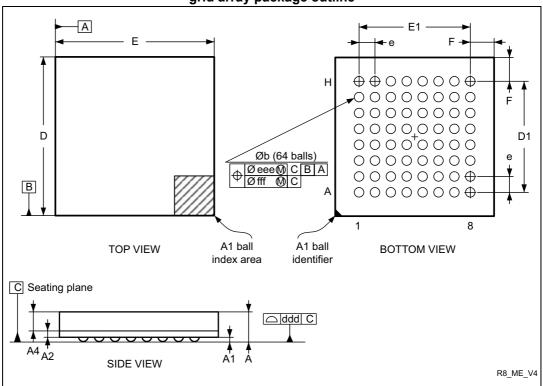


Figure 39. LQFP64 marking example (package top view)

^{1.} Parts marked as "ES", "E" or accompanied by an Engineering Sample notification letter, are not yet qualified and therefore not approved for use in production. ST is not responsible for any consequences resulting from such use. In no event will ST be liable for the customer using any of these engineering samples in production. ST's Quality department must be contacted prior to any decision to use these engineering samples to run a qualification activity.

7.3 TFBGA64 package information (R8)

Figure 40. TFBGA64 – 64-ball, 5 x 5 mm, 0.5 mm pitch thin profile fine pitch ball grid array package outline



1. Drawing is not to scale.

Table 81. TFBGA64 – 64-ball, 5 x 5 mm, 0.5 mm pitch thin profile fine pitch ball grid array package outline

Symbol	millimeters			inches ⁽¹⁾		
Symbol	Min	Тур	Max	Min	Тур	Max
Α	-	-	1.200	-	-	0.0472
A1	0.150	-	-	0.0059	-	-
A2	-	0.200	-	-	0.0079	-
A4	-	-	0.600	-	-	0.0236
b	0.250	0.300	0.350	0.0098	0.0118	0.0138
D	4.850	5.000	5.150	0.1909	0.1969	0.2028
D1	-	3.500	-	-	0.1378	-
Е	4.850	5.000	5.150	0.1909	0.1969	0.2028
E1	-	3.500	-	-	0.1378	-
е	-	0.500	-	-	0.0197	-
F	-	0.750	-	-	0.0295	-

Table 81. TFBGA64 – 64-ball, 5 x 5 mm, 0.5 mm pitch thin profile fine pitch ball grid array package outline (continued)

Symbol	millimeters			inches ⁽¹⁾		
Symbol	Min	Тур	Max	Min	Тур	Max
ddd	-	-	0.080	-	-	0.0031
eee	-	-	0.150	-	-	0.0059
fff	-	-	0.050	-	-	0.0020

^{1.} Values in inches are converted from mm and rounded to 4 decimal digits.

Figure 41. TFBGA64 – 64-ball, 5 x 5 mm, 0.5 mm pitch, thin profile fine pitch ball ,grid array recommended footprint

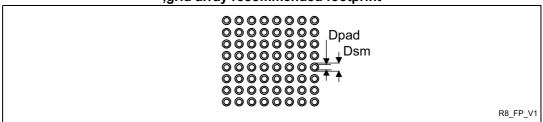


Table 82. TFBGA64 recommended PCB design rules (0.5 mm pitch BGA)

Dimension	Recommended values
Pitch	0.5
Dpad	0.280 mm
Dsm	0.370 mm typ. (depends on the soldermask registration tolerance)
Stencil opening	0.280 mm
Stencil thickness	Between 0.100 mm and 1.125 mm
Pad trace width	0.100 mm

Device marking for TFBGA64

The following figure gives an example of topside marking versus ball A 1 position identifier location.

The printed markings may differ depending on the supply chain.

Other optional marking or inset/upset marks, which depend on supply chain operations, are not indicated below.

Product identification⁽¹⁾

Date code = Year + week
Y WW
Revision code

MSv33797V3

Figure 42. TFBGA64 marking example (package top view)

1. Parts marked as "ES", "E" or accompanied by an Engineering Sample notification letter, are not yet qualified and therefore not approved for use in production. ST is not responsible for any consequences resulting from such use. In no event will ST be liable for the customer using any of these engineering samples in production. ST's Quality department must be contacted prior to any decision to use these engineering samples to run a qualification activity.



7.4 LQFP48 package information (5B)

This LQFP is a 48-pin, 7 x 7 mm low-profile quad flat package

Note: See list of notes in the notes section.

Figure 43. LQFP48 – Outline⁽¹⁵⁾

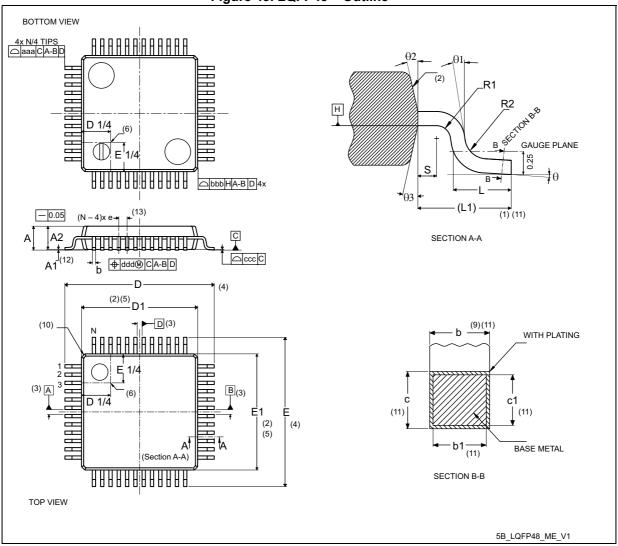


Table 83. LQFP48 - Mechanical data

Complete	millimeters		inches ⁽¹⁴⁾			
Symbol	Min	Тур	Max	Min	Тур	Max
Α	-	-	1.60	-	-	0.0630
A1 ⁽¹²⁾	0.05	-	0.15	0.0020	-	0.0059
A2	1.35	1.40	1.45	0.0531	0.0551	0.0571
b ⁽⁹⁾⁽¹¹⁾	0.17	0.22	0.27	0.0067	0.0087	0.0106
b1 ⁽¹¹⁾	0.17	0.20	0.23	0.0067	0.0079	0.0090
c ⁽¹¹⁾	0.09	-	0.20	0.0035	-	0.0079
c1 ⁽¹¹⁾	0.09	-	0.16	0.0035	-	0.0063
D ⁽⁴⁾		9.00 BSC			0.3543 BSC	
D1 ⁽²⁾⁽⁵⁾		7.00 BSC			0.2756 BSC	
E ⁽⁴⁾		9.00 BSC		0.3543 BSC		
E1 ⁽²⁾⁽⁵⁾		7.00 BSC		0.2756 BSC		
е		0.50 BSC		0.1970 BSC		
L	0.45	0.60	0.75	0.0177	0.0236	0.0295
L1		1.00 REF		0.0394 REF		
N ⁽¹³⁾				48		
θ	0°	3.5°	7°	0°	3.5°	7°
θ1	0°	-	-	0°	-	-
θ2	10°	12°	14°	10°	12°	14°
θ3	10°	12°	14°	10°	12°	14°
R1	0.08	-	-	0.0031	-	-
R2	0.08	-	0.20	0.0031	-	0.0079
S	0.20	-	-	0.0079	-	-
aaa ⁽¹⁾⁽⁷⁾	0.20			0.0079		
bbb ⁽¹⁾⁽⁷⁾	0.20		0.0079			
ccc ⁽¹⁾⁽⁷⁾		0.08		0.0031		
ddd ⁽¹⁾⁽⁷⁾		0.08			0.0031	

Notes:

- 1. Dimensioning and tolerancing schemes conform to ASME Y14.5M-1994.
- 2. The Top package body size may be smaller than the bottom package size by as much as 0.15 mm.
- 3. Datums A-B and D to be determined at datum plane H.
- 4. To be determined at seating datum plane C.
- 5. Dimensions D1 and E1 do not include mold flash or protrusions. Allowable mold flash or protrusions is "0.25 mm" per side. D1 and E1 are Maximum plastic body size dimensions including mold mismatch.
- 6. Details of pin 1 identifier are optional but must be located within the zone indicated.
- 7. All Dimensions are in millimeters.
- 8. No intrusion allowed inwards the leads.
- 9. Dimension "b" does not include dambar protrusion. Allowable dambar protrusion shall not cause the lead width to exceed the maximum "b" dimension by more than 0.08 mm. Dambar cannot be located on the lower radius or the foot. Minimum space between protrusion and an adjacent lead is 0.07 mm for 0.4 mm and 0.5 mm pitch packages.
- 10. Exact shape of each corner is optional.
- 11. These dimensions apply to the flat section of the lead between 0.10 mm and 0.25 mm from the lead tip.
- 12. A1 is defined as the distance from the seating plane to the lowest point on the package body.
- 13. "N" is the number of terminal positions for the specified body size.
- 14. Values in inches are converted from mm and rounded to 4 decimal digits.
- 15. Drawing is not to scale.

Figure 44. LQFP48 - Recommended footprint

1. Dimensions are expressed in millimeters.

Device marking for LQFP48

The following figure gives an example of topside marking versus pin 1 position identifier location.

The printed markings may differ depending on the supply chain.

Other optional marking or inset/upset marks, which depend on supply chain operations, are not indicated below.

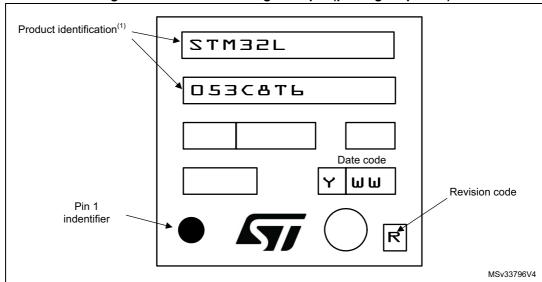


Figure 45. LQFP48 marking example (package top view)

1. Parts marked as "ES", "E" or accompanied by an Engineering Sample notification letter, are not yet qualified and therefore not approved for use in production. ST is not responsible for any consequences resulting from such use. In no event will ST be liable for the customer using any of these engineering samples in production. ST's Quality department must be contacted prior to any decision to use these engineering samples to run a qualification activity.



7.5 UFQFPN48 package information (A0B9)

This UFQFPN is a 48-lead, 7 x 7 mm, 0.5 mm pitch, ultra thin fine pitch quad flat package.

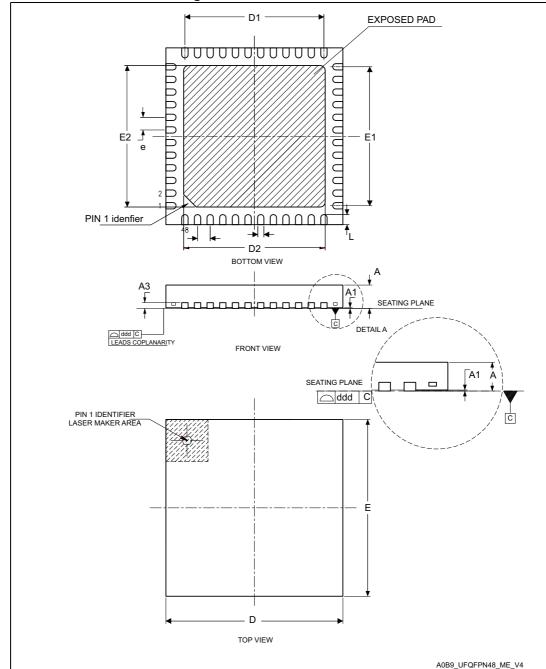


Figure 46. UFQFPN48 - Outline

- 1. Drawing is not to scale.
- 2. All leads/pads should also be soldered to the PCB to improve the lead/pad solder joint life.
- 3. There is an exposed die pad on the underside of the UFQFPN48 package. It is recommended to connect and solder this back-side pad to PCB ground.

Cumbal		millimeters			inches ⁽¹⁾	
Symbol	Min	Тур	Max	Min	Тур	Max
А	0.500	0.550	0.600	0.0197	0.0217	0.0236
A1	0.000	0.020	0.050	0.0000	0.0008	0.0020
A3	-	0.152	-	-	0.0060	-
b	0.200	0.250	0.300	0.0079	0.0098	0.0118
D ⁽²⁾	6.900	7.000	7.100	0.2717	0.2756	0.2795
D1	5.400	5.500	5.600	0.2126	0.2165	0.2205
D2 ⁽³⁾	5.500	5.600	5.700	0.2165	0.2205	0.2244
E ⁽²⁾	6.900	7.000	7.100	0.2717	0.2756	0.2795
E1	5.400	5.500	5.600	0.2126	0.2165	0.2205
E2 ⁽³⁾	5.500	5.600	5.700	0.2165	0.2205	0.2244
е	-	0.500	-	-	0.0197	-
L	0.300	0.400	0.500	0.0118	0.0157	0.0197
ddd	-	-	0.080	-	-	0.0031

Table 84. UFQFPN48 - Mechanical data

- 1. Values in inches are converted from mm and rounded to four decimal digits.
- 2. Dimensions D and E do not include mold protrusion, not exceed 0.15 mm.
- 3. Dimensions D2 and E2 are not in accordance with JEDEC.

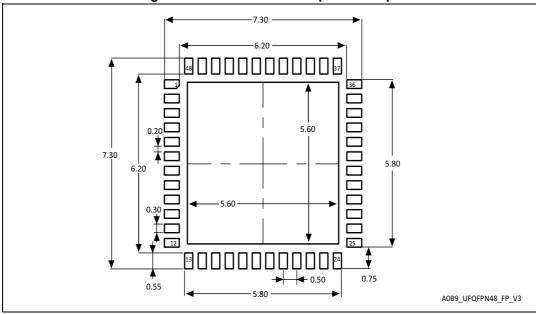


Figure 47. UFQFPN48 – Footprint example

1. Dimensions are expressed in millimeters.

Device marking for UFQFPN48

The following figure gives an example of topside marking versus pin 1 position identifier location.

The printed markings may differ depending on the supply chain.

Other optional marking or inset/upset marks, which depend on supply chain operations, are not indicated below.

Product identification⁽¹⁾

STM32L053

CBULD

Date code

Y WW

Revision code

Figure 48. UFQFPN48 marking example (package top view)

^{1.} Parts marked as "ES", "E" or accompanied by an Engineering Sample notification letter, are not yet qualified and therefore not approved for use in production. ST is not responsible for any consequences resulting from such use. In no event will ST be liable for the customer using any of these engineering samples in production. ST's Quality department must be contacted prior to any decision to use these engineering samples to run a qualification activity.

7.6 Thermal characteristics

The maximum chip-junction temperature, T_J max, in degrees Celsius, may be calculated using the following equation:

 $T_J \max = T_A \max + (P_D \max \times \Theta_{JA})$

Where:

- T_A max is the maximum ambient temperature in °C,
- Θ_{JA} is the package junction-to-ambient thermal resistance, in °C/W,
- P_D max is the sum of P_{INT} max and $P_{I/O}$ max (P_D max = P_{INT} max + $P_{I/O}$ max),
- P_{INT} max is the product of I_{DD} and V_{DD}, expressed in Watts. This is the maximum chip internal power.

P_{I/O} max represents the maximum power dissipation on output pins where:

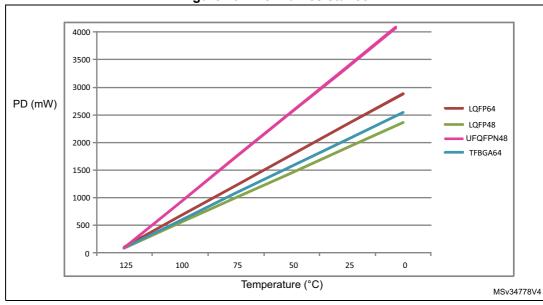
$$P_{I/O} \max = \sum (V_{OL} \times I_{OL}) + \sum ((V_{DD} - V_{OH}) \times I_{OH}),$$

taking into account the actual V_{OL} / I_{OL} and V_{OH} / I_{OH} of the I/Os at low and high level in the application.

Symbol Parameter Value Unit Thermal resistance junction-ambient 61 TFBGA64 - 5 x 5 mm / 0.5 mm pitch Thermal resistance junction-ambient 45 LQFP64 - 10 x 10 mm / 0.5 mm pitch °C/W Θ_{JA} Thermal resistance junction-ambient 55 LQFP48 - 7 x 7 mm / 0.5 mm pitch Thermal resistance junction-ambient 31 UFQFPN48 - 7 x 7 mm / 0.5 mm pitch

Table 85. Thermal characteristics

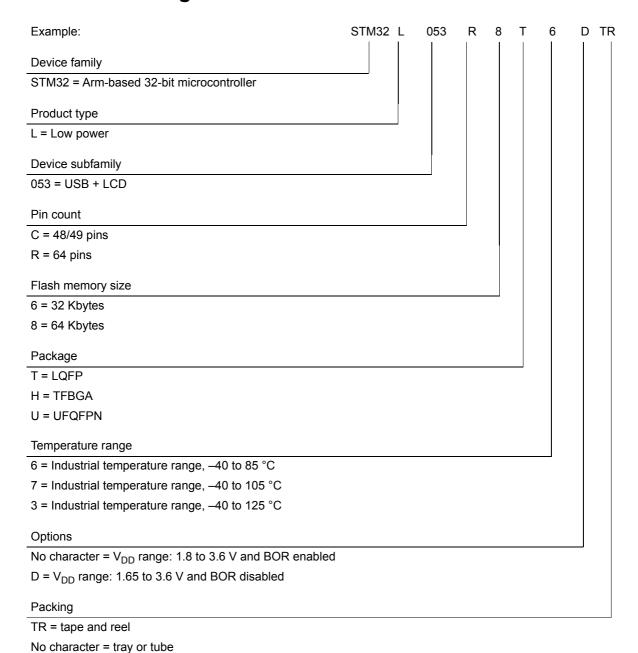




7.6.1 Reference document

JESD51-2 Integrated Circuits Thermal Test Method Environment Conditions - Natural Convection (Still Air). Available from www.jedec.org.

8 Ordering information



For a list of available options (speed, package, etc.) or for further information on any aspect of this device, please contact your nearest ST sales office.

9 Important security notice

The STMicroelectronics group of companies (ST) places a high value on product security, which is why the ST product(s) identified in this documentation may be certified by various security certification bodies and/or may implement our own security measures as set forth herein. However, no level of security certification and/or built-in security measures can guarantee that ST products are resistant to all forms of attacks. As such, it is the responsibility of each of ST's customers to determine if the level of security provided in an ST product meets the customer needs both in relation to the ST product alone, as well as when combined with other components and/or software for the customer end product or application. In particular, take note that:

- ST products may have been certified by one or more security certification bodies, such as Platform Security Architecture (www.psacertified.org) and/or Security Evaluation standard for IoT Platforms (www.trustcb.com). For details concerning whether the ST product(s) referenced herein have received security certification along with the level and current status of such certification, either visit the relevant certification standards website or go to the relevant product page on www.st.com for the most up to date information. As the status and/or level of security certification for an ST product can change from time to time, customers should re-check security certification status/level as needed. If an ST product is not shown to be certified under a particular security standard, customers should not assume it is certified.
- Certification bodies have the right to evaluate, grant and revoke security certification in relation to ST products. These certification bodies are therefore independently responsible for granting or revoking security certification for an ST product, and ST does not take any responsibility for mistakes, evaluations, assessments, testing, or other activity carried out by the certification body with respect to any ST product.
- Industry-based cryptographic algorithms (such as AES, DES, or MD5) and other open standard technologies which may be used in conjunction with an ST product are based on standards which were not developed by ST. ST does not take responsibility for any flaws in such cryptographic algorithms or open technologies or for any methods which have been or may be developed to bypass, decrypt or crack such algorithms or technologies.
- While robust security testing may be done, no level of certification can absolutely guarantee protections against all attacks, including, for example, against advanced attacks which have not been tested for, against new or unidentified forms of attack, or against any form of attack when using an ST product outside of its specification or intended use, or in conjunction with other components or software which are used by customer to create their end product or application. ST is not responsible for resistance against such attacks. As such, regardless of the incorporated security features and/or any information or support that may be provided by ST, each customer is solely responsible for determining if the level of attacks tested for meets their needs, both in relation to the ST product alone and when incorporated into a customer end product or application.
- All security features of ST products (inclusive of any hardware, software, documentation, and the like), including but not limited to any enhanced security features added by ST, are provided on an "AS IS" BASIS. AS SUCH, TO THE EXTENT PERMITTED BY APPLICABLE LAW, ST DISCLAIMS ALL WARRANTIES, EXPRESS OR IMPLIED, INCLUDING BUT NOT LIMITED TO THE IMPLIED WARRANTIES OF MERCHANTABILITY OR FITNESS FOR A PARTICULAR PURPOSE, unless the applicable written and signed contract terms specifically provide otherwise.



10 Revision history

Table 86. Document revision history

Changes
itial release.
pdated Table 4: Functionalities depending on the working mode (from Run/active down to andby). Added Section 3.2: Interconnect matrix. pdated Figure 4: STM32L053x6/8 TFBGA64 ballout. Added VREF_OUT additional notion to PB0 and PB1, replaced TTa I/O structure by TC, and updated PA0/4/5 and C5/14 I/O structure, and added note 2 in Table 15: STM32L053x6/8 pin definitions. pdated Table 24: General operating conditions, Table 21: Voltage characteristics and able 22: Current characteristics. odified conditions in Table 27: Embedded internal reference voltage. pdated Table 30: Current consumption in Run mode, code with data processing running om flash, Table 30: Current consumption in Run mode, code with data processing running om RAM, Table 30: Current consumption in Sleep mode, Table 33: Current consumption in sow-power run mode, Table 34: Current consumption in Low-power sleep mode, Table 35: ripical and maximum current consumptions in Stop mode and Table 36: Typical and aximum current consumptions in Standby mode. Added Figure 12: IDD vs VDD, at TA= 55/55/85/105 °C, Run mode, code running from flash memory, Range 2, HSE, 1WS, igure 13: IDD vs VDD, at TA= 25/55/85/105 °C, Run mode, code running from flash emory, Range 2, HSI16, 1WS, Figure 14: IDD vs VDD, at TA= 25/55/85/105/125 °C, Low-ower run mode, code running from RAM, Range 3, MSI (Range 0) at 64 KHz, 0 WS, igure 15: IDD vs VDD, at TA= 25/55/85/105/125 °C, Stop mode with RTC enabled and imning on LSE Low drive and Figure 16: IDD vs VDD, at TA= 25/55/85/105/125 °C, Stop ode with RTC disabled, all clocks OFF. pdated Table 43: HSE oscillator characteristics and Table 44: LSE oscillator naracteristics. Added Figure 21: HS116 minimum and maximum value versus temperature. pdated Table 55: ESD absolute maximum ratings, Table 57: I/O accreateristics and igure 22: VIH/VIL versus VDD (CMOS I/Os) and Figure 23: VIH/VIL versus VDD TTL I/Os). pdated Table 59: Output voltage characteristics, Table 60: I/O AC characteristics and igure 24: I/O AC characteristics definition.



Table 86. Document revision history (continued)

Date	Revision	Changes
		ADC now guaranteed down to 1.65 V.
		Cover page: updated core speed, added minimum supply voltage for ADC, DAC and comparators.
		Updated list of applications in <i>Section 1: Introduction</i> . Changed number of I2S interfaces to one in <i>Section 2: Description</i> .
		Updated RTC/TIM21 in Table 5: STM32L053x6/8 peripherals interconnect matrix.
		Updated Table 4: Functionalities depending on the working mode (from Run/active down to standby).
		Updated Section 3.4.1: Power supply schemes.
	3	Updated Figure 4: STM32L053x6/8 TFBGA64 ballout.
		Updated V _{DDA} in <i>Table 24: General operating conditions</i> .
25-Jun- 2014		Divided Table Current consumption in Run mode, code with data processing running from flash into Table 28 and Table 29 and content updated. Divided Table Current consumption in Run mode, code with data processing running from RAM into Table 30 and Table 31 and content updated. Updated Table 32: Current consumption in Sleep mode, Table 33: Current consumption in Low-power run mode, Table 34: Current consumption in Low-power sleep mode, Table 35: Typical and maximum current consumptions in Stop mode, Table 36: Typical and maximum current consumptions in Standby mode, and added Table 37: Average current consumption during wake-up.
		Updated Table 38: Peripheral current consumption in Run or Sleep mode and added Table 39: Peripheral current consumption in Stop and Standby mode.
		Updated <i>Table 46: HSI48 oscillator characteristics</i> . Removed note 1 below <i>Figure 19: HSE oscillator circuit diagram</i> .
		Updated t _{LOCK} in <i>Table 49: PLL characteristics</i> .
		Updated Table 51: Flash memory and data EEPROM characteristics and Table 52: Flash memory and data EEPROM endurance and retention.
		Updated Table 60: I/O AC characteristics.
		Updated Table 62: ADC characteristics.
		Updated Figure 49: Thermal resistance and added note 1.



Table 86. Document revision history (continued)

Date	Revision	Changes
05-Sep- 2014	4	Extended operating temperature range to 125 °C. Updated minimum ADC operating voltage to 1.65 V. Replaced USART3 by LPUART1 in <i>Table 15: STM32L053x6/8 pin definitions</i> and LPUART by LPUART1 in <i>Table 16: Alternate function port A, Table 17: Alternate function port B, Table 18: Alternate function port C, Table 19: Alternate function port D and <i>Table 20: Alternate function port H.</i> Updated PA6 in <i>Table 16: Alternate function port A.</i> Updated temperature range in <i>Section 2: Description, Table 1: Ultra-low-power STM32L053x6/x8 device features and peripheral counts.</i> Updated PD, TA and TJ to add range 3 in <i>Table 24: General operating conditions.</i> Added range 3 in <i>Table 51: Flash memory and data EEPROM characteristics, Table 52: Flash memory and data EEPROM characteristics, Table 32: Current consumption in Run mode, code with data processing running from flash, Table 30: Current consumption in Run mode, code with data processing running from RAM, Table 32: Current consumption in Sleep mode, Table 33: Current consumption in Low-power run mode, Table 34: Current consumptions in Slop mode, Table 36: Typical and maximum current consumptions in Stop mode, Table 36: Typical and maximum current consumptions in Stop mode, Table 36: Typical and maximum current consumptions in Stop mode, Table 36: Typical and maximum current consumptions in Standby mode and Table 40: Low-power mode wake-up timings. Updated Figure 49: Thermal resistance and removed note 1. Updated Figure 14: IDD vs VDD, at TA= 25/55/85/105/125 °C, Low-power run mode, code running from RAM, Range 3, MSI (Range 0) at 64 KHz, 0 WS, Figure 15: IDD vs VDD, at TA= 25/55/85/105/125 °C, Stop mode with RTC disabled, all clocks OFF. Updated Table 36: Typical and maximum current consumption in Run or Sleep mode. Updated Table 39: Peripheral current consumption in Run or Sleep mode. Updated Table 39: Peripheral current consumption in Delow Table 40: Low-power mode wake-up timings. Updated VF(NRST) and VNF(NRST) in Table 61: NRST pin characteristics. Updated V</i></i>

Table 86. Document revision history (continued)

Date	Revision	Changes
08-Sep- 2015	5	Updated all pinout/ballout schematics to highlight pin/ball supplied through VDD_USB. Updated current consumption in Run mode in Section: Features. Renamed BOOT1 into nBOOT1. Changed USARTx_RTS into USARTx_RTS_DE and LPUARTx_RTS into LPUARTx_RTS_DE. Updated VLCD in Section 3.12: Analog-to-digital converter (ADC) ADC no more available in Low-power run and Low-power Sleep modes in Table 4: Functionalities depending on the working mode (from Run/active down to standby). Updated Figure 3: STM32L053x6/8 LQFP64 pinout, Figure 4: STM32L053x6/8 TFBGA64 ballout and Figure 5: STM32L053x6/8 LQFP48 pinout. Changed I/O structure for PC5 and modified E5 and E6 signals for TFBGA64 in Table 15: STM32L053x6/8 pin definitions. Added Slyndous and updated Slop(PIN) in Table 22: Current characteristics Updated VDD_USB and updated Slop(PIN) in Table 22: Current characteristics Updated VDD_USB in Table 22: Current characteristics. Changed temperature condition in Table 7: Internal voltage reference measured values and Table 26: Embedded internal reference voltage calibration values. Updated TCoeff in Table 27: Embedded internal reference voltage. Added note related to Standby mode in Table 39: Peripheral current consumption in Stop and Standby mode. Updated Figure 14: IDD vs VDD, at TA= 25/55/85/105/125 °C, Low-power run mode, code running from RAM, Range 3, MSI (Range 0) at 64 KHz, 0 WS, Figure 15: IDD vs VDD, at TA= 25/55/85/105/125 °C, Stop mode with RTC disabled, all clocks OFF. Updated Table 40: Low-power mode wake-up timings. Updated Table 40: Low-power mode wake-up timings. Updated Table 62: ADC characteristics, Table 54: EMI characteristics and Table 55: ESD absolute maximum ratings. Added typ_LDO in Table 62: ADC characteristics. Updated Table 57: I/O current injection susceptibility, Table 58: I/O static characteristics (Ilkg) and Table 60: I/O AC characteristics: updated introduction and Table 71: I2C analog filter characteristics. Updated Figure 31: SPI timing diagram - slave mode and CPHA = 0. Added S



Table 86. Document revision history (continued)

_	Table 86. Document revision history (continued)		
Date	Revision	Changes	
11-Mar- 2016	6	Updated number of SPIs on cover page and in <i>Table 1: Ultra-low-power STM32L053x6/x8 device features and peripheral counts.</i> Changed minimum comparator supply voltage to 1.65 V on cover page. Added number of fast and standard channels in <i>Section 3.12: Analog-to-digital converter (ADC).</i> Changed LCD_VLCD1 into LCD_VLCD2 in <i>Section 3.13.2: V_{LCD} voltage monitoring.</i> Updated <i>Section 3.19.2: Universal synchronous/asynchronous receiver transmitter (USART)</i> and <i>Section 3.19.4: Serial peripheral interface (SPI)/Inter-integrated sound (I2S)</i> to mention the fact that USARTs with synchronous mode feature can be used as SPI master interfaces. Added baudrate allowing to wake up the MCU from Stop mode in <i>Section 3.19.2: Universal synchronous/asynchronous receiver transmitter (USART)</i> and <i>Section 3.19.3: Low-power universal asynchronous receiver transmitter (UPART).</i> In <i>Section 6: Electrical characteristics</i> , updated notes related to values guaranteed by characterization. Section 6.3.15: 12-bit ADC characteristics: — <i>Table 62: ADC characteristics:</i> — <i>Table 62: ADC characteristics:</i> Distinction made between V _{DDA} for fast and standard channels; added note 1 Added note 4 related to R _{ADC} . Updated f _{TRIG} . and V _{AIN} maximum value; added V _{REF+} . Updated t _S and t _{CONV} . — Updated equation 1 description. — Updated <i>Table 63: R_{AIN} max for f_{ADC} = 16 MHz</i> for f _{ADC} = 16 MHz and distinction made between fast and standard channels. Updated R _O and added Note 2 in <i>Table 65: DAC characteristics</i> . Added <i>Table 72: USART/LPUART characteristics</i> . Updated <i>Figure 48: UFQFPN48 marking example (package top view)</i> .	
11-Oct- 2016	7	Updated note related to PA4 in <i>Table 15: STM32L053x6/8 pin definitions</i> ; added same note to PA4 in <i>Table 8: Capacitive sensing GPIOs available on STM32L053x6/8 devices</i> and <i>Table 16: Alternate function port A.</i> Updated VDD_USB and VDD in <i>Table 15: STM32L053x6/8 pin definitions</i> . Renamed USB_OE into USB_NOE. Added mission profile compliance with JEDEC JESD47 in <i>Section 6.2: Absolute maximum ratings</i> . Added note 2. related to the position of the external capacitor below <i>Figure 25: Recommended NRST pin protection</i> . Updated R _L in <i>Table 62: ADC characteristics</i> . Updated t _{AF} maximum value for range 1 in <i>Table 71: I2C analog filter characteristics</i> . Updated t _{WUUSART} description in <i>Table 72: USART/LPUART characteristics</i> . Updated <i>Figure 31: SPI timing diagram - slave mode and CPHA = 0</i> and <i>Figure 32: SPI timing diagram - slave mode and CPHA = 1</i> . Added reference to optional marking or inset/upset marks in all package device marking sections.	

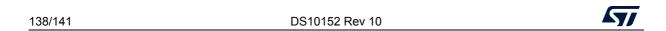


Table 86. Document revision history (continued)

Date	Revision	Changes
11-Sep- 2017	Revision	Memories and I/Os moved after Core in Features. Removed column "I/O operation" from Table 2: Functionalities depending on the operating power supply range and added note related to GPIO speed. Updated V _{DD_USB} in Section 3.4.1: Power supply schemes. Updated Figure 30: 12-bit buffered/non-buffered DAC and added note below figure. In Section 5: Memory mapping, replaced memory mapping schematic by reference to the
	8	reference manual. Updated minimum and maximum values of I/O weak pull-up equivalent resistor (R _{PU}) and weak pull-down equivalent resistor (R _{PD}) in <i>Table 58: I/O static characteristics</i> . Updated minimum and maximum values of NRST weak pull-up equivalent resistor (R _{PU}) in <i>Table 61: NRST pin characteristics</i> . Removed <i>Table 90: USART/LPUART characteristics</i> . Updated <i>Figure 40: TFBGA64 – 64-ball, 5 x 5 mm, 0.5 mm pitch thin profile fine pitch ball grid array package outline</i> . Updated note below marking schematics.



Table 86. Document revision history (continued)

Date	Revision	Changes
		-
27-Jun- 2019	9	Added UFQFPN48 package. Updated Arm logo and added Arm word mark notice in <i>Section 1: Introduction</i> . Removed Cortex and USB logos. Updated <i>Table 4: Functionalities depending on the working mode (from Run/active down to standby)</i> to change I2C functionality to disabled in Low-power Run and Low-power Sleep modes. Updated V _{DD_USB} description in <i>Section 3.4.1: Power supply schemes</i> . Replaced LCD_VLCD2 by LCD_VLCD1 in <i>Section 3.13.2: V_{LCD} voltage monitoring</i> . Changed USARTx_RTS, USARTx_RTS_DE into USARTx_RTS/USARTx_DE, and LPUART1_RTS, LPUART1_RTS_DE into LPUART1_RTS/LPUART1_DE in <i>Section 4: Pin descriptions</i> . In <i>Table 15: STM32L053x6/8 pin definitions</i> changed PB2 and PB12 additional functions to LCD_VLCD2 and LCD_VLCD1, respectively. Updated V _{DD_USB} and note 2. in <i>Table 24: General operating conditions</i> . Updated Figure 40: TFBGA64 – 64-ball, 5 x 5 mm, 0.5 mm pitch thin profile fine pitch ball grid array package outline, Figure 41: TFBGA64 – 64-ball, 5 x 5 mm, 0.5 mm pitch, thin profile fine pitch ball ,grid array recommended footprint and Figure 82: TFBGA64 recommended PCB design rules (0.5 mm pitch BGA). Updated paragraph introducing all package marking schematics to add the new sentence "The printed markings may differ
		depending on the supply chain". Added UFQFPN48 package marking example.
	10	Added indication that patents apply in <i>Section : Features</i> . Added sustainability logo. Added SPI mode to USART feature on cover page and <i>Section 3.19.2: Universal synchronous/asynchronous receiver transmitter (USART)</i> .
		Added reference to the device errata sheet in Section 1: Introduction. Updated Figure 2: Clock tree.
		Updated pin numbers for UFQFPN48 in <i>Table 15: STM32L053x6/8 pin definitions</i> . Added note on reduced touch sensing sensitivity to PA5 in <i>Table 15: STM32L053x6/8 pin definitions</i> and <i>Table 16: Alternate function port A</i> .
		Updated V _{IN} maximum value on FT and FTf pins in <i>Table 21: Voltage characteristics</i> .
		Added reference to AN4899 and recommendation of GPIO low- and high-level voltages in Section 6.3.13: I/O port characteristics.
		Added twuusart and twulpuart in Table 40: Low-power mode wake-up timings.
31-Jul- 2025		Updated V _{HSEH} and V _{HSEL} characteristics in <i>Table 41: High-speed external user clock characteristics</i> , as well as V _{LSEH} and V _{LSEL} characteristics in <i>Table 42: Low-speed external user clock characteristics</i> .
		Updated Figure 24: I/O AC characteristics definition. Updated Table 54: EMI characteristics.
		Updated Figure 26: ADC accuracy characteristics and Figure 27: Typical connection diagram using the ADC. Removed R _{10K} and R _{400K} from Table 68: Comparator 1 characteristics.
		Updated Figure 31: SPI timing diagram - slave mode and CPHA = 0, Figure 32: SPI timing diagram - slave mode and CPHA = 1, and Figure 33: SPI timing diagram - master mode, and removed notes on measurement at $0.3V_{\rm DD}$ and $0.7V_{\rm DD}$.
		Added Section 7.1: Device marking. Updated Section 7.2: LQFP64 package information (5W), Section 7.4: LQFP48 package information (5B), and Section 7.5: UFQFPN48 package information (A0B9).
		Added Section 9: Important security notice.



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